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AUTOMATED ARRAY ASSEMBLY

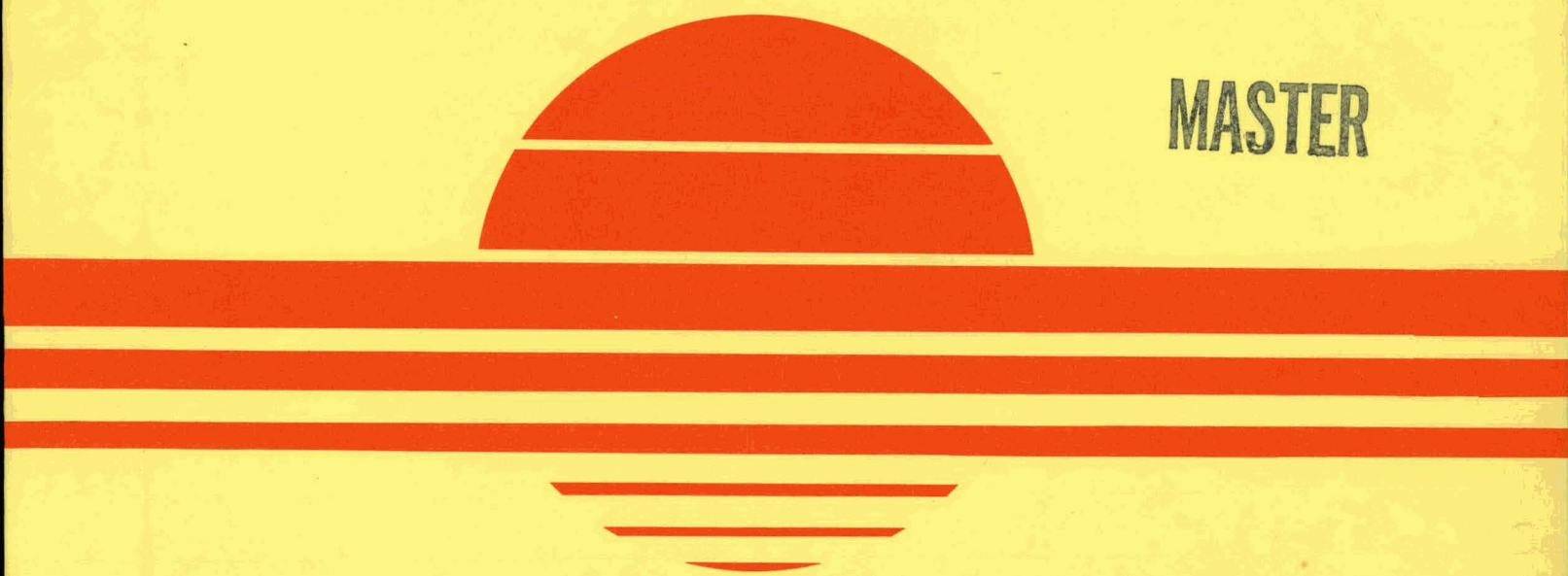
Final Report, February 3, 1976—November 2, 1977

By
R. V. D'Aiello

December 1977

Work Performed Under Contract No. NAS-7-100-954352

RCA Laboratories
Princeton, New Jersey



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PREFACE

This Final Report, prepared by RCA Laboratories, Princeton, NJ 08540, describes the results of work performed from February 3, 1976 to November 2, 1977 in the Energy Systems Research Laboratory, B. F. Williams, Director; Materials and Process Laboratory, Solid State Division, H. Veloric, Manager; and at the Advanced Technology Laboratory, Government and Commercial Systems, Camden, NJ, P. Wright, Director. The Project Scientist is R. V. D'Aiello and the Project Supervisor is D. Richman, Head, Semiconductor Materials Research. Others who participated in the research and writing of this report are:

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D. Richman	-	silicon material
D. Redfield	-	device modeling
G. Schnable	-	metallization
W. Kern	-	metallization
K. Bube	-	metallization
R. Scott	-	panel design and fabrication
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U. Roundtree	-	manufacturing
E. Cave	-	manufacturing
L. Guarino	-	manufacturing

The JPL Task Manager is Don Bickler.

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SECTION I

SUMMARY

This report contains three main sections which describe a general technology assessment and manufacturing cost analysis; a near-term (1982) factory design; and the results of an experimental production study for the large-scale production of flat-panel silicon solar-cell arrays.

Section II describes the results of an extensive study and detailed analysis of technologies which could be related to array module manufacturing. From this study, several manufacturing sequences emerge as candidates for satisfying the ERDA/JPL cost goal of $0.50/W selling price in 1986. We have found a minimum manufacturing cost in a highly automated line of $0.30/W assuming the silicon is free. The panels are of a double-glass construction and are based on round wafers. Screen-printed silver has been used as the metallization with a spray-coated antireflection (AR) layer. The least expensive junction-formation technology appears to be ion implantation; however, several other technologies also may be used with very little cost penalty as described in this report.

Based on the required investment, a profit of $0.05W appears reasonable. If silicon wafers are available at a price of $20 to 40/M^2, a selling price for these array modules of $0.50 to 0.66/W is projected.

An analysis of the impact of factory size in the 1986 time frame has been made. For a production level of 500 MW/yr, the price above is derived. For comparison, a factory processing 50 MW/yr using the same technology would sell modules for $0.54/W to $0.70/W. An analysis of the impact of wafer size indicates that with traditional metallization and panel designs there is no advantage in increasing wafer size from 3 in. to 5 in., and, in fact, there is some penalty (10% in $/W) due to increased metallization costs and reduced system performance.

There is a premium placed on high efficiency due to its impact, not only on array module cost, but on system cost. For the near-term goals of this program, wafers cut from single-crystal material seem the most likely sheet configuration.

In Section III, an interim 1982 factory is described for the large-scale production of silicon solar-cell array modules. The boundary conditions for this design are the use of Czochralski silicon crystals and $25/kg polycrystalline silicon. The objective is a large-scale production facility to meet an intermediate ERDA cost goal of $2.00/W in 1982.

Our approach was to first consider a panel design which could be expected to have a 20-year life and would also meet the JPL specification on mechanical, electrical, and environmental stability. Attention was then directed to a cost analysis of the production of the elements comprising this panel. Since it was expected that wafer production would comprise a major fraction of the cost, several cost reduction schemes were considered for the Czochralski pulling and sawing of the wafers. A solar-cell processing sequence was selected on the basis of our previous cost studies and the projected availability of production equipment by 1982. These criteria resulted in the selection of $POCL_3$ gaseous diffusion for junction formation, thick-film Ag screen-printed metallization, spray-on AR coating, and solder reflow interconnect technology.

The economic study was made by computer analysis of the cost elements of these process sequences at production levels ranging from 3 to 100 MW/yr. With the results of this study, a 30-MW/yr factory was designed, and a preliminary floor plan layout is given. We have projected a manufacturing cost of $2.01/W and, including factory overhead and profit, a selling price of $2.41/W.

Section IV describes a 6-month experimental production study of the elements of low-cost solar-cell manufacturing sequences and is an outgrowth of our cost and manufacturing studies. This program consisted of three parts: an experimental production line study of the major variables associated with the fabrication of 3-in.-diameter silicon solar cells; a study of thick-film screen-printed silver metallization; and panel design and assembly development.

The experimental production studies were conducted at RCA's Solid State Division under simulated factory conditions. No automation or advanced handling techniques were used; manual handling by hourly workers with the supervision of one foreman and one engineer was used throughout this production study. Approximately 500 3-in.-diameter solar cells were fabricated

using the three junction-formation technologies of $POCl_3$ gaseous diffusion, spin-on source and diffusion, and ion implantation. The problems encountered, some production yield statistics, and summaries of the performance characteristics of the solar cells made by each junction technique are described.

In the screen-printed metallization studies, commercial inks were evaluated for their impurity content and experiments were conducted to determine their suitability for contacting solar-cell surfaces. A suitable ink was identified and some of the printing and firing variables were determined.

A panel design consisting of a double-glass laminate which is expected to meet JPL specifications on mechanical, electrical, and environmental stability was completed. Preliminary studies of the lamination technology were conducted on small (6 by 6 in.) panels and on two full-size (4 by 4 ft) panels.

SECTION II

GENERAL TECHNOLOGY AND COST ANALYSIS OF LARGE SCALE MANUFACTURING SEQUENCES - 1986 PRICE GOAL

A. INTRODUCTION

The purpose of this study was to assess manufacturing process sequences for silicon solar array modules which could be sold for $0.50/peak W in 1986 assuming a yearly sales volume of 500 MW. The study has identified such process sequences. All of the relevant technologies which exist in the semiconductor manufacturing art have been analyzed in detail. The basic philosophy of this study was to identify those manufacturing processes which had the smallest cost of consumed materials and expense items (defined later) based on this comprehensive analysis. It was assumed that the automation of these low material cost processes would result in the lowest cost array module. This philosophy has not changed.

There have been three levels of cost estimation applied to this task. Estimates of the present day costs for each of the potentially relevant processes were made as described above. For the class of processes which seemed the most attractive from a manufacturing cost point of view, the near term (approximately 5 years for full implementation) costs were developed. Finally, for the most cost-effective sequences, the manufacturing costs in a heavily automated facility were projected. A summary of this work is presented in Fig. 1.

In this report, the most cost-effective manufacturing sequence and panel design are described in detail. Variations on this sequence are also costed out.

In subsection D we discuss the effect of wafer size on manufacturing cost. In most of the cost analysis in this report, 3-in. wafers were used as the sheet material. Factory level overhead costs are developed in subsection E.

B. ARRAY MODULE MANUFACTURING COST

The lowest cost manufacturing process sequence which we have identified is shown in Fig. 2. As can be seen in the figure, the cost for this sequence is $0.264/peak W with 58% of the cost associated with material and expense items.

COST ANALYSIS:PROCESS AND OTHER COST ESTIMATES

PROCESS COST ESTIMATE-$/WATT

ASSUMPTIONS: 0.500 WATTS PER SOLAR CELL AND $ 0.0 FOR 7.8 CM (3") DIAMETER WAFER.
100% YIELD FOR ALL PROCESSES FOLLOWING. ANNUAL PRODUCTION: 50.0 MEGAWATTS.

PAGE	YIELD	ITEM	TECH LEVEL	MAT'L.	D. L.	EXP.	P. OH.	INT.	DEPR.	TOTALS	INVEST
1	99.0%	SYSTEM "2" WAFER CLEANING	EXISTING	0.0	0.009	0.002	0.001	0.000	0.000	0.012	0.002
2	99.0%	SYSTEM "2" WAFER CLEANING	NEAR FUTURE	0.0	0.001	0.001	0.000	0.000	0.000	0.003	0.002
3	99.0%	SC-1 CLEANING	EXISTING	0.0	0.014	0.012	0.005	0.001	0.002	0.034	0.015
4	99.0%	WAFER SCRUBBER	EXISTING	0.0	0.025	0.004	0.005	0.001	0.002	0.037	0.014
5	99.0%	MEGASONIC CLEANING	EXISTING	0.0	0.016	0.007	0.006	0.001	0.002	0.032	0.012
6	95.0%	TEXTURIZING:HYDRAZINE	EXISTING	0.0	0.043	0.059	0.026	0.001	0.002	0.132	0.016
7	95.0%	TEXTURIZING:SODIUM HYDROXIDE	EXISTING	0.0	0.043	0.002	0.026	0.001	0.002	0.075	0.016
8	95.0%	SPIN-ON SOURCE	EXISTING	0.007	0.026	0.000	0.011	0.001	0.001	0.046	0.008
9	95.0%	SPIN-ON SOURCE:1 SIDE	NEAR FUTURE	0.007	0.010	0.000	0.005	0.002	0.002	0.025	0.017
10	95.0%	SPIN-ON SOURCE:2 SIDES	NEAR FUTURE	0.013	0.029	0.001	0.012	0.004	0.006	0.065	0.044
11	95.0%	SPIN-ON SOURCE:2 SIDES+EDGE STOP	NEAR FUTURE	0.013	0.048	0.002	0.020	0.007	0.010	0.100	0.072
12	99.0%	SPRAY-ON SOURCE & BAKE	EXISTING	0.0	0.022	0.005	0.032	0.001	0.001	0.062	0.010
13	98.0%	SCREEN PRINT SOURCE:2 SIDES	NEAR FUTURE	0.013	0.008	0.007	0.007	0.003	0.004	0.042	0.031
14	99.0%	SCREEN PRINT SOURCE:2 SIDES	FUTURE	0.013	0.005	0.007	0.005	0.004	0.006	0.040	0.045
15	99.0%	200 DEG. C. BAKE	EXISTING	0.0	0.019	0.000	0.005	0.000	0.000	0.024	0.000
16	99.0%	200 DEGREE C. OVEN BAKE-2	EXISTING	0.0	0.019	0.000	0.005	0.000	0.000	0.024	0.000
17	98.0%	DIFFUSION	NEAR FUTURE	0.0	0.009	0.002	0.002	0.001	0.003	0.016	0.012
18	98.0%	DIFFUSION:36" WIDE BELT	NEAR FUTURE	0.0	0.008	0.002	0.002	0.001	0.003	0.015	0.012
19	99.0%	DIFFUSION	FUTURE	0.0	0.003	0.002	0.001	0.001	0.003	0.009	0.010
20	99.0%	POCL3 DEPOSITION AND DIFFUSION	EXISTING	0.0	0.016	0.028	0.020	0.003	0.004	0.072	0.031
21	99.0%	POCL3 DEPOSITION AND DIFFUSION	FUTURE	0.0	0.003	0.028	0.001	0.001	0.001	0.033	0.006
22	99.0%	DOPED OXIDE DEPOSITION:P TYPE	EXISTING	0.0	0.028	0.040	0.019	0.005	0.008	0.100	0.057
23	99.0%	DOPED OXIDE DEPOSITION:N TYPE	EXISTING	0.0	0.028	0.040	0.019	0.005	0.008	0.100	0.057
24	98.0%	DOPED OXIDE DEPOSITION:2 SIDES	EXISTING	0.0	0.057	0.081	0.039	0.011	0.017	0.205	0.120
25	85.0%	CLOSE SPACE EPITAXY	NEAR FUTURE	0.0	0.068	0.258	0.020	0.026	0.042	0.415	0.294
26	99.0%	ION IMPLANTATION-FRONT	EXISTING	0.0	0.045	0.024	0.042	0.033	0.053	0.197	0.370
27	99.0%	ION IMPLANTATION-BACK	EXISTING	0.0	0.045	0.024	0.042	0.033	0.053	0.197	0.370
28	96.0%	ION IMPLANTATION:2 SIDES	NEAR FUTURE	0.0	0.010	0.011	0.009	0.013	0.021	0.066	0.150
29	99.0%	ION IMPLANTATION:2 SIDES	FUTURE	0.0	0.004	0.007	0.002	0.010	0.016	0.039	0.112
30	99.0%	POST DIFFUSION INSPECTION	EXISTING	0.0	0.015	0.000	0.005	0.003	0.005	0.028	0.033
31	99.0%	POST DIFFUSION INSPECTION	NEAR FUTURE	0.0	0.004	0.000	0.003	0.003	0.005	0.015	0.033
32	99.0%	POST DIFFUSION INSPECTION:10%	FUTURE	0.0	0.001	0.000	0.001	0.001	0.001	0.003	0.006
33	99.0%	FRONT SIDE RESIST APPLICATION	EXISTING	0.0	0.006	0.071	0.014	0.002	0.003	0.096	0.019
34	99.0%	RESIST REMOVAL	EXISTING	0.0	0.005	0.009	0.005	0.001	0.001	0.021	0.007
35	95.0%	GLASS REMOVAL	EXISTING	0.0	0.007	0.001	0.002	0.001	0.001	0.012	0.006
36	99.0%	GLASS REMOVAL	NEAR FUTURE	0.0	0.002	0.001	0.001	0.000	0.001	0.005	0.005
37	95.0%	PIM ETCH	EXISTING	0.0	0.012	0.034	0.013	0.002	0.003	0.064	0.020
38	95.0%	EDGE POLISH	NEAR FUTURE	0.0	0.002	0.004	0.001	0.000	0.001	0.008	0.005
39	100.0%	VACUUM EVAPORATION METALLIZATION	EXISTING	0.0	0.173	0.011	0.070	0.020	0.032	0.307	0.227
40	98.0%	TI/AG METALLIZATION-FRONT	EXISTING	0.019	0.177	0.011	0.072	0.024	0.039	0.342	0.271
41	98.0%	TI/AG METALLIZATION-BACK	EXISTING	0.022	0.177	0.011	0.072	0.024	0.039	0.345	0.271
42	98.0%	AL METALLIZATION-FRONT	EXISTING	0.004	0.177	0.011	0.072	0.021	0.033	0.318	0.232
43	98.0%	AL METALLIZATION-BACK	EXISTING	0.004	0.177	0.011	0.072	0.021	0.033	0.318	0.232
44	98.0%	MAGNETRON SPUTTERING TI/AG:FRONT	EXISTING	0.019	0.037	0.009	0.013	0.018	0.028	0.123	0.195
45	98.0%	MAGNETRON SPUTTERING TI/AG:BACK	EXISTING	0.022	0.037	0.009	0.013	0.018	0.028	0.126	0.195
46	98.0%	MAGNETRON SPUTTERING AL:FRONT	EXISTING	0.007	0.037	0.009	0.013	0.020	0.031	0.116	0.217
47	98.0%	MAGNETRON SPUTTERING AL:BACK	EXISTING	0.007	0.037	0.009	0.013	0.020	0.031	0.116	0.217
48	100.0%	SCREEN PRINT WAFER REWORK	NEAR FUTURE	0.0	0.001	0.000	0.001	0.000	0.000	0.002	0.001
49	100.0%	SCREEN PRINT WAFER REWORK	FUTURE	0.0	0.001	0.000	0.001	0.000	0.000	0.002	0.001
50	98.0%	THICK AG METAL-BACK:AUTO	NEAR FUTURE	0.026	0.004	0.005	0.006	0.003	0.005	0.049	0.035
51	99.0%	THICK AG METAL-BACK:AUTO	FUTURE	0.026	0.002	0.005	0.003	0.004	0.007	0.047	0.048
52	98.0%	THICK AG METAL-FRONT:AUTO	NEAR FUTURE	0.027	0.010	0.012	0.013	0.006	0.010	0.078	0.069
53	99.0%	THICK AG METAL-FRONT:AUTO	FUTURE	0.026	0.006	0.012	0.006	0.008	0.012	0.070	0.087
54	98.0%	THICK AL/AG METAL-BACK:AUTO	NEAR FUTURE	0.015	0.008	0.010	0.009	0.004	0.007	0.053	0.050
55	98.0%	THICK AL METAL-BACK:AUTO	NEAR FUTURE	0.011	0.004	0.005	0.006	0.003	0.005	0.034	0.035
56	98.0%	THICK AL METAL-FRONT:AUTO	NEAR FUTURE	0.012	0.010	0.012	0.013	0.006	0.010	0.063	0.069
57	95.0%	AR COATING:SPIN-ON	EXISTING	0.021	0.049	0.001	0.018	0.001	0.001	0.091	0.008
58	95.0%	AR COATING:SPIN-ON	NEAR FUTURE	0.021	0.019	0.001	0.007	0.002	0.004	0.053	0.025
59	98.0%	AR COATING:SPIN-ON	FUTURE	0.020	0.010	0.001	0.004	0.003	0.005	0.042	0.034
60	99.0%	AR COATING:SPRAY-ON	NEAR FUTURE	0.002	0.004	0.000	0.001	0.001	0.001	0.009	0.008
61	99.0%	AR COATING:EVAPORATE	EXISTING	0.010	0.070	0.006	0.035	0.011	0.018	0.150	0.128
62	80.0%	TEST	EXISTING	0.0	0.022	0.000	0.007	0.005	0.008	0.042	0.056
63	80.0%	TEST	NEAR FUTURE	0.0	0.005	0.000	0.005	0.005	0.008	0.023	0.056
64	90.0%	TEST	FUTURE	0.0	0.004	0.000	0.002	0.004	0.007	0.017	0.049
65	96.0%	ARRAY FAB.:RS:ACRYLIC PANEL,CB	EXISTING	0.359	0.158	0.066	0.048	0.010	0.016	0.657	0.109
66	96.0%	ARRAY FAB.:RS:GLASS SUPERSTRATE	EXISTING	0.152	0.158	0.066	0.048	0.010	0.016	0.450	0.109
67	96.0%	ARRAY FAB.:GW:ACRYLIC PANEL,CB	EXISTING	0.382	0.125	0.000	0.045	0.009	0.014	0.575	0.096
68	96.0%	ARRAY FAB.:GW:GLASS SUPERSTRATE	EXISTING	0.152	0.125	0.009	0.045	0.009	0.014	0.353	0.096
69	96.0%	ARRAY FAB.:ULS:ACRYLIC PANEL,CB	EXISTING	0.378	0.125	0.000	0.045	0.010	0.015	0.574	0.107
70	96.0%	ARRAY FAB.:ULS:GLASS SUPERSTRATE	EXISTING	0.156	0.125	0.000	0.045	0.010	0.015	0.352	0.107
71	98.0%	INTERCONNECT:REFLOW SOLDER	NEAR FUTURE	0.003	0.008	0.000	0.002	0.002	0.004	0.019	0.025
72	98.0%	INTERCONNECT:GAP WELDING	NEAR FUTURE	0.003	0.008	0.003	0.002	0.002	0.004	0.022	0.025
73	98.0%	INTERCONNECT:ULTRASONIC	NEAR FUTURE	0.003	0.013	0.000	0.003	0.002	0.004	0.025	0.025
74	100.0%	DOUBLE GLASS PANEL ASSEMBLY	NEAR FUTURE	0.103	0.003	0.003	0.001	0.002	0.003	0.114	0.018
75	100.0%	GLASS SUPERSTRATE PANEL ASSEMBLY	NEAR FUTURE	0.150	0.003	0.000	0.001	0.002	0.003	0.159	0.018
76	100.0%	RIBBON IN TUBES PANEL ASSEMBLY	NEAR FUTURE	0.140	0.003	0.000	0.001	0.002	0.003	0.148	0.018
77	100.0%	ARRAY MODULE PACKAGING	EXISTING	0.010	0.003	0.0	0.000	0.000	0.000	0.014	0.001

Figure 1. Cost analysis summary.

ION IMPLANTATION (C)

ASSUMPTIONS: 0.717 WATTS PER SOLAR CELL AND $0.0 FOR 7.8 CM (3") DIAMETER WAFER

STEP	YIELD (%)	PROCESS		MAT'L.	EXP.	LABOR +O.H.	INT.+ DEPR.	TOTALS	INVEST
1	99.0	SYSTEM "Z" WAFER CLEANING	(B)	0.0	0.001	0.001	0.000	0.003	0.002
2	99.0	ION IMPLANTATION:2 SIDES	(C)	0.0	0.005	0.004	0.020	0.029	0.084
3	99.0	DIFFUSION	(C)	0.0	0.002	0.004	0.003	0.009	0.010
4	99.0	POST DIFFUSION INSPECTION 10%	(C)	0.0	0.000	0.000	0.000	0.001	0.003
5	99.0	THICK AG METAL-BACK:AUTO	(C)	0.021	0.004	0.004	0.008	0.041	0.037
6	99.0	THICK AG METAL-FRONT:AUTO	(C)	0.021	0.009	0.010	0.016	0.060	0.069
7	90.0	TEST	(C)	0.0	0.000	0.004	0.008	0.012	0.035
8	99.0	AR COATINGS:SPRAY-ON	(C)	0.002	0.002	0.005	0.002	0.011	0.008
9	98.0	INTERCONNECT:GAP WELDING	(B)	0.002	0.002	0.008	0.005	0.016	0.019
10	100.0	DOUBLE GLASS PANEL ASSEMBLY	(B)	0.072	0.002	0.003	0.003	0.080	0.014
11	100.0	ARRAY MODULE PACKAGING	(A)	0.007	0.0	0.001	0.000	0.009	0.000
	82.2	TOTALS		0.124	0.027	0.046	0.066	0.264	0.282
			%	47.22	10.35	17.12	25.31		

Figure 2. Ion implantation cost analysis.

This process sequence is identified as Ion Implantation (C) where the (C) denotes a heavily automated extrapolation of a near-future version, Ion Implantation (B), which will be evaluated later.

In the three class (C) cases which will be described, all of the machinery is fully automated and only the interfaces between each step involve people. The sheets, in this case 3-in. wafers, are transported between each step in 500-wafer cassettes. As will be shown below, additional people are involved in maintenance, support, and administrative functions.

As can be seen in Fig. 3, the factory on which these cost estimates are based produces 50 MW/year and operates 345 days/year. At this level of production, there is only a slight projectable advantage in increasing the factory size (subsection E). Ten such factories will produce 500 MW/year.

For understanding Fig. 2, Fig. 4 is a listing of all the material and expense items which have appeared during the entire analysis. As a rule, those

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YEARS OF STUDY: 1 RUN TYPE:PRO-FORMA BASE YEAR OF RUN: 1

ANNUAL PRODUCTION IN WATTS: 5.00000E+07 PRODUCTION GROWTH PROFILE #: 0

2ND SHIFT PREMIUM:10.00% 3RD SHIFT PREMIUM:10.00%
WORKING DAYS/YR:345 # HOURS/SHIFT:12.00 # SHIFTS/DAY: 2

BOOK DEPRECIATION METHOD:SL TAX DEPRECIATION METHOD:SYD

FACTORY CONSTRUCTION COST,$/FT**2: 0.0 FACTORY DEPRECIATION LIFE-BOOK: 20 TAX: 20 INVESTMENT TAX CREDIT:YES
LAND COST,$/FT**2 OF FACTORY: 0.0 (NOT A DEPRECIABLE INVESTMENT) FACTORY EXCESS SPACE-1ST YR: 0.0%

INVESTMENT TAX CREDIT RATE: 10.00% INTEREST RATE ON DEBT: 9.00% INTEREST RATE GROWTH PROFILE #: 0
DEBT RATIO-INITIAL YEAR: 100.00%

PURCHASED SILICON COST: 0. $/SHEET. SILICON COST GROWTH PROFILE #: 0
SOLAR CELLS/SHEET: 1 # SOLAR CELLS/ARRAY MODULE: 224 AREA OF ARRAY MODULE:13564.0CM**2
WATTS PER SOLAR CELL(DEFAULT): 0.50 WATTS PER SOLAR CELL GROWTH PROFILE #: 0

WT. OF SHEET: 3.960 GRAMS. AREA OF SHEET: 47.800CM**2 FORM:3" WAFER.
DEFINITION OF SHEET:7.8 CM (3") DIAMETER WAFER

GENERAL INPUTS:LABOR TYPE DEFINITIONS 01/20/77 16:15:43 PAGE 5

LABOR NAME	LABOR TYPE	WAGE RATE	GP#	FRINGE BENEFITS	GP#	EFFICIENCY
HOURLY OPERATOR	DIRECT	5.00$/HR	0	35.0%	0	85.0%
REWORK OPERATOR	DIRECT	5.00$/HR	0	35.0%	0	85.0%
HOURLY INSPECTOR	DIRECT	5.00$/HR	0	35.0%	0	85.0%
MACH. ATTENDANT	INDIRECT	5.60$/HR	0	35.0%	0	85.0%
FOREMAN	INDIRECT	7.65$/HR	0	35.0%	0	100.0%
ENGR. SUPPORT	INDIRECT	11.75$/HR	0	35.0%	0	100.0%
TECHNICIAN	INDIRECT	7.15$/HR	0	35.0%	0	100.0%
CLERICAL	INDIRECT	5.10$/HR	0	35.0%	0	100.0%
QUALITY CONTROL	INDIRECT	5.60$/HR	0	35.0%	0	100.0%
MAINTENANCE	INDIRECT	5.10$/HR	0	35.0%	0	100.0%
HANDLER	INDIRECT	5.10$/HR	0	35.0%	0	100.0%

Figure 3. Factory production analysis.

GENERAL INPUTS:EXPENSE TYPE DEFINITIONS 01/20/77 16:15:43 PAGE 6

EXPENSE NAME	RESTRICTION	TYPE	COST	GP#	SALVAGE	SALVAGE VALUE	GP#
AG-PLATED CU WIRE	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
AL CHANNEL	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
ALUMINUM	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
ALUMINUM RIBBON	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
AL FOIL SUBSTRATE	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
BOX FOR MODULE	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
CELL ADHESIVE	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
CONFORMAL COAT+5 MIL METAL	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
EDGE SEAL	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
END CAPS	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
EPOXY SPACER	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
EXTENDED HEAT SINK	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
FINAL ASSEMBLY MATERIAL	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
GLASS TUBING	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
INDEX MATCHING MATERIAL	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
IN-HOUSE SPIN-ON AR COATING	NONE	MATERIAL	1.00000E-02$/CM**3	0	0.0%	0.0 $/CM**3	0
IN-HOUSE PASTE SOURCE	NONE	MATERIAL	4.00000E-03$/CM**3	0	0.0%	0.0 $/CM**3	0
IN-HOUSE SPIN-ON SOURCE	NONE	MATERIAL	4.00000E-03$/CM**3	0	0.0%	0.0 $/CM**3	0
INK AG-FRONT FINE GRID	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
INK AG-FRONT FINE GRID LOST	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
INK AG-FRONT BUS BAR	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
INK AG-FRONT BUS BAR LOST	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
INK AG-BACK GRID	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
INK AG-BACK GRID LOST	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
INK AG-BACK PAD	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
INK AG-BACK PAD LOST	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
INK AL-FRONT FINE GRID	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
INK AL-FRONT FINE GRID LOST	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
INK AL-FRONT BUS BAR	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
INK AL-FRONT BUS BAR LOST	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
INK AL-BACK GRID	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
INK AL-BACK GRID LOST	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
INTERCONNECT MATERIAL	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
INTERCONNECT METAL	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
PANEL ASSEMBLY MATERIAL	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
PANEL CONNECTOR	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
SILVER	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
SUBSTRATE	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
TANTALUM PENTOXIDE	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
TITANIUM	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
WINDOW	NONE	MATERIAL	SPECIFIED IN $	0	0.0%	$ 0.0	0
ACETIC ACID	NONE	DIRECT EXP.	1.72200E-03$/GM.	0			
AMMONIA GAS	NONE	DIRECT EXP.	5.50000E-06$/CM**3	0			
AMMONIUM HYDROXIDE	NONE	DIRECT EXP.	8.90000E-04$/CM**3	0			
BOATS,LINERS,ETC.	NONE	DIRECT EXP.	SPECIFIED IN $	0			
DEVELOPER	NONE	DIRECT EXP.	SPECIFIED IN $	0			
DETERGENT	NONE	DIRECT EXP.	0.0 $/GM.	0			
DE-IONIZED WATER	NONE	DIRECT EXP.	1.06000E-06$/CM**3	0			
DIAMOND BLADES,ETC.	NONE	DIRECT EXP.	SPECIFIED IN $	0			
DIBORANE 5% IN HYDROGEN	NONE	DIRECT EXP.	2.82700E-05$/CM**3	0			
ELECTRICITY	NONE	DIRECT EXP.	3.00000E-02$/KWH	0			
ELECTRODES	NONE	DIRECT EXP.	SPECIFIED IN $	0			
FILAMENTS/INSULATORS	NONE	DIRECT EXP.	SPECIFIED IN $	0			
FILTERS	NONE	DIRECT EXP.	SPECIFIED IN $	0			

Figure 4. Material and expense definition.

GENERAL INPUTS:EXPENSE TYPE DEFINITIONS 01/20/77 16:15:43 PAGE 6.1

EXPENSE NAME	RESTRICTION	TYPE	COST	GP#	SALVAGE	SALVAGE VALUE	GP#
HYDRAZINE	NONE	DIRECT EXP.	1.23000E-01$/GM.	0			
HYDROCHLORIC ACID	NONE	DIRECT EXP.	8.36000E-04$/GM.	0			
HYDROFLUORIC ACID	NONE	DIRECT EXP.	1.23000E-03$/CM**3	0			
HYDROGEN	NONE	DIRECT EXP.	2.65000E-07$/CM**3	0			
HYDROGEN CHLORIDE	NONE	DIRECT EXP.	6.60000E-03$/CM**3	0			
HYDROGEN PEROXIDE	NONE	DIRECT EXP.	1.14000E-03$/CM**3	0			
ION SOURCE GAS	NONE	DIRECT EXP.	SPECIFIED IN $	0			
LIME	NONE	DIRECT EXP.	4.65000E-05$/GM.	0			
LIQUID NITROGEN	NONE	DIRECT EXP.	7.50000E-05$/CM**3	0			
NITRIC ACID	NONE	DIRECT EXP.	1.03400E-03$/GM.	0			
NITROCELLULOSE LACQUER	NONE	DIRECT EXP.	1.50000E-03$/CM**3	0			
NITROGEN	NONE	DIRECT EXP.	4.77000E-08$/CM**3	0			
NITROGEN AMBIENT	NONE	DIRECT EXP.	4.77000E-08$/CM**3	0			
NITROGEN CURTAINS	NONE	DIRECT EXP.	4.77000E-08$/CM**3	0			
O-RINGS & FILTERS	NONE	DIRECT EXP.	SPECIFIED IN $	0			
OUTSIDE ENGR. SERVICES	NONE	DIRECT EXP.	SPECIFIED IN $	0			
OXYGEN	NONE	DIRECT EXP.	1.84000E-07$/CM**3	0			
PHOSPHINE 5% IN HYDROGEN	NONE	DIRECT EXP.	2.88000E-05$/CM**3	0			
PHOSPHORUS OXYCHLORIDE	NONE	DIRECT EXP.	2.04000E-02$/GM.	0			
PHOTORESIST	NONE	DIRECT EXP.	SPECIFIED IN $	0			
QUARTZ	NONE	DIRECT EXP.	SPECIFIED IN $	0			
SCREENS	NONE	DIRECT EXP.	SPECIFIED IN $	0			
SILANE 100%	NONE	DIRECT EXP.	4.04000E-01$/GM.	0			
SILICON TETRACHLORIDE	NONE	DIRECT EXP.	5.72000E-03$/GM.	0			
SODIUM HYDROXIDE	NONE	DIRECT EXP.	3.77000E-05$/GM.	0			
SOLVENT	NONE	DIRECT EXP.	SPECIFIED IN $	0			
SOLVENT-INK	NONE	DIRECT EXP.	5.27700E-04$/CM**3	0			
SOLVENT-PASTE	NONE	DIRECT EXP.	5.27700E-04$/CM**3	0			
SPRAY-ON SOURCE	NONE	DIRECT EXP.	SPECIFIED IN $	0			
SQUEEGEES	NONE	DIRECT EXP.	SPECIFIED IN $	0			
SULFURIC ACID	NONE	DIRECT EXP.	6.82000E-04$/GM.	0			
THERMOCCUPLE,ETC.	NONE	DIRECT EXP.	SPECIFIED IN $	0			
SUSCEPTORS	NONE	DIRECT EXP.	SPECIFIED IN $	0			
TRANSDUCERS & TUBES	NONE	DIRECT EXP.	SPECIFIED IN $	0			
TRICHLOROSILANE	NONE	DIRECT EXP.	1.98000E-03$/GM.	0			
WATER-COOLING	NONE	DIRECT EXP.	2.00000E-07$/CM**3	0			

Figure 4. Continued.

materials which become part of the finished array module are considered "material" and those which are used up during the process sequence are considered "expense."

Figures 5 through 10 are the remaining cost summaries for the class B and class C process sequences which are considered the most cost-effective.

Figure 11 is a comparison of the three class (C) process sequences; Ion Implantation (C), Spin-On + $POCl_3$ Diffusion (C), and Screen Print 2 Sides (C). All of the processes in these three cases are the same except for the junction-formation technique. In Spin-On + $POCl_3$ Diffusion (C), the back of the wafer is doped with a spin-on source during a $POCl_3$ diffusion of the front junction. In Screen Print 2 Sides (C), an appropriate source paste is screened onto each side of the wafer and the wafer doped in a subsequent diffusion step. The purpose of this figure is to emphasize that several cost-effective junction-formation processes are available. Performance penalties which may be experienced with the nonstandard processes such as screened-on doping sources are not considered in this cost analysis.

It is the purpose of this analysis to provide guidance as to which technologies should be developed; it suggests ion implantation and screened-on doping sources are technologies worthy of further investigation.

Figure 12 is a cost comparison of these same technologies as we have evaluated them in a near-future context. Two factors result in lower cost in the automated line. First is a direct reduction in labor and process overhead. Second, the overall yield has increased from 65% to 80%. A detailed evaluation of the capital costs shows an actual reduction (slight) in the automated case due to substantially higher throughput for the fully automated equipment.

C. DETAILED COST ESTIMATE FOR ION IMPLANTATION (C)

Because it is the lowest cost sequence, a complete description of Ion Implantation (C) will be given. Recall that except for the junction-formation technology, this sequence is identical to the other two recommended class (C) process sequences.

1. Solar Panel Design

The single largest cost component in the assembly of a solar cell panel is the material required to provide structural and environmental projection

COST ANALYSIS:CASE II:SPIN-ON +POCL3 DIFFUSION(C) 02/03/77 13:09:18 PAGE 1

PROCESS COST OVERVIEW-$/WATT

ASSUMPTIONS: 0.717 WATTS PER SOLAR CELL AND $ 0.0 FOR 7.8 CM (3") DIAMETER WAFER

STEP	YIELD	PROCESS		MAT'L.	D. L.	EXP.	P. OH.	INT.	DEPR.	SUBTOT	SALVG.	TOTALS	%	INVEST	%
1	99.0%	SYSTEM "Z" WAFER CLEANING	(B)	0.0	0.001	0.001	0.000	0.000	0.000	0.003	0.0	0.003	1.2	0.002	0.8
2	95.0%	SPIN-ON SOURCE:1 SIDE	(B)	0.006	0.009	0.000	0.004	0.001	0.002	0.022	0.0	0.022	7.8	0.015	7.0
3	99.0%	POCL3 DEPOSITION AND DIFFUSION	(C)	0.0	0.003	0.024	0.001	0.001	0.001	0.030	0.0	0.030	10.3	0.006	2.7
4	95.0%	EDGE POLISH	(B)	0.0	0.002	0.004	0.001	0.000	0.001	0.007	0.0	0.007	2.5	0.005	2.5
5	99.0%	GLASS REMOVAL	(B)	0.0	0.001	0.001	0.000	0.000	0.000	0.003	0.0	0.003	1.1	0.003	1.5
6	99.0%	POST DIFFUSION INSPECTION:10%	(C)	0.0	0.000	0.000	0.000	0.000	0.000	0.001	0.0	0.001	0.5	0.003	1.4
7	99.0%	THICK AG METAL-FRONT:AUTO	(C)	0.021	0.005	0.009	0.005	0.006	0.010	0.056	0.0	0.056	19.4	0.069	31.7
8	99.0%	THICK AG METAL-BACK:AUTO	(C)	0.021	0.002	0.004	0.002	0.003	0.005	0.037	0.0	0.037	12.9	0.037	17.1
9	99.0%	AR COATING:SPRAY-ON	(B)	0.002	0.004	0.002	0.001	0.001	0.001	0.011	0.0	0.011	3.6	0.008	3.9
10	90.0%	TEST	(C)	0.0	0.003	0.000	0.001	0.003	0.005	0.012	0.0	0.012	4.2	0.035	16.1
11	98.0%	INTERCONNECT:GAP WELDING	(B)	0.002	0.006	0.002	0.002	0.002	0.003	0.016	0.0	0.016	5.6	0.019	8.9
12	100.0%	DOUBLE GLASS PANEL ASSEMBLY	(B)	0.072	0.002	0.002	0.001	0.001	0.002	0.080	0.0	0.080	27.7	0.014	6.3
13	100.0%	ARRAY MODULE PACKAGING	(A)	0.007	0.001	0.0	0.000	0.000	0.000	0.009	0.0	0.009	3.1	0.000	0.2
	74.2%	TOTALS		0.130	0.039	0.049	0.019	0.020	0.031	0.289	0.0	0.289	100.0	0.218	100.0
			%	45.18	13.52	17.12	6.64	6.78	10.76	100.00					

NOTE: (A)=EXISTING TECHNOLOGY; (B)=NEAR FUTURE; (C)=FUTURE ANNUAL PRODUCTION: 50.0 MEGAWATTS.

Figure 5. Cost summary - spin-on + $POCl_3$ diffusion (C).

COST ANALYSIS:CASE IV:SCREEN PRINT 2 SIDES(C) 02/03/77 13:09:18 PAGE 1

PROCESS COST OVERVIEW-$/WATT

ASSUMPTIONS: 0.717 WATTS PER SOLAR CELL AND $ 0.0 FOR 7.8 CM (3") DIAMETER WAFER

STEP	YIELD	PROCESS		MAT'L.	D. L.	EXP.	P. OH.	INT.	DEPR.	SUBTOT	SALVG.	TOTALS	%	INVEST	%
1	99.0%	SYSTEM "Z" WAFER CLEANING	(B)	0.0	0.001	0.001	0.000	0.000	0.000	0.003	0.0	0.003	1.2	0.002	0.7
2	99.0%	SCREEN PRINT SOURCE:2 SIDES	(C)	0.011	0.004	0.006	0.004	0.004	0.006	0.035	0.0	0.035	12.8	0.040	16.6
3	99.0%	DIFFUSION	(C)	0.0	0.003	0.002	0.001	0.001	0.002	0.009	0.0	0.009	3.2	0.010	4.1
4	99.0%	GLASS REMOVAL	(B)	0.0	0.001	0.001	0.000	0.000	0.000	0.003	0.0	0.003	1.2	0.003	1.3
5	99.0%	POST DIFFUSION INSPECTION:10%	(C)	0.0	0.000	0.000	0.000	0.000	0.000	0.001	0.0	0.001	0.5	0.003	1.2
6	99.0%	THICK AG METAL-BACK:AUTO	(C)	0.021	0.002	0.004	0.002	0.003	0.005	0.038	0.0	0.038	13.8	0.037	15.4
7	99.0%	THICK AG METAL-FRONT:AUTO	(C)	0.021	0.005	0.009	0.005	0.006	0.010	0.056	0.0	0.056	20.5	0.069	28.6
8	99.0%	AR COATING:SPRAY-ON	(B)	0.002	0.004	0.002	0.001	0.001	0.001	0.011	0.0	0.011	3.9	0.008	3.5
9	90.0%	TEST	(C)	0.0	0.003	0.000	0.001	0.003	0.005	0.012	0.0	0.012	4.5	0.035	14.5
10	98.0%	INTERCONNECT:GAP WELDING	(B)	0.002	0.006	0.002	0.002	0.002	0.003	0.016	0.0	0.016	5.9	0.019	8.1
11	100.0%	DOUBLE GLASS PANEL ASSEMBLY	(B)	0.072	0.002	0.002	0.001	0.001	0.002	0.080	0.0	0.080	29.2	0.014	5.7
12	100.0%	ARRAY MODULE PACKAGING	(A)	0.007	0.001	0.0	0.000	0.000	0.000	0.009	0.0	0.009	3.3	0.000	0.2
	81.4%	TOTALS		0.135	0.033	0.029	0.018	0.022	0.035	0.273	0.0	0.273	100.0	0.241	100.0
			%	49.58	12.11	10.68	6.68	7.95	13.00	100.00					

NOTE: (A)=EXISTING TECHNOLOGY; (B)=NEAR FUTURE; (C)=FUTURE ANNUAL PRODUCTION: 50.0 MEGAWATTS.

Figure 6. Cost summary - screen print 2 sides (C).

COST ANALYSIS:CASE I:ION IMPLANTATION(B) 02/03/77 13:09:18 PAGE 1

PROCESS COST OVERVIEW-$/WATT

ASSUMPTIONS: 0.717 WATTS PER SOLAR CELL AND $ 0.0 FOR 7.8 CM (3") DIAMETER WAFER

STEP	YIELD	PROCESS		MAT'L.	D. L.	EXP.	P. OH.	INT.	DEPR.	SUBTOT	SALVG.	TOTALS	%	INVEST	%
1	99.0%	SYSTEM "Z" WAFER CLEANING	(B)	0.0	0.001	0.001	0.000	0.000	0.000	0.003	0.0	0.003	1.0	0.002	0.5
2	98.0%	ION IMPLANTATION:2 SIDES	(B)	0.0	0.010	0.010	0.009	0.013	0.020	0.061	0.0	0.061	17.9	0.140	38.8
3	98.0%	DIFFUSION	(B)	0.0	0.009	0.002	0.002	0.001	0.003	0.016	0.0	0.016	4.8	0.012	3.3
4	99.0%	POST DIFFUSION INSPECTION	(B)	0.0	0.003	0.000	0.003	0.003	0.004	0.013	0.0	0.013	3.9	0.030	8.3
5	98.0%	THICK AG METAL-BACK:AUTO	(B)	0.024	0.004	0.005	0.005	0.003	0.004	0.045	0.0	0.045	13.0	0.031	8.6
6	98.0%	THICK AG METAL-FRONT:AUTO	(B)	0.024	0.009	0.011	0.012	0.006	0.009	0.070	0.0	0.070	20.5	0.062	17.2
7	99.0%	AR COATING:SPRAY-ON	(B)	0.002	0.004	0.002	0.001	0.001	0.001	0.011	0.0	0.011	3.1	0.008	2.3
8	80.0%	TEST	(B)	0.0	0.004	0.000	0.003	0.004	0.006	0.018	0.0	0.018	5.1	0.042	11.6
9	98.0%	INTERCONNECT:GAP WELDING	(B)	0.002	0.006	0.002	0.002	0.002	0.003	0.016	0.0	0.016	4.7	0.019	5.4
10	100.0%	DOUBLE GLASS PANEL ASSEMBLY	(B)	0.072	0.002	0.002	0.001	0.001	0.002	0.080	0.0	0.080	23.3	0.014	3.8
11	100.0%	ARRAY MODULE PACKAGING	(A)	0.007	0.001	0.0	0.000	0.000	0.000	0.009	0.0	0.009	2.6	0.000	0.1
	70.2%	TOTALS		0.131	0.053	0.035	0.038	0.032	0.053	0.343	0.0	0.343	100.0	0.361	100.0
			%	38.21	15.54	10.31	11.09	9.48	15.36	100.00					

NOTE: (A)=EXISTING TECHNOLOGY; (B)=NEAR FUTURE; (C)=FUTURE ANNUAL PRODUCTION: 50.0 MEGAWATTS.

Figure 7. Cost summary - ion implantation.

COST ANALYSIS:CASE II:SPIN-ON +POCL3 DIFFUSION(B) 02/03/77 13:09:18 PAGE 1

PROCESS COST OVERVIEW-$/WATT

ASSUMPTIONS: 0.717 WATTS PER SOLAR CELL AND $ 0.0 FOR 7.8 CM (3") DIAMETER WAFER

STEP	YIELD	PROCESS		MAT'L.	D. L.	EXP.	P. OH.	INT.	DEPR.	SUBTOT	SALVG.	TOTALS	%	INVEST	%
1	99.0%	SYSTEM "Z" WAFER CLEANING	(B)	0.0	0.002	0.002	0.000	0.000	0.000	0.005	0.0	0.005	1.3	0.003	1.0
2	95.0%	SPIN-ON SOURCE:1 SIDE	(B)	0.007	0.010	0.000	0.005	0.002	0.003	0.026	0.0	0.026	6.9	0.018	6.5
3	99.0%	POCL3 DEPOSITION AND DIFFUSION	(A)	0.0	0.017	0.028	0.021	0.003	0.004	0.073	0.0	0.073	19.3	0.031	11.6
4	95.0%	EDGE POLISH	(B)	0.0	0.002	0.004	0.001	0.000	0.001	0.008	0.0	0.008	2.0	0.005	2.0
5	99.0%	GLASS REMOVAL	(B)	0.0	0.002	0.001	0.001	0.000	0.001	0.005	0.0	0.005	1.3	0.005	1.8
6	99.0%	POST DIFFUSION INSPECTION	(B)	0.0	0.003	0.000	0.003	0.003	0.004	0.013	0.0	0.013	3.6	0.030	11.1
7	98.0%	THICK AG METAL-FRONT:AUTO	(B)	0.025	0.009	0.011	0.012	0.006	0.009	0.071	0.0	0.071	18.7	0.062	23.1
8	98.0%	THICK AG METAL-BACK:AUTO	(B)	0.024	0.004	0.005	0.005	0.003	0.004	0.044	0.0	0.044	11.6	0.031	11.5
9	99.0%	AR COATING:SPRAY-ON	(B)	0.002	0.004	0.002	0.001	0.001	0.001	0.011	0.0	0.011	2.8	0.008	3.1
10	80.0%	TEST	(B)	0.0	0.004	0.000	0.003	0.004	0.006	0.018	0.0	0.018	4.7	0.042	15.6
11	98.0%	INTERCONNECT:GAP WELDING	(B)	0.002	0.006	0.002	0.002	0.002	0.003	0.016	0.0	0.016	4.3	0.019	7.2
12	100.0%	DOUBLE GLASS PANEL ASSEMBLY	(B)	0.072	0.002	0.002	0.001	0.001	0.002	0.080	0.0	0.080	21.1	0.014	5.1
13	100.0%	ARRAY MODULE PACKAGING	(A)	0.007	0.001	0.0	0.000	0.000	0.000	0.009	0.0	0.009	2.4	0.000	0.2
	64.6%	TOTALS		0.138	0.066	0.057	0.054	0.024	0.038	0.378	0.0	0.378	100.0	0.269	100.0
			%	36.47	17.46	15.11	14.37	6.41	10.18	100.00					

NOTE: (A)=EXISTING TECHNOLOGY; (B)=NEAR FUTURE; (C)=FUTURE ANNUAL PRODUCTION: 50.0 MEGAWATTS.

Figure 8. Cost summary - spin-on + $POCl_3$ diffusion.

COST ANALYSIS:CASE III:SPIN-ON 2 SIDES(B) 02/03/77 13:09:18 PAGE 1

PROCESS COST OVERVIEW-$/WATT

ASSUMPTIONS: 0.717 WATTS PER SOLAR CELL AND $ 0.0 FOR 7.8 CM (3") DIAMETER WAFER

STEP	YIELD	PROCESS		MAT'L.	D. L.	EXP.	P. OH.	INT.	DEPR.	SUBTOT	SALVG.	TOTALS	%	INVEST	%
1	99.0%	SYSTEM "Z" WAFER CLEANING	(B)	0.0	0.002	0.002	0.000	0.000	0.000	0.005	0.0	0.005	1.3	0.003	1.0
2	95.0%	SPIN-ON SOURCE:2 SIDES	(B)	0.014	0.030	0.001	0.012	0.004	0.007	0.068	0.0	0.068	18.6	0.046	16.4
3	98.0%	DIFFUSION	(B)	0.0	0.009	0.002	0.002	0.001	0.003	0.016	0.0	0.016	4.5	0.012	4.3
4	95.0%	EDGE POLISH	(B)	0.0	0.002	0.004	0.001	0.000	0.001	0.008	0.0	0.008	2.1	0.005	1.9
5	99.0%	GLASS REMOVAL	(B)	0.0	0.002	0.001	0.001	0.000	0.001	0.005	0.0	0.005	1.3	0.005	1.7
6	99.0%	POST DIFFUSION INSPECTION	(B)	0.0	0.003	0.000	0.003	0.003	0.004	0.013	0.0	0.013	3.7	0.030	10.8
7	98.0%	THICK AG METAL-BACK:AUTO	(B)	0.024	0.004	0.005	0.005	0.003	0.004	0.045	0.0	0.045	12.3	0.031	11.2
8	98.0%	THICK AG METAL-FRONT:AUTO	(B)	0.024	0.009	0.011	0.012	0.006	0.009	0.070	0.0	0.070	19.4	0.062	22.4
9	99.0%	AR COATING:SPRAY-ON	(B)	0.002	0.004	0.002	0.001	0.001	0.001	0.011	0.0	0.011	3.0	0.008	3.0
10	80.0%	TEST	(B)	0.0	0.004	0.000	0.003	0.004	0.006	0.018	0.0	0.018	4.8	0.042	15.1
11	98.0%	INTERCONNECT:GAP WELDING	(B)	0.002	0.006	0.002	0.002	0.002	0.003	0.016	0.0	0.016	4.5	0.019	7.0
12	100.0%	DOUBLE GLASS PANEL ASSEMBLY	(B)	0.072	0.002	0.002	0.001	0.001	0.002	0.080	0.0	0.080	22.0	0.014	4.9
13	100.0%	ARRAY MODULE PACKAGING	(A)	0.007	0.001	0.0	0.000	0.000	0.000	0.009	0.0	0.009	2.5	0.000	0.2
	64.0%	TOTALS		0.145	0.078	0.031	0.043	0.025	0.041	0.363	0.0	0.363	100.0	0.278	100.0
			%	39.87	21.52	8.63	11.87	6.89	11.22	100.00					

NOTE: (A)=EXISTING TECHNOLOGY; (B)=NEAR FUTURE; (C)=FUTURE ANNUAL PRODUCTION: 50.0 MEGAWATTS.

Figure 9. Cost summary - spin-on 2 sides.

COST ANALYSIS:CASE IV:SCREEN PRINT 2 SIDES(B) 02/03/77 13:09:18 PAGE 1

PROCESS COST OVERVIEW-$/WATT

ASSUMPTIONS: 0.717 WATTS PER SOLAR CELL AND $ 0.0 FOR 7.8 CM (3") DIAMETER WAFER

STEP	YIELD	PROCESS		MAT'L.	D. L.	EXP.	P. OH.	INT.	DEPR.	SUBTOT	SALVG.	TOTALS	%	INVEST	%
1	99.0%	SYSTEM "Z" WAFER CLEANING	(B)	0.0	0.001	0.001	0.000	0.000	0.000	0.003	0.0	0.003	1.0	0.002	0.7
2	98.0%	SCREEN PRINT SOURCE:2 SIDES	(B)	0.013	0.008	0.007	0.007	0.003	0.004	0.042	0.0	0.042	12.7	0.031	12.0
3	98.0%	DIFFUSION	(B)	0.0	0.009	0.002	0.002	0.001	0.003	0.016	0.0	0.016	5.0	0.012	4.7
4	99.0%	GLASS REMOVAL	(B)	0.0	0.002	0.001	0.001	0.000	0.001	0.005	0.0	0.005	1.5	0.005	1.9
5	99.0%	POST DIFFUSION INSPECTION	(B)	0.0	0.003	0.000	0.003	0.003	0.004	0.013	0.0	0.013	4.1	0.030	11.7
6	98.0%	THICK AG METAL-BACK:AUTO	(B)	0.024	0.004	0.005	0.005	0.003	0.004	0.045	0.0	0.045	13.6	0.031	12.1
7	98.0%	THICK AG METAL-FRONT:AUTO	(B)	0.024	0.009	0.011	0.012	0.006	0.009	0.070	0.0	0.070	21.4	0.062	24.3
8	99.0%	AR COATING:SPRAY-ON	(B)	0.002	0.004	0.002	0.001	0.001	0.001	0.011	0.0	0.011	3.3	0.008	3.3
9	80.0%	TEST	(B)	0.0	0.004	0.000	0.003	0.004	0.006	0.018	0.0	0.018	5.4	0.042	16.4
10	98.0%	INTERCONNECT:GAP WELDING	(B)	0.002	0.006	0.002	0.002	0.002	0.003	0.016	0.0	0.016	4.9	0.019	7.6
11	100.0%	DOUBLE GLASS PANEL ASSEMBLY	(B)	0.072	0.002	0.002	0.001	0.001	0.002	0.080	0.0	0.080	24.3	0.014	5.3
12	100.0%	ARRAY MODULE PACKAGING	(A)	0.007	0.001	0.0	0.000	0.000	0.000	0.009	0.0	0.009	2.7	0.000	0.2
	69.5%	TOTALS		0.144	0.054	0.033	0.037	0.023	0.038	0.328	0.0	0.328	100.0	0.257	100.0
			%	43.78	16.44	10.09	11.16	7.04	11.49	100.00					

NOTE: (A)=EXISTING TECHNOLOGY; (B)=NEAR FUTURE; (C)=FUTURE ANNUAL PRODUCTION: 50.0 MEGAWATTS.

Figure 10. Cost summary - screen print 2 sides.

	Ion Implant(C) (¢/W)	Spin-on + $POCL_3$(C) (¢/W)	Screen Print 2 Sides(C) (¢/W)
Junction Formation	4.2	6.6	5.1
Metallization	9.4	9.4	9.4
AR Coating	1.1	1.1	1.1
Test and Sort	1.2	1.2	1.2
Interconnect, Encapsulation & Packaging	10.5	10.5	10.5
	26.4	29.0	27.4
Labor & Process Overhead Content	4.6	5.8	5.1

Figure 11. Comparison of three class (C) (advanced) process sequences.

	Ion Implant (¢/W)	Spin-on + $POCl_3$ (¢/W)	Screen Print 2 Sides (¢/W)	Spin-on 2 Sides (¢/W)
Junction Formation	9.3	13.0	7.9	11.5
Metallization	11.5	11.5	11.5	11.5
AR Coating	1.1	1.1	1.1	1.1
Test and Sort	1.8	1.8	1.8	1.8
Interconnect, Encapsulation & Packaging	10.5	10.5	10.5	10.5
	34.3	37.8	32.8	36.3
Labor & Process Overhead Content	9.1	12.0	9.1	12.1

Figure 12. Comparison of four class (B) (near future) process sequences.

for the photovoltaic circuit. It is, therefore, necessary to clearly define the panel design considered in the automation study in order that the assembly processes are consistent with the materials selected.

Figure 13 shows the panel design which is the basis for the cost analysis described in this report. The design is characterized by several features which are worthy of comment.

- Glass is used as both substrate and window for the enclosure. We are not convinced that there is a credible alternative to glass in terms of cost and reliable protection for environmental threats. The concept shown calls for the window and substrate to be bonded together structurally so that 1/8-in. sheet can be used in both places and the total assembly is structurally equivalent to a 1/4-in. or greater panel.
- The circuit is configured in a series-parallel arrangement in which four cells are connected in parallel to preserve panel performance if point failures occur at the cell level. The series circuit makes an odd number of traverses across the panel so that the panel interconnection terminals can occur at opposite corners on the panel diagonal. This feature permits ease of packaging for shipment and ease of system interconnection as will be discussed in a later paragraph. The interconnector design utilizes threaded terminals which are ruggedly imbedded into the panel to assure easy system assembly and maintenance (Fig. 14).
- Round cells are utilized since they are available in large quantity. As shown in Fig. 15, the cells are bonded to the substrate using a low-cost compliant bond. Compliant optical filler material is applied between the window and the cells to reduce optical losses in the photon path. By reducing the structural requirements on this material, lower cost compounds can be used. Table 1, originally shown in Quarterly Report No. 3 [1], compares the materials cost for various panel designs. The panel proposed here is column II. By comparing columns I and II, it is easily seen that the elimination of the use of transparent adhesive is a cost-effective step. Note the region between cells does not contain potting compound.

The panel shown in Fig. 13 uses a nonstandard cell size of 4.45-in. diameter in order to meet simultaneously the constraints of 4- x 4-ft panel size, four-parallel-cell circuit, and diagonally opposite circuit termination. The panel has a packing factor of approximately 83% and will deliver 15 V dc and a peak current of 13 A. We find no difficulty in specifying an odd cell size since this solar cell factory will have enough production volume to create

1. B. F. Williams, *Automated Array Assembly*, Quarterly Report No. 3, ERDA/JPL-954352-76/3, prepared under Contract No. 954352 for Jet Propulsion Laboratory, September 1976.

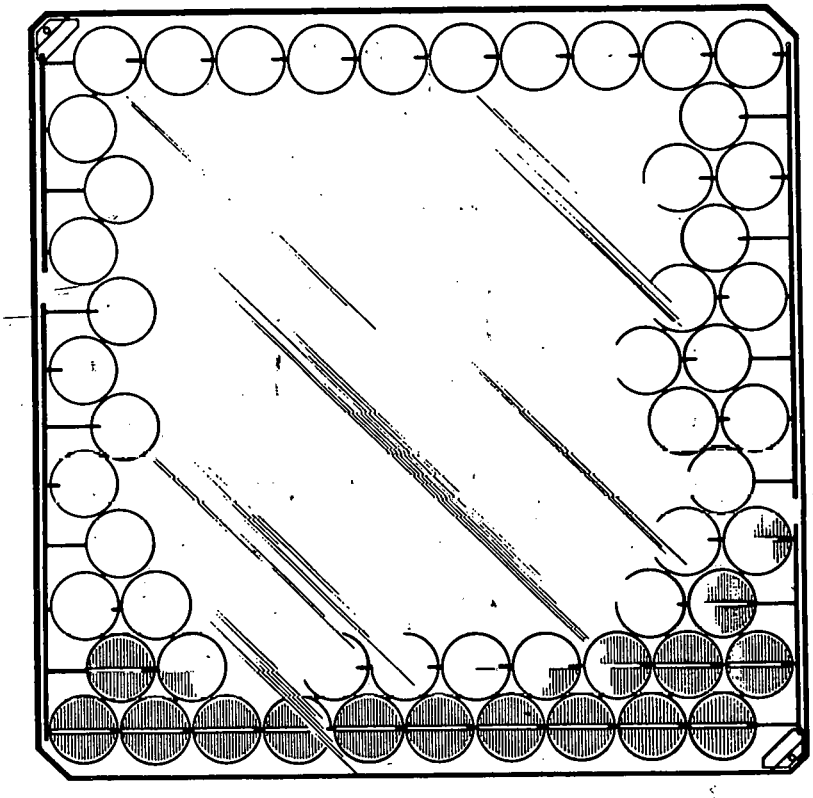

Figure 13. Solar panel design.

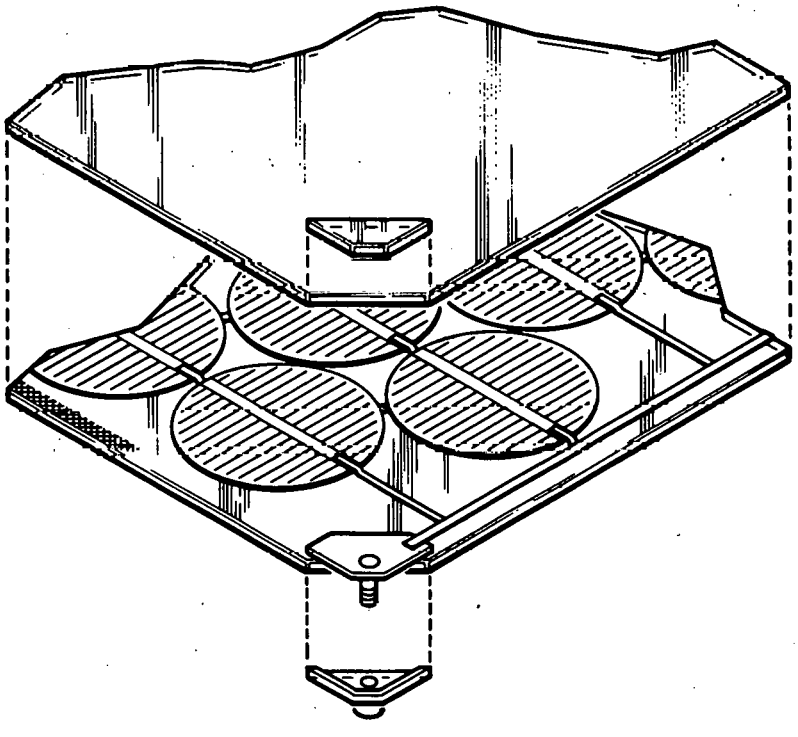

Figure 14. Interconnector design.

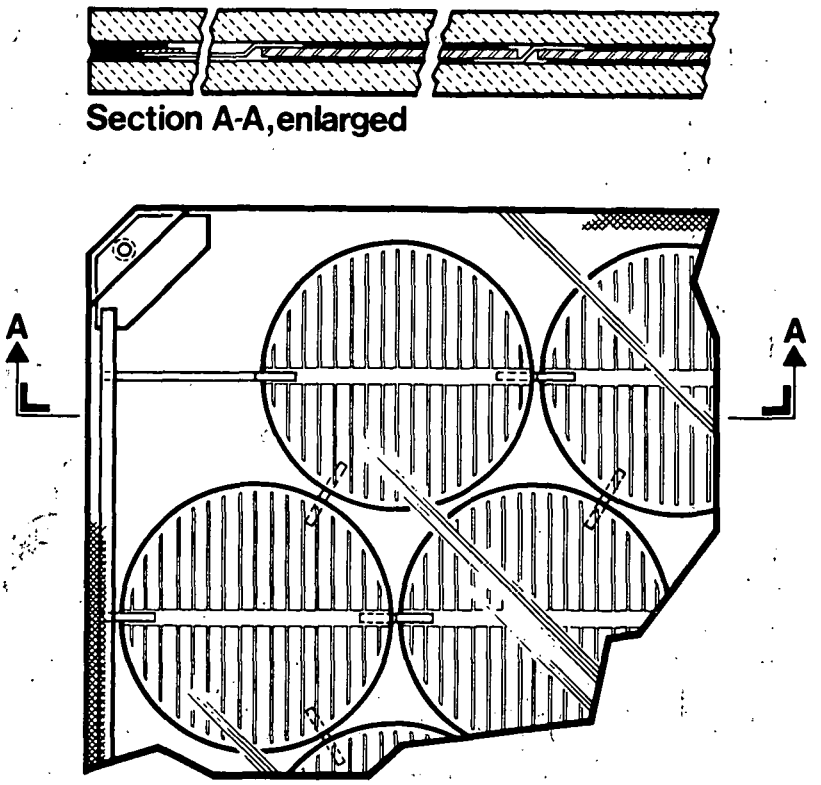

Figure 15. Round cell configuration.

as standard any size which meets the need of its products. A different cell size will change the panel dimensions to maintain high panel area efficiency. Detailed baseline cost estimates have been made on the basis of a 3-in. cell as the basic building block. Almost all of the costs of the panel itself are cell size independent, the one exception being interconnection and assembly capital equipment cost which decreases linearly as cell size goes up. Since the cost of this equipment is a small fraction of the total cost and the influence of cell size on its value is small, the analysis shows that the 3- to 5-in. cell size range, panel and assembly costs are almost independent of cell size (10.5¢/W compared with 9.9¢/W for 5-in. cell; see Fig. 36).

2. Panel Installation

The proposed panel design is configured for simple and low cost installation. Figure 16 shows a system configuration of solar cell panels which is six panels wide and five panels high (24 x 20 ft). The configuration shows that the panels are installed using standard window glazing techniques. Each

TABLE 1. COST COMPARISON OF PACKAGING MATERIALS

Item	I	II	III	IV	V	VI	VII
Substrate							
1/16 glass sheet					0.19		
1/8 glass sheet		0.22					
0.005 alum. foil			0.05			0.05	0.05
Cell Adhesive							
RTV15/Primer	0.41			0.41			
RTV 102		0.10	0.10		0.10	0.10	0.10
Window							
1/16 glass sheet					0.19		
1/8 glass sheet		0.22		0.22			
1/4 glass sheet	0.44						
1-in.-diam R6 tubing			.45				
1-in.-diam N51 tubing						0.60	
2-in.-diam R6 tubing							1.07
Assembly Closure							
Conformal coating + 3-mil metal	0.11			0.11			
Edge seal		0.04			0.06		
End caps			0.06			0.06	0.03
Panel Connector	0.09	0.09	0.18	0.36	0.36	0.18	0.13
Aluminum Structural Channel	____	____	0.10	____	____	0.10	0.10
Total	1.05	0.67	0.94	1.10	0.90	1.09	1.48

Column Identification:

I - 1/4 glass with conformal coating 4 x 4 ft module
II - 1/8 glass window and substrate bonded together 4 x 4 ft module
III - 1-in.-diam R6 tubing with aluminum for substrate (48 tubes in module)
IV - 1/8 glass with conformal coating (four) 2 x 2 ft panels in a 4 x 4 ft module
V - 1/16 glass window and substrate bonded together into four 2 x 2 ft panels in a 4 x 4 ft module
VI - 1-in.-diam N51 tubing with aluminum foil substrate (48 tubes in module)
VII - 2-in.-diam R6 tubing with aluminum foil substrate (24 tubes in module)

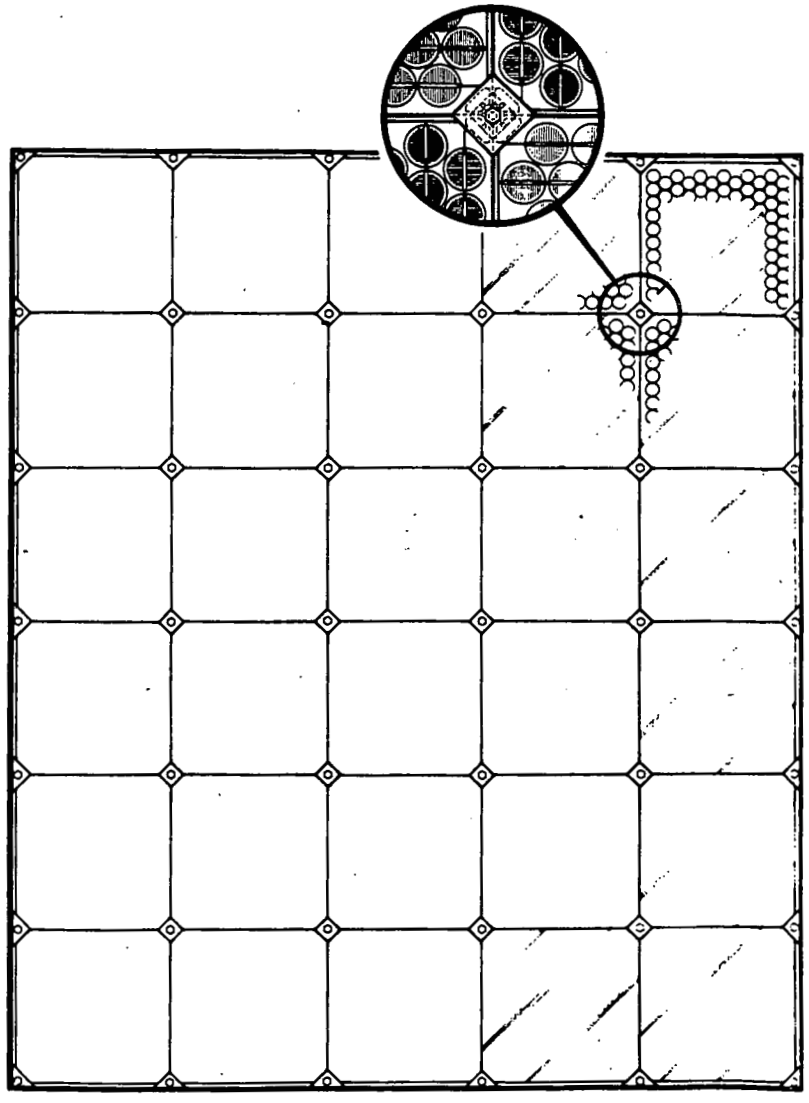

Figure 16. Solar cell panel system configuration.

panel is bedded in a compliant sealing compound and is structurally secured at the corners using a diamond-shaped retaining clip. The spaces between the panels are caulked with clear compliant sealant which give the final assembly the appearance of monolithic glass. The "I" sections of the supporting superstructure all project from the back of the system. All electrical interconnections are made at the point where the four corners of adjacent panels meet. These connections are made at every other intersection point in the panel array. Protection of the interconnection is accomplished using waterproof junction boxes on the back of the structure as shown in the detail view of Fig. 17. Termination of the entire assembly can occur wherever desired by appropriate system layout.

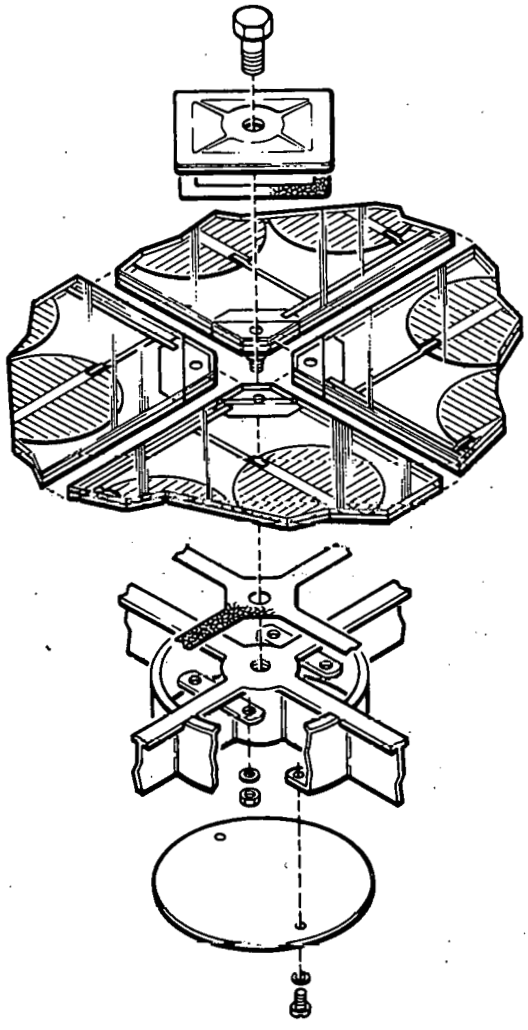

Figure 17. Detail rear view of interconnection.

In Fig. 16, they are shown at the top of the assembly, the assumption being that a power bus can be safely brought to this point. It should be obvious that a range of series-parallel possibilities can be achieved with the proposed construction because of the symmetry between positive and negative panel terminals. This same symmetry could, of course, cause assembly errors unless adequate coding is used.

3. Solar Cell Panel Assembly

The floor plan for a production line to assemble solar cell panels is shown in Fig. 18. This diagram indicates the process flow, equipment complement, factory floor space, and operating personnel required to accomplish

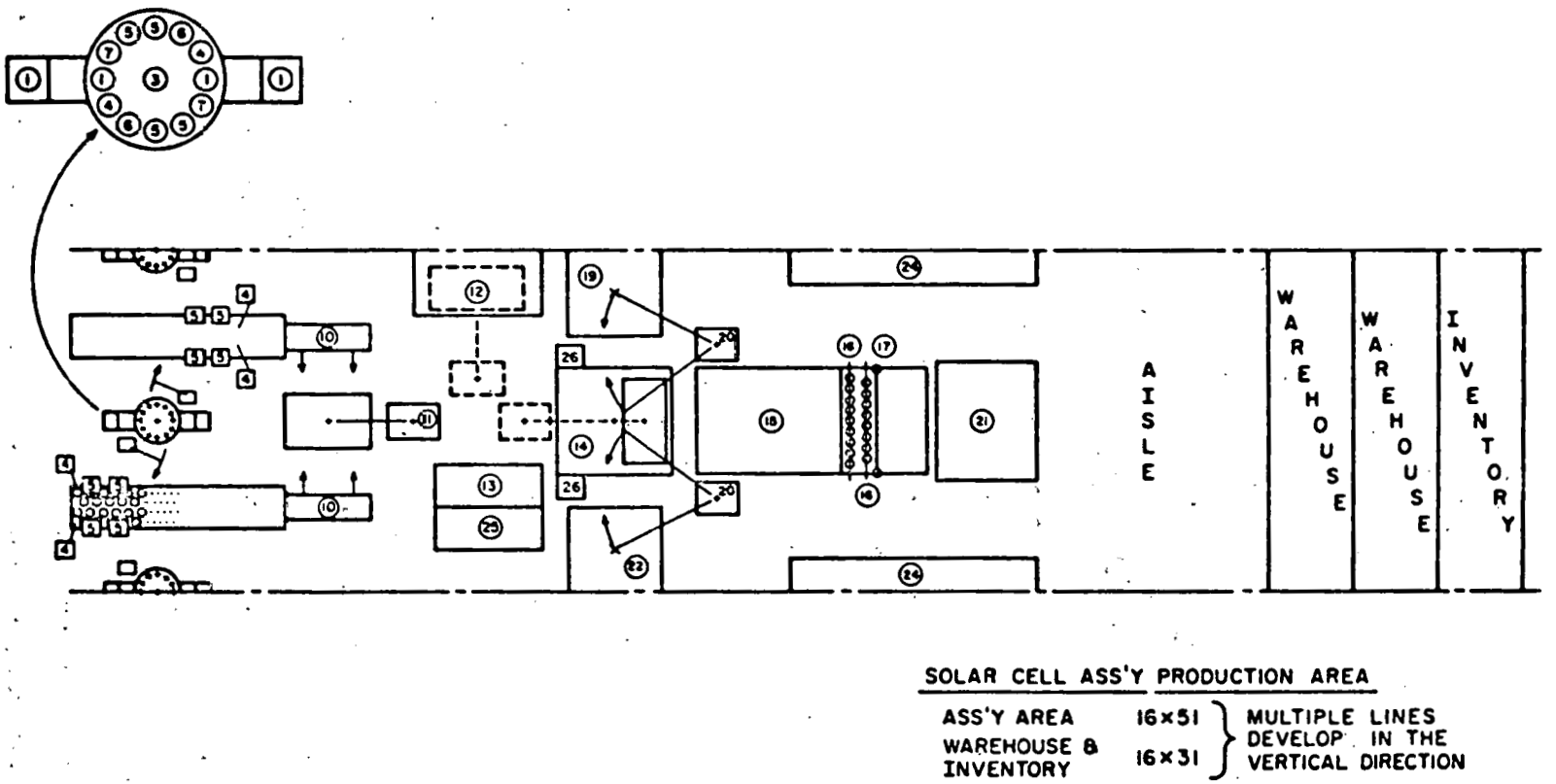

Figure 18. Production line floor plan.

automated assembly of solar cells. The floor plan is laid out in lines so that multiples of its design throughput can be achieved by locating parallel lines side by side. The nominal throughput of the line shown in the figure is approximately 40,000 W per day or 15 MW per year (345 working days per year). As indicated on the figure the production floor space is 16 x 50 ft, and the associated storage and aisle space is 16 x 30 ft. The numbers of the drawing correspond to pieces of important capital equipment required as part of this line. A listing of this equipment and our estimate of its cost is shown in Table 2. The assembly procedure sequence is described below.

4. Panel Assembly Line Functions

a. Sorting - The input into the panel assembly area is cartridges of sorted cells. The exact nature of this sort will not be determined until the distribution of electrical properties versus yield of low-cost solar cells is determined. If one can presume that there will be a greater variation in the properties of a low-cost cell than now exists with space-quality products, then such sorting will be a crucial importance. Several sorting strategies are now being investigated to determine how to configure a panel to most closely approach the performance inherent in the individual cells.

b. Cell Handling - A key element of a solar module factor will be the cell-handling equipment. It is this equipment which will determine the speed and throughput of the line and be responsible for most of the physical breakage which occurs during the various processes. Ideally, it would be desirable to have a continuous process with no operator intervention until the operation is complete. For reasons of process flexibility, the need for buffering between various stations, sorting after various steps, and just the practicality of building up a production line incrementally, cartridge cell handling has been built around each process. It appears that 500-cell cartridges are feasible so that at 1000 cells per hour reasonable amounts of operator attention are possible.

The cell-handling sequence during assembly takes the cell from the cartridge to a rotary table and then to a linear assembly table. Circuit strings

TABLE 2. SOLAR-CELL PANEL ASSEMBLY EQUIPMENT

Station No.	Equipment Description	Qty Req'd	Unit Cost $K
1	Wafer Unloader	4	4
2	Linear Index Table	2	10
3	Rotary Index Table	2	25
4	Pick & Place Assembly	10	5
5	Parallel Gap Bonder	18	5
6	Wafer Turner	2	4
7	Interconnect Formation Tool	4	15
8	Microprocessor Control	1	15
9	Sensors & Assembly Wiring	Lot	20
10	Linear Index Table	2	7.5
11	Robot Arm & Vacuum Hand	1	25
12	Pulse Xenon I-V Tester	1/2	80
13	String Reject Position	1	2
14	Assembly Fixture	1	15
15	Linear Index Table	1	10
16	Adhesive Dispenser	2	10
17	Sealant Bead Dispenser	1	10
18	Panel Assembly Sensors	Lot	15
19	Window Supply Fixture	1	5
20	Glass Handling Robot	2	17.5
21	Substrate Storage/Dispenser	1	5
22	Curing Rack	1	20
23	System Integration	Lot	50
24	Repair Bench	1	3
25	Repaired String Position	1	6
26	Electrical Connector Dispenser	2	6
27	Linear Index Table	1	10

are created on this table and combined into parallel arrangements in subsequent steps. The handling of strings from this point to final assembly is controlled by a robot arm which interfaces the circuit with a vacuum pickup hand.

(1) Airtrack Cell Transport - Figure 19 shows a cartridge of cells pneumatically unloaded onto a linear air-track cushion for transport to a vacuum chuck position on a rotary index welding table. Air transport of the cells helps to reduce physical damage to the cells during transport; it is being used increasingly in the semiconductor industry and would become more highly recommended as cell size increases. Handling rates of 1200 cells/hour are feasible with minor extrapolation from present equipment. A circular cell format is most compatible with this transport technique since edge chipping of any noncircular format has always been a problem during wafer handling.

(2) Rotary Index Table - A rotary index table is used at the first interconnect station since it permits all of the preparatory steps for string assembly to be completed off-line. The table in Fig. 19 has six positions, but notice

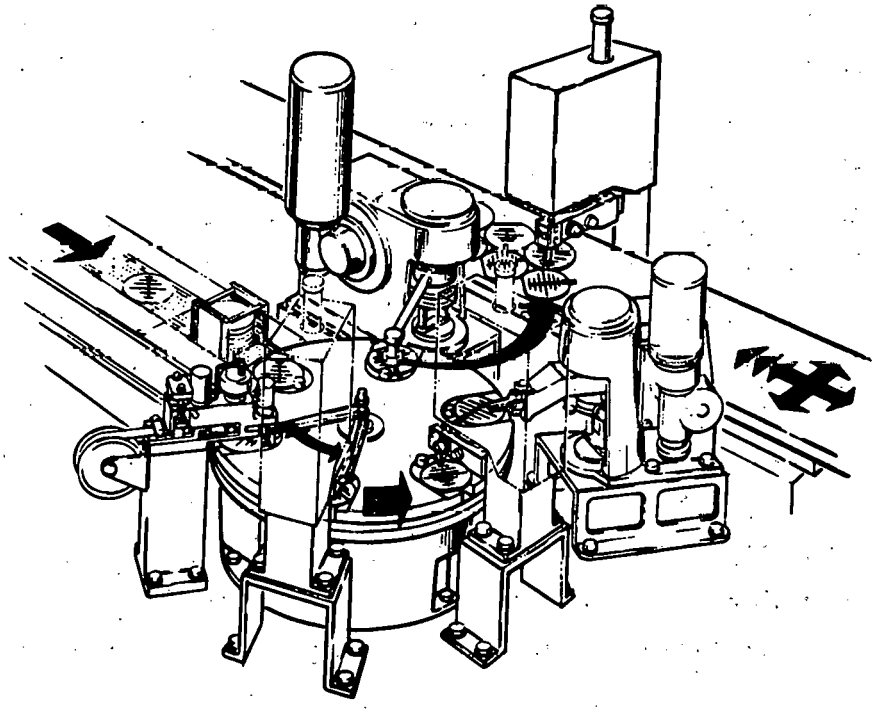

Figure 19. Air-track cell transport of cells onto rotary.

that the throughput of the line would not change regardless of how many positions were on the table. As presently conceived, the operations completed on the rotary table are:

- position the cell
- orient the cell with regard to angular position
- form and place interconnects
- make two front side welds
- turn over cells
- prepare contact areas for interconnection (if necessary)
- pick up position for string assembly table

(3) Series Connection Table - Series and parallel interconnections are made on a linear motion table. In Fig. 18, station 10 represents the interconnection assembly area. Four bonds are made at this station. Two of these are the series connections for each of the two strings being assembled at the station. The others are the bonds necessary to make parallel connection between each of the cells in the two series strings.

When the strings are completed, they are advancing to a combining position indicated by the arrows at station 10. Two groups of cells from adjacent tables are combined at a pickup point for the assembly robot at station 11.

(4) Panel Assembly Robot - After the cells are bonded together electrically, they are handled by a multiported vacuum pickup hand which is 4 ft long and four circuit strings wide. This vacuum hand will be mounted on the end of a robot arm which has 5 degrees of freedom, namely, X translation, Y translation, Z translation, rotation about the arm axis at the carriage, and rotation about the arm axis at the vacuum head. The robot arm, under computer control, can address five string positions: string pickup, string test, panel placement, string reject, and repair pickup.

The function at each of these positions will be discussed in later paragraphs. The cell handling until the cells have been bonded to the panel substrate is by virtue of vacuum contact at the robot arm pickup hand. The total cycle time for the robot is 100 s per four-string placement. Since each robot has two arms each acting 180° out of phase with the other, the effective cycle rate is 50 s. The timing sequence for this position is shown in Table 3.

TABLE 3. PANEL ASSEMBLY TIMING SEQUENCE

Step	Time Sequence (s) Arm 1	Arm 2
Four-string pickup	0-2	50-52
Transfer to test	2-4	52-54
Test sequence	4-6	54-56
Transfer to rejects	6-10	56-60
Drop defective part (if any)	10-12	60-62
Pick up replacement string (if required)	12-14	62-64
Index to final bonding station	14-16	64-66
Dwell at bonding station	16-46	66-96
Index to panel placement	46-66	96-16
Dwell at panel placement	66-96	16-46
Return to pickup	96-100	46-50

c. Panel Materials Handling - The other panel materials are glass (substrate and window), adhesives and sealants, and electrical components. Glass and final panel handling will be accomplished using a simplified robot arm with vacuum pickup hand. Adhesive and sealant will be dispensed in dots and beads from an automatic pneumatic dispensing machine. Electrical parts will be located and placed using pick and place equipment fed from a vibrating bowl.

d. Panel Assembly Processes - In addition to material handling, panel assembly involves five other significant processes, namely, electrical interconnect bonding, physical bonding of cells to substrate and window, electrical testing of circuit strings, final panel wiring, and protective envelope closure.

(1) Solar Cell Interconnection - Interconnection of solar cells can be done most quickly and reliably using parallel gap techniques in conjunction with appropriate automated material-handling equipment. This technique permits the metallurgical operation to proceed quickly, under close control, and with minimum consumables. The cost, thus, is low because consumed material is minimum and process yield is maximum.

There is no final conclusion on which metallurgical process is preferred since more technology input is required with regard to application of the candidate processes applied to thick-film conductors. Our analysis shows that the cost to create the interconnect bond will not be significantly different if the bonding technique is solder reflow, welding, or ultrasonic bonding.

(2) Electrical Test - Testing of assembled solar cell strings will be accomplished using a pulsed Xenon I-V tester. Existing equipment is available to generate a detailed I-V curve in less than 1 s. Since the illuminated aperture of this tester can be large and testing time is only a fraction of string dwell at the test site, it will be possible to share a tester for two assembly lines.

Testing criteria can be established on the strings based on the input cell characteristics. Cell changes induced by interconnect bonding or poor quality bonds can be identified using this technique and the involved circuit strings rejected.

(3) Cell Bonding - The preferred technique for bonding solar cells to a structural substrate is through the use of a compliant silicone rubber adhesive on the backside of the cell. This allows the use of higher strength and lower cost compounds for this purpose. It will be necessary to use a transparent material between the cells and the panel window in order to reduce the optical losses caused by refractive index mismatch. By reducing the structural demand on this material, simpler and low-cost materials can be used.

The proposed design calls for a structural epoxy bond between substrate and window. This bond will allow the load incident on the panel to be shared by both panel and substrate. This epoxy will be dispensed at the same time as the cell bonding adhesive and will be located in the spaces adjacent to every fourth cell in the panel.

(4) Final Panel Wiring - The panel design shown in Fig. 13 utilizes a corner connector bonded between the substrate and window to make electrical penetration from the protective envelope. The positive and negative connectors and associated power bus will be bonded to the appropriate string interconnectors after the cells are bonded to the substrate. Placement of these components is done automatically with pick and place equipment.

(5) Protective Envelope Closure - The final assembly operation calls for placement of the panel window onto a completely assembled circuit substrate. In this operation previously metered quantities of spacer and connector adhesives, optical matching material, and panel edge sealant are compressed to create intimate contacts with their related parts. The finished panel is positioned in a wiring rack which is kept at elevated temperature during a short cure cycle. The closure is visually examined at this point along with other physical properties of the assembly. Final packaging in a shock-isolated crate prepares the products for delivery from the plant.

e. Panel Assembly Summary - The assembly procedures and associated equipment can be divided into four groupings: string interconnection, testing, panel assembly, and final assembly. The following summary description lists the steps on the assembly procedure and by reference to Fig. 18 identifies the equipment required to perform each function.

	Assembly Step	Station No.
INTERCONNECTION	1. Unload cells from cartridge	1
	2. Form and place series interconnects	4
	3. Bond interconnect to cell (2 places)	5
	4. Turn over cell	6
	5. Lift and place on linear table	7
	6. Make cell series connection	5
	7. Form and place parallel interconnects	4
	8. Make cell parallel connection	5
	9. Advance double string to assembly pickup point	10
TEST	10. Lift two double strings and index to test position	11
	11. Generate illuminated I-V curve for each of two double strings	13
PANEL ASSEMBLY	12. Index string to reject position and leave any rejected string	13
	13. Index to repaired string pickup position and lift replacement strings	25
	14. Return to parallel bonding station and combine double strings	10
	15. Eject panel substrate to panel prep area	21
	16. Dispense closure bead onto substrate	16

		Assembly Step	Station No.
PANEL ASSEMBLY	17.	Dispense structural epoxy onto substrate	16
	18.	Dispense cell adhesive onto substrate	16
	19.	Advance prepared substrate to assembly position	15
	20.	Place quadruple string on a prepared panel substrate	14
	21.	Place and bond panel connectors and bus	26,5
FINAL ASSEMBLY	22.	Dispense optical matching material onto panel window	19
	23.	Lift and place window onto completed circuit assembly	20
	24.	Lift and place complete assembly in a curing rack	20
	25.	Place curing rack in curing oven	22
	26.	Remove finished assembly for final inspection and packaging	-

String repair takes place at station 24. Repaired strings are placed at station 25 for automatic pickup.

The process parameters for the interconnect step, the double-glass panel assembly, and the array module packing are given in Figs. 20, 21, and 22.

5. Process: Test

This step automatically tests the completed cells for photovoltaic performance, separates the acceptable cells from the rejects, and sorts the good cells according to efficiency in 1% increments. The machine is microprocessor-controlled and consists of a test station and sorter. At the test station the wafer is contacted by probes and exposed to a known light source. The shape of the I-V curve is determined in the region of the knee (maximum power point) to determine the fill factor. The open-circuit voltage and short-circuit current are determined by the preset test program, and from these results the efficiency is calculated. The sorter, which is activated by the result of the test station, automatically assigns the cell to a cassette of the right classification. Process parameters are shown in Fig. 23.

PROCESS PARAMETERS:INTERCONNECT:GAP WELDING 04/18/77 09:51:24 PAGE 72

ESTIMATE DATE:12/27/76 BY:BEN SHELPUK, PC4971, CAMDEN, BLDG. 10-8-12 CLASS:ARRAY FABRICATION
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:NEAR FUTURE MATERIAL FORM:3" WAFER.
INPUT UNIT:SOLAR CELLS OUTPUT UNIT:SOLAR CELLS TRANSPORT IN:500 SHEET CASSETTE TRANSPORT OUT:PICKUP TABLE
PROCESS YIELD: 98.0% YIELD GROWTH PROFILE: 0
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:VALUE IN$
PERFORMANCE FACTORS-I(R)/I(SC): 1.000000E+00 V(R)/V(OC): 1.000000E+00 F(R)/F: 1.000000E+00

INPUT UNITS:	0.	0.	0.
FLOOR SPACE,FT**2:	0.	0.	0.

DESCRIPTION:INTERCONNECTION:GAP WELDING(B)

ASSUMPTIONS:

1. 3" DIAMETER WAFER, 12-14 MILS THICK,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. REWORK OPERATOR REWORKS STRING TEST REJECTS (=3% OF INPUT)

PROCEDURE

1. WAFER FROM CASSETTE TO AIR TRACK TO ROTARY TABLE FOR P-CONTACT BOND.
2. AUTOMATIC PICKUP AND PLACE FROM ROTARY TABLE TO LINEAR TABLE FOR SERIES BOND.
3. INDIVIDUAL STRINGS ARE PRESENTED TO THE TEST STATION USING PICK AND PLACE HANDLING.
4. STRINGS ARE ILLUMINATED WITH A PULSED XENON LAMP AND A COMPLETE I-V CURVE IS GENERATED.
5. ACCEPTANCE CRITERIA WILL BE PROGRAMMED INTO TEST LOGIC.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT	UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
GW INTERCONNECT EQUIP.(B)	3800.00	CELLS/HR	100.0%	$ 27:000.	85.0%	130.
STRING TEST EQUIPMENT(B)	7600.00	CELLS/HR	100.0%	$ 88000.	95.0%	110.

LABOR

(DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	GW INTERCONNECT EQUIP.(B)	3.330E-01		
REWORK OPERATOR	GW INTERCONNECT EQUIP.(B)	1.000E+00		
HOURLY OPERATOR	STRING TEST EQUIPMENT(B)	2.000E-01		
MAINTENANCE	GW INTERCONNECT EQUIP.(B)	1.000E-01		
MAINTENANCE	STRING TEST EQUIPMENT(B)	1.000E-01		
FOREMAN —	DL	1.000E-01		

SUPPLIES/EXPENSES

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	UNITS	BASE
ELECTRICITY	0.0	8.000E+00	KWH.	PER AVAILABLE INVESTMENT-HOUR OF GW INTERCONNECT EQUIP.(B)
ELECTRICITY	0.0	3.000E+00	KWH.	PER AVAILABLE INVESTMENT-HOUR OF STRING TEST EQUIPMENT(B)
AG-PLATED CU WIRE	0.0	1.430E-03	$	PER INPUT UNIT. % UNITS= 100.0%
ELECTRODES	0.0	1.430E-03	$	PER INPUT UNIT. % UNITS= 100.0%

Figure 20. Process parameters – interconnect step.

PROCESS PARAMETERS:DOUBLE GLASS PANEL ASSEMBLY 04/18/77 09:51:24 PAGE 74

ESTIMATE DATE:01/25/77 BY:BEN SHELPUK, PC4971, CAMDEN, BLDG. 10-8-12 CLASS:ARRAY FABRICATION
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:NEAR FUTURE MATERIAL FORM:3" WAFER.
INPUT UNIT:SOLAR CELLS OUTPUT UNIT:ARRAY MODULES TRANSPORT IN:PICKUP TABLE TRANSPORT OUT:CURING RACK
PROCESS YIELD:100.0% YIELD GROWTH PROFILE: 0
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:VALUE IN$
PERFORMANCE FACTORS-I(R)/I(SC): 1.000000E+00 V(R)/V(OC): 1.000000E+00 F(R)/F: 1.000000E+00

INPUT UNITS:	0.	0.	0.
FLOOR SPACE,FT**2:	0.	0.	0.

DESCRIPTION:PANEL ASSEMBLY, FINAL ASSEMBLY, & TEST(B)

ASSUMPTIONS:

1. 3" DIAMETER WAFER, 12-14 MILS THICK,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. NO BREAKAGE ASSUMED.
3. DOUBLE GLASS PANEL, 14.6FT**2. SEE QUARTERLY REPORT #3, PAGE 38, TABLE 5, COLUMN 2.
4. NOTE: TO DETERMINE MATERIAL $/FT**2, MULTIPLY MATERIAL COST SHOWN($/CELL) X 224 CELLS/14.6FT**2.
5. 5 CURING RACKS NEEDED FOR EACH PIECE OF PANEL ASSEMPLY EQUIPMENT.

PROCEDURE

1. AUTOMATIC PICK UP & PLACEMENT OF MULTIPLE STRINGS ONTO SUBSTRATE POSITIONED ON X-Y MOTION TABLE.
2. STRINGS COMPLIANTLY BONDED TO GLASS SUBSTRATE.
3. PARALLEL ELECTRICAL CONNECTION OF STRINGS.
4. SERIES CONNECTION TO POWER TERMINATIONS BY PARALLEL GAP WELDING.
5. FINAL ASSEMBLY:WINDOW IS APPLIED TO THE ASSEMBLY USING PICK AND PLACE.
6. WINDOW IS BONDED TO THE SUBSTRATE USING A MULTIPLICITY OF EPOXY BONDED SPACERS.
7. ENCLOSED SPACE IS SEALED FROM MOISTURE PENETRATION BY A PERIMETER BOND OF POLYISOBUTYLENE.
8. FINAL ASSEMBLY IS TRANSFERRED TO CURING RACKS USING PICK AND PLACE.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT	UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
PANEL ASSEMBLY EQUIPMENT(B)	3724.00	CELLS/HR	100.0%	$ 103000.	85.0%	300.
FINAL ASSEMBLY EQUIPMENT(B)	3724.00	CELLS/HR	100.0%	$ 125000.	85.0%	280.
CURING RACK	744.80	CELLS/HR	100.0%	$ 50.	100.0%	20.

LABOR

(DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	PANEL ASSEMBLY EQUIPMENT(B)	2.500E-01		
HOURLY OPERATOR	FINAL ASSEMBLY EQUIPMENT(B)	2.500E-01		
MAINTENANCE	PANEL ASSEMBLY EQUIPMENT(B)	1.000E-01		
MAINTENANCE	FINAL ASSEMBLY EQUIPMENT(B)	1.000E-01		
FOREMAN	DL	1.000E-01		

SUPPLIES/EXPENSES

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	UNITS	BASE
ELECTRICITY	0.0	8.000E-01	KWH.	PER AVAILABLE INVESTMENT-HOUR OF PANEL ASSEMBLY EQUIPMENT(B)
ELECTRICITY	0.0	4.000E+00	KWH.	PER AVAILABLE INVESTMENT-HOUR OF FINAL ASSEMBLY EQUIPMENT(B)
SUBSTRATE	0.0	1.430E-02	$	PER INPUT UNIT. % UNITS= 100.0%
CELL ADHESIVE	0.0	6.520E-03	$	PER INPUT UNIT. % UNITS= 100.0%
WINDOW	0.0	1.430E-02	$	PER INPUT UNIT. % UNITS= 100.0%
PANEL CONNECTOR	0.0	5.870E-03	$	PER INPUT UNIT. % UNITS= 100.0%
EDGE SEAL	0.0	3.910E-03	$	PER INPUT UNIT. % UNITS= 100.0%
EPOXY SPACER	0.0	2.610E-03	$	PER INPUT UNIT. % UNITS= 100.0%
SOLVENT	0.0	1.300E-03	$	PER INPUT UNIT. % UNITS= 100.0%

Figure 21. Process parameters - double glass panel assembly.

PROCESS PARAMETERS:ARRAY MODULE PACKAGING 04/18/77 09:51:24 PAGE 77

ESTIMATE DATE:12/28/76 BY:BEN SHELPUK, PC4571, CAMDEN, BLDG. 10-8-12 CLASS:PACKAGING
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:EXISTING MATERIAL FORM:3" WAFER.
INPUT UNIT:ARRAY MODULES OUTPUT UNIT:ARRAY MODULES TRANSPORT IN:CURING RACK TRANSPORT OUT:BOX
PROCESS YIELD:100.0% YIELD GROWTH PROFILE: 0
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:VALUE IN$
PERFORMANCE FACTORS-I:R)/I(SC): 1.000000E+00 V(R)/V(OC): 1.000000E+00 F(R)/F: 1.000000E+00

INPUT UNITS:	0.	0.	0.
FLOOR SPACE,FT**2:	0.	0.	0.

DESCRIPTION:ARRAY MODULES PLACED IN WOOD CRATE.

ASSUMPTIONS:

1. 14.6 FT**2 PANEL.
2. 14.6 FT**2 OF WOOD CRATE NEEDED AT 5.08 PER FT**2 OF PANEL.
3. 1 OPERATOR CAN PACKAGE 50 MODULES/HR USING PACKAGING EQUIPMENT.
4. N, THE NUMBER OF PANELS PER WOOD CRATE, IS TO BE DETERMINED.

PROCEDURE

1. OPERATOR REMOVES N PANELS FROM CURING RACK & PLACES THEM IN BOX.
2. BOX STAPLED.
3. BOX PLACED ON STACK FOR REMOVAL TO WAREHOUSE.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT	UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
PACKAGING EQUIPMENT	50.00	A.M./HR	100.0%	$ 25000.	100.0%	100.

LABOR

(DL=DIRECT LABOR PERSONSTYL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	PACKAGING EQUIPMENT	1.000E+00		
FOREMAN	DL	1.000E-01		

SUPPLIES/EXPENSES

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	UNITS	BASE
BOX FOR MODULE	0.0	1.170E+00	$	PER INPUT UNIT. % UNITS= 100.0%

Figure 22. Process parameters - array module packing.

PROCESS PARAMETERS:TEST 04/18/77 09:51:24 PAGE 63

ESTIMATE DATE:12/27/76 BY:DAVE RICHMAN, X3207, RCA LABS, E-321A CLASS:TEST
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:NEAR FUTURE MATERIAL FORM:3" WAFER.
INPUT UNIT:SHEETS OUTPUT UNIT:SOLAR CELLS TRANSPORT IN:500 SHEET CASSETTE TRANSPORT OUT:500 SHEET CASSETTE
PROCESS YIELD: 80.0% YIELD GROWTH PROFILE: 0
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:FRACTION OF INPUT UNIT VALUE
PERFORMANCE FACTORS-I(R)/I(SC): 1.000000E+00 V(R)/V(OC): 1.000000E+00 F(R)/F: 1.000000E+00

INPUT UNITS:	0.	0.	0.
FLOOR SPACE,FT**2:	0.	0.	0.

DESCRIPTION:WAFER ELECTRICAL TEST AND SORT.

ASSUMPTIONS:

1. 3" DIAMETER WAFER, 12-14 MILS THICK,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. TEST FOR: OPEN CIRCUIT VOLTAGE;SHORT CIRCUIT CURRENT;REVERSE BIAS LEAKAGE; FILL FACTOR.
3. MINICOMPUTER-CONTROLLED MEASUREMENT OF 12 POINTS ALONG KNEE OF I-V CURVE FOR KNOWN LIGHTING.
4. WAFERS BELOW 10% EFFICIENCY ARE REJECTED. 80% YIELD ESTIMATED.

PROCEDURE

1. OPERATOR LOADS CASSETTE INTO MACHINE.
2. WAFERS AUTOMATICALLY FED TO TEST EQUIPMENT AND MEASUREMENTS MADE.
3. WAFERS SORTED INTO MAGAZINES USING CRITERIA TO BE DEFINED.
4. OPERATOR REMOVES CASSETTES AS THEY ARE FILLED.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
SILTEC WAFER SORTER-W.E.T.	1200.00 SH/HR	100.0%	$ 175000.	80.0%	200.

LABOR

(DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	SILTEC WAFER SORTER-W.E.T.	2.500E-01		
MAINTENANCE	SILTEC WAFER SORTER-W.E.T.	2.000E-01		
FOREMAN	DL	1.000E-01		

SUPPLIES/EXPENSES

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	UNITS	BASE
ELECTRICITY	0.0	5.000E+00	KWH.	PER AVAILABLE INVESTMENT-HOUR OF SILTEC WAFER SORTER-W.E.T.

Figure 23. Process parameters - test.

6. Antireflection Coating, Spray-On

Use of conventional spin-on application of solutions for depositing the AR coating on solar cells is expensive because of the low rate of throughput and will cause problems of film uniformity because of the metallization pattern interfering with the uniform spreading of the solution.

We have examined the technical and economic feasibility of spray coating techniques as an alternative, and we are entirely convinced that spray coating is indeed the technique of choice for this particular application.

Commercial equipment, designed primarily for the semiconductor industry, offers excellent control and performance of high-quality film deposits, and remarkable economy.

The heart of the machine is the vapor carrier system which uses a superheated chemically inert hydrocarbon vapor of high molecular weight as the transporting medium for the coating material. The low velocity and pressure at which the coating material is conveyed by the vapor to the target surface minimizes the problems encountered with systems based on pressurized gases as the carrier. The solar cells are transported in a 6-wafer-wide stream by a conveyor belt from the load station into the spray station. The coating is applied by a fully automated and adjustable spray gun which traverses the six 3-in.-diam wafers at a set speed and distance. Work flow proceeds at a rate of typically 3/4 in./s. Under these conditions the Autocoater can process 5,400 cells per hour, or 4.4×10^7 cells per year.

The thickness of the $SiO_2 + TiO_2$ containing AR film after drying and baking is specified to be 700 Å. The control of coating thickness is within $\pm 5\%$. Figure 24 shows the performance of such an AR coating which was spun-on compared with thermally oxidized Ta_2O_5. Both layers make a very good AR coating.

An additional part of the system is an infrared-heated section capable of attaining 500°C. Since we require only 200° and 400°C for bake out (15 min each, at present), this limit is quite adequate. The rate of throughput may be a problem, however, and may require either a change in processing or the addition of heaters working in parallel.

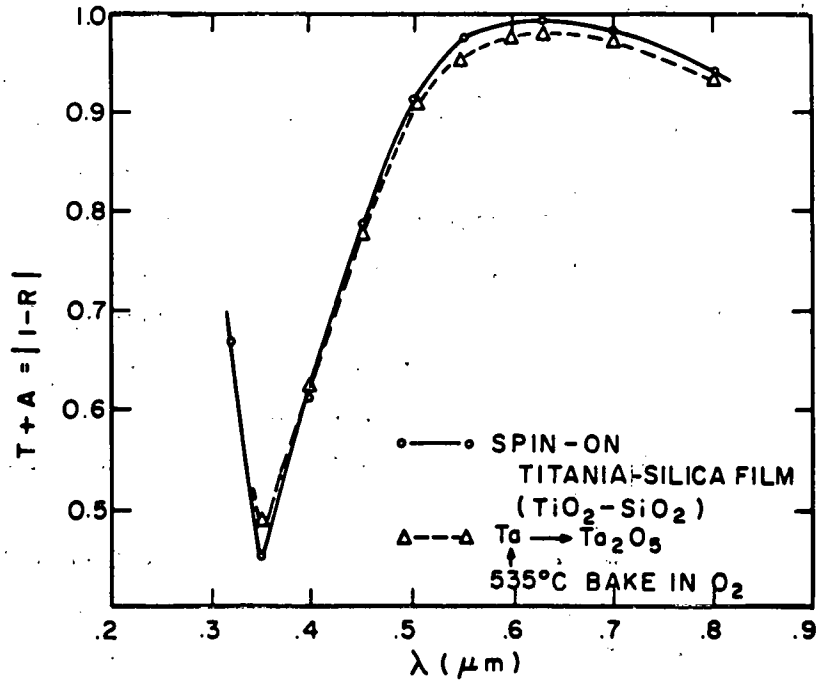

Figure 24. Reflection spectra: spin-on titania-silica film and Ta_2O_5 formed by thermal oxidation of evaporated Ta.

The AR coating process parameters are shown in Fig. 25.

7. Metallizations

a. Thick-Film Screen Printing - We believe that a metallization technology based on screen-printed contacts is the most cost effective. The principal problem with this technology is to combine low contact resistance with low penetration and high adhesion.

In Quarterly Report No. 3 [1] we showed that the contact resistance must be below 0.1 Ω-cm^2 to not seriously affect device performance. In an experimental evaluation of commercial Al, Ni, and Ag inks we have not found it possible to produce this low a contact resistance without producing excessive penetration.

Therefore, we have investigated formulating a silver metallization with the proper n-type dopant, phosphorus, which would require a low firing temperature and thereby minimize penetration and contact resistance simultaneously. $AgPO_3$ was selected because of its low melting point, i.e., 485°C. Similar Ag-P compounds are under study. A small amount of the material was prepared

PROCESS PARAMETERS:AR COATING:SPRAY-ON 04/18/77 09:51:24 PAGE 60

ESTIMATE DATE:02/28/77 BY:RCA ESTIMATES CLASS:AR COATING
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:NEAR FUTURE MATERIAL FORM:3" WAFER.
INPUT UNIT:SHEETS OUTPUT UNIT:SHEETS TRANSPORT IN:500 SHEET CASSETTE TRANSPORT OUT:500 SHEET CASSETTE
PROCESS YIELD: 95.0% YIELD GROWTH PROFILE: 0
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:FRACTION OF INPUT UNIT VALUE
PERFORMANCE FACTORS-I(R)/I(SD): 1.000000E+00 V(R)/V(OC): 1.000000E+00 F(R)/F: 1.000000E+00

INPUT UNITS:	0.	0.	C.
FLOOR SPACE,FT**2:	0.	0.	C.

DESCRIPTION:SPRAY-ON ANTIREFLECTION COATING(3)

ASSUMPTIONS:

1. 3" DIAMETER WAFER, 12-14 MILS THICK,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. 500 WAFERS/CASSETTE
3. NOTE: IN-HOUSE AR COATING NEEDS TO BE DEVELOPED.
4. LIQUID SPRAY-ON SOURCE(TIO2,SIO2) AT $10/LITER. 0.1 CM**3 WILL COVER 1 SIDE WITH 0.07 MICRONS.
7. APPLIED AFTER FINAL METALLIZATION.
8. OVEN BAKE REQUIRED AT 400 C. FOR 1/2 HR. IN AIR.
9. ROOM REQUIREMENTS: DRY,CLEAN FILTERED AIR, 2830 LITERS/HR/SYSTEM.

PROCEDURE

1. WAFERS ARE LOADED FROM CASSETTE TO DEPOSITION ZONE.
2. INERT HYDROCARBON CARRIER GAS TRANSPORTS COATING MATERIAL.
3. AFTER DEPOSITION, WAFER TRANSPORTED VIA BELT TO INFRARED DRYING ZONE.
4. WAFERS ARE BAKED FOR 1/2 HR. AT 400 C. IN AIR.
5. WAFERS LOADED INTO CASSETTE.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
ZICON MODEL 11000 AUTOCOATER	5400.00 SH/HR	100.0%	$ 120000.	85.0%	100.
OPTICAL REFLECTOMETER	5400.00 SH/HR	100.0%	$ 20000.	85.0%	16.

LABOR

(DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	ZICON MODEL 11000 AUTOCOATER	1.000E+00		
MAINTENANCE	ZICON MODEL 11000 AUTOCOATER	2.500E-01		
MAINTENANCE	OPTICAL REFLECTOMETER	5.000E-02		

SUPPLIES/EXPENSES

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	UNITS	BASE
ELECTRICITY	0.0	1.000E+01	KWH.	PER AVAILABLE INVESTMENT-HOUR OF ZICON MODEL 11000 AUTOCOATER
VAPOR CARRIER	0.0	3.000E-01	$	PER AVAILABLE INVESTMENT-HOUR OF ZICON MODEL 11000 AUTOCOATER
IN-HOUSE SPRAY-ON AR COATING	0.0	1.000E-01	CM**3	PER INPUT UNIT. % UNITS= 100.0%

Figure 25. Process parameters - antireflection coating, spray-on.

by reacting $AgNO_3$ with $NaPO_3$-stabilized metaphosphoric acid (HPO_3). The precipitate was dried, crushed, and ground to pass through a 325-mesh sieve. An "off-the-shelf" silver powder was mechanically blended with the $AgPO_3$ powder to yield 95 wt pct Ag-5 wt pct $AgPO_3$. This mixture was suspended in a cellulosic-type organic vehicle and screen printed using a newly designed pattern containing two rows of 0.2-cm-diam dots. The dots were fired onto the same silicon material, i.e., n-type, (100), 5 x $10^{19}/cm^3$, as that used for the evaluation of the commercial inks. The lowest test firing temperature was 500°C, since the $AgPO_3$ melting point is 485°C and a contact angle of 8° was found for $AgPO_3$ on silicon when fired for 2 min at this temperature. A summary of the results for 5-min firings at 500°, 600°, and 700°C is shown in Table 4.

TABLE 4. SPECIFIC CONTACT RESISTANCE OF Ag-$AgPO_3$ METALLIZATION*

Firing Temperature (°C)	Least Square Fit, $y = b + mx$	r^2	Specific Contact Resistance Ω-cm^2
500	$y = 39.88 + 122.56\ x$	0.49	0.65
600	$y = 6.55 + 32.54\ x$	0.29	0.11
650	$y = 17.44 + 6.94\ x$	0.17	0.28
700	$y = 24.15 - 2.12\ x$	0.34	0.39

*Dot-to-dot spacing ranged from 0.6 to 1.9 cm, center-to-center. Gold wire Kelvin connection was used for resistance measurements. Specific contact resistance, ρ_c, = 1/2 b times dot area.

Determination of the least square fit is based on at least four test points. The lowest specific contact resistance was found to be 0.11 Ω-cm^2 at 600°C. However, the poor correlation in each case suggested that the metal-to-silicon contacts are spotty in nature. Angle lapping and metallographic examination disclosed two contributing causes for the poor correlation: gaps in the physical contact between metallization and silicon and voids in the metal. The gap does, however, decrease with increasing temperature, and, most important at the highest temperature, there is no evidence of metallization penetration into the silicon. The high density of voids present in the

metallization also contributes to an apparently high specific contact resistance. Closing of the silicon-to-metal gap and reduction of voids in the fired film will result when changes are made in the silver and $AgPO_3$ particle size distribution and relative amounts of each.

We believe this is an area very worthy of continued attention.

In our cost estimates we have assumed this technology has been developed, and we use ink costs as they exist today. For this metallizing step, cassettes with silicon wafers arrive on carts from the preceding test station (i.e., that following n-p junction formation) and the cassettes are manually placed into the loader adjacent to the screen-printing machine. The loader automatically feeds silicon wafers into the screen printer which applies the particular metallization pattern. This sequence requires three printing and drying operations prior to firing: first the back, then the collecting grid, and then the bus bar on the front.

Detailed evaluation of the technique using printing pastes based on silver, aluminum, and nickel have been carried out from technical and cost viewpoints. The minimum cost of typical Al and Ni pastes ($1.90/troy ounce) is lower than that of Ag paste ($5.42/troy ounce based on the December 1976 market price for Ag). All three pastes shrink close to 50% on drying and firing. The electrical conductivity of a fired coating depends on the paste composition and the firing conditions, and has been assumed in all calculations to be one-half of the bulk conductivity for Ag and one-third for both Al and Ni. For comparing various metallizations, it is important to point out that simply changing metal thickness to provide equal conductivity is not the appropriate course. The metals all cost different amounts and have different conductivities, and the optimum thickness must be determined from minimizing the overall system $/W.

The cost optimization factor (F) with respect to Ag is

$$\left.\begin{array}{l}\text{Factor for}\\ \text{optimizing}\\ \text{pattern}\\ \text{thickness}\end{array}\right\} = F = \frac{\left(\frac{\rho_M}{\rho_{Ag}}\right)^{1/2}}{\left(\frac{\$cm^{-3}_M}{\$cm^{-3}_{Ag}}\right)^{1/2}}$$

where M refers to any fired metal paste and Ag refers to the fired Ag paste.

Compared with Ag, the optimum Al thickness is 4.22 times as thick and the optimum Ni is 6.63 times as thick. The actual thickness of the optimum Ag pattern is derived below.

As can be seen in the cost summary (Fig. 2), the total cost for the metallization step is on the order of 10¢/W. The process parameters for the front and back metallization are shown in Figs. 26 and 27.

b. Metallizing by Nickel/Solder Deposition

(1) Basic Process - Because of its seeming cost effectiveness, a cost estimate has been completed for this alternate metallization process for the purpose of comparison with other methods. Several techniques and process combinations of metal depositions by plating are possible. The process sequence selected is based on well-established electroless plating and solder deposition technology. Essentially, a thin layer of electroless nickel is selectively deposited on both sides of the cell, followed by sintering to create a nickel silicide with good ohmic contact, electroless plating of one additional nickel layer, and, finally, deposition of molten tin-lead solder to provide an ample thickness of metal for good conductance. The entire process is an almost fully automated batch operation where unit lots of 1000 wafers are processed automatically on a continuous basis requiring a minimal amount of labor.

(2) Outline of Processing Sequence

1 Deposition of Mask Pattern

- Screen print a reverse metallization pattern of organic masking material on the cell front side to protect 95° of area. Leave the cell backside exposed.
- Pass the wafers through a drying oven to evaporate solvent material from the masking material.

2 Surface Cleaning

- Immerse the wafers in mild oxidizing solution to remove organic impurities from the exposed surface without affecting the mask coating.
- Rinse in deionized water.
- Dry mechanically.

3 Sensitization and Complexing

- Sensitize in bath of $PdCl_2$ (activator)-HF-CH_3CO_2H.
- Rinse in deionized water.

PROCESS PARAMETERS:THICK AG METAL-FRONT:AUTO 01/20/77 16:15:43 PAGE 53

ESTIMATE DATE:01/12/77 BY:WERNER KERN, X2094, RCA LABS, 03-076 CLASS:METALLIZATION
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:FUTURE MATERIAL FORM:3" WAFER.
INPUT UNIT:SHEETS OUTPUT UNIT:SHEETS TRANSPORT IN:500 WAFER CASSETTE TRANSPORT OUT:500 WAFER CASSETTE
PROCESS YIELD: 99.0% YIELD GROWTH PROFILE: 0
SUBPROCESS USED:SCREEN PRINT WAFER REWORK
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:VALUE IN$
PERFORMANCE FACTORS-I(R)/I(SC): 1.000000E+00 V(R)/V(OC): 1.000000E+00 F(R)/F: 1.000000E+00

INPUT UNITS:	0.	0.	0.
FLOOR SPACE,FT**2:	0.	0.	0.

DESCRIPTION:SCREEN PRINTING AND SINTERING CONDUCTIVE NETWORK-FRONT

ASSUMPTIONS:

1. 3" DIAMETER WAFER, 12-14 MILS THICK,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. BACK METALLIZATION PATTERN MUST BE SCREEN PRINTED FIRST.
3. AG PASTE: $5.42/TROY OZ. = $.1743/GM. 80% AG, WHEN AG COSTS $4.40/TROY OZ.
   DENSITY OF AG PASTE=3.756/CM**3. (31.1G=1 TROY OZ.)
   2:1 RATIO FOR INK THICKNESS TO POST FIRING AG THICKNESS.
4. FRONT AG FINE GRID: 5% COVERAGE, 17 MICRONS THICK AFTER FIRING.
5. FRONT BUS BAR: 1% COVERAGE, 170 MICRONS THICK AFTER FIRING.
6. SCREEN PRINT & DRY SYSTEM:

ITEM	COST	POWER	COMMENTS
LOADER	10.7K	1KW	INSERTS WAFER INTO PRINTER
PRINTER	24.4K	1KW	PRINTER APPLIES PATTERN
COLLATOR	10.0K	1KW	FORMS PARALLEL ROWS FOR DRYER.
DRYER	20.0K	10KW	DRIES INK TO PREVENT SMEARING.
RELOADER	14.7K	1KW	RELOADS WAFERS INTO CASSETTE.
CASSETTES	4.0K	-	HOLDS WAFERS FOR PRINTER.
TOTALS	83.8K	14KW	

   ********NOTE: $125K ESTIMATED FOR ADVANCED SYSTEM.
7. SCREEN PRINT & FIRE SYSTEM:

ITEM	COST	POWER	COMMENTS
LOADER	10.7K	1KW	INSERTS WAFER INTO PRINTER
PRINTER	24.4K	1KW	PRINTER APPLIES PATTERN
COLLATOR	10.0K	1KW	FORMS PARALLEL ROWS FOR DRYER.
DRYER	20.0K	10KW	DRIES INK TO PREVENT SMEARING.
FURNACE	45.0K	15KW	SINTERS PATTERN AT 550 C.
RELOADER	14.7K	1KW	RELOADS WAFERS INTO CASSETTE.
CASSETTES	4.0K	-	HOLDS WAFERS FOR PRINTER.
TOTALS	128.8K	29KW	

   **********NOTE: $208K ESTIMATED FOR ADVANCED SYSTEM.
8. BELT->CASSETTE LOADER CAN DO 6000 WAFERS/HR.
9. SCREEN AT $23, REPLACED 3 TIMES PER DAY FOR FINE GRID.
   SCREEN IS REPLACED 2 TIMES PER DAY FOR BUS BAR SYSTEM.
   SQUEEGES AT $.40, REPLACED ONCE PER HOUR.

Figure 26. Process parameters - front metallization.

PROCESS PARAMETERS:THICK AG METAL-FRONT;AUTO 04/18/77 09:51:24 PAGE 53.1

PROCEDURE

1. OPERATOR LOADS CASSETTE FROM BACK METALLIZATION STEP INTO LOADER.
2. SCREEN PRINT & DRY SYSTEM APPLIES FINE GRID.
   OPTICAL SCANNER VALIDATES PATTERN. 10% REJECT ESTIMATE.
3. OPERATOR LOADS CASSETTE FOR SCREEN PRINT & FIRE SYSTEM.
4. SYSTEM APPLIES FRONT BUS BAR & FIRES. (SEPARATE PRINT STEP NEEDED SINCE PATTERN IS THICKER THAN FINE GRID.)
   OPTICAL SCANNER VALIDATES PATTERN BEFORE FIRING. 1% BUS BAR REJECTS ESTIMATED.
   REJECTS ARE LOADED INTO A CASSETTE BY BELT->CASSETTE STACKER FOR REWORK.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT	UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
SCREEN PRINT & DRY SYSTEM-2	1800.00	SH/HR	111.0%	$ 125000.	80.0%	1600.
OPTICAL SCANNER	1800.00	SH/HR	111.0%	$ 50000.	80.0%	16.
BELT->CASSETTE STACKER	1800.00	SH/HR	111.0%	$ 15000.	80.0%	0.
SCREEN PRINT & FIRE SYSTEM-2	1800.00	SH/HR	101.0%	$ 200000.	80.0%	1600.
OPTICAL SCANNER	1800.00	SH/HR	101.0%	$ 50000.	80.0%	16.
BELT->CASSETTE STACKER	1800.00	SH/HR	101.0%	$ 15000.	80.0%	0.

LABOR

(DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	SCREEN PRINT & DRY SYSTEM-2	2.000E-01		
HOURLY OPERATOR	SCREEN PRINT & FIRE SYSTEM-2	2.000E-01		
MAINTENANCE	SCREEN PRINT & DRY SYSTEM-2	2.000E-01		
MAINTENANCE	SCREEN PRINT & FIRE SYSTEM-2	2.000E-01		
MAINTENANCE	OPTICAL SCANNER	1.000E-02		
FOREMAN	DL	1.000E-01		

SUPPLIES/EXPENSES

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	UNITS	BASE
ELECTRICITY	0.0	1.400E+01	KWH.	PER AVAILABLE INVESTMENT-HOUR OF SCREEN PRINT & DRY SYSTEM-2
ELECTRICITY	0.0	2.900E+01	KWH.	PER AVAILABLE INVESTMENT-HOUR OF SCREEN PRINT & FIRE SYSTEM-2
ELECTRICITY	0.0	1.000E-01	KWH.	PER AVAILABLE INVESTMENT-HOUR OF OPTICAL SCANNER
SCREENS	0.0	2.880E+00	$	PER AVAILABLE INVESTMENT-HOUR OF SCREEN PRINT & DRY SYSTEM-2
SCREENS	0.0	1.920E+00	$	PER AVAILABLE INVESTMENT-HOUR OF SCREEN PRINT & FIRE SYSTEM-2
SQUEEGEES	0.0	4.000E-01	$	PER AVAILABLE INVESTMENT-HOUR OF SCREEN PRINT & DRY SYSTEM-2
SQUEEGEES	0.0	4.000E-01	$	PER AVAILABLE INVESTMENT-HOUR OF SCREEN PRINT & FIRE SYSTEM-2
SOLVENT-INK	0.0	1.440E-01	CM**3	PER INPUT UNIT. % UNITS= 111.0%
SOLVENT-INK	0.0	1.440E-01	CM**3	PER INPUT UNIT. % UNITS= 101.0%
THERMOCOUPLE,ETC.	0.0	6.060E-04	$	PER INPUT UNIT. % UNITS= 111.0%
THERMOCOUPLE,ETC.	0.0	6.060E-04	$	PER INPUT UNIT. % UNITS= 101.0%
INK AG-FRONT FINE GRID	0.0	3.920E-03	$	PER INPUT UNIT. % UNITS= 100.0%
INK AG-FRONT FINE GRID LOST	0.0	1.600E-03	$	PER INPUT UNIT. % UNITS= 11.0%
INK AG-FRONT BUS BAR	0.0	8.950E-03	$	PER INPUT UNIT. % UNITS= 100.0%
INK AG-FRONT BUS BAR LOST	0.0	3.760E-03	$	PER INPUT UNIT. % UNITS= 1.0%

Figure 26. Continued.

PROCESS PARAMETERS:THICK AG METAL-BACK:AUTO 04/18/77 09:51:24 PAGE 51

ESTIMATE DATE:02/03/77 BY:WERNER KERN, X2094, RCA LABS, 03-076 CLASS:METALLIZATION
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:FUTURE MATERIAL FORM:3" WAFER.
INPUT UNIT:SHEETS OUTPUT UNIT:SHEETS TRANSPORT IN:500 SHEET CASSETTE TRANSPORT OUT:500 SHEET CASSETTE
PROCESS YIELD: 99.0% YIELD GROWTH PROFILE: 0
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:VALUE IN$
PERFORMANCE FACTORS-I(R)/I(SC): 1.000000E+00 V(R)/V(OC): 1.000000E+00 F(R)/F: 1.000000E+00

INPUT UNITS:	0.	0.	0.
FLOOR SPACE,FT**2:	0.	0.	0.

DESCRIPTION:SCREEN PRINTING AND SINTERING CONDUCTIVE NETWORK-BACK

ASSUMPTIONS:

1. 3" DIAMETER WAFER, 12-14 MILS THICK,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. BACK METALLIZATION PATTERN MUST BE SCREEN PRINTED FIRST.
3. AG PASTE: $5.42/TROY OZ. = $.1743/GM, 80% AG, WHEN AG COSTS $4.40/TROY OZ.
   DENSITY OF AG PASTE=3.756/CM**3. (31.1G=1 TROY OZ.)
   2:1 RATIO FOR INK THICKNESS TO POST FIRING AG THICKNESS.
   NOTE: 5 MILS THINNEST LINE POSSIBLE. WIDTH GREATER THAN OR EQUAL TO 4 TIMES THICKNESS.
4. BACK AG GRID: 25% COVERAGE, 8.5 MICRONS THICK AFTER FIRING.
5. SCREEN PRINT & FIRE SYSTEM:

ITEM	COST	POWER	COMMENTS
LOADER	10.7K	1KW	INSERTS WAFER INTO PRINTER
PRINTER	24.4K	1KW	PRINTER APPLIES PATTERN
COLLATOR	10.0K	1KW	FORMS PARALLEL ROWS FOR DRYER.
DRYER	20.0K	10KW	DRIES INK TO PREVENT SMEARING.
FURNACE	45.0K	15KW	SINTERS PATTERN AT 550 C.
RELOADER	14.7K	1KW	RELOADS WAFERS INTO CASSETTE.
CASSETTES	4.0K	-	HOLDS WAFERS FOR PRINTER.
TOTALS	128.8K	29KW	

   ********NOTE: $200K ESTIMATED FOR ADVANCED SYSTEM.
6. BELT->CASSETTE LOADER CAN DO 6000 WAFERS/HR.
7. SCREEN AT $23, REPLACED 2 TIMES PER DAY.
   SQUEEGES AT $.40, REPLACED ONCE PER HOUR.
8. COST OF 1.5% BACK REWORK IGNORED.
9. FIRING OF BACK NEEDED SO THAT PASTE IS NOT REMOVED IN CASE OF FRONT GRID REWORK.

PROCEDURE

1. OPERATOR LOADS CASSETTE FROM PREVIOUS STEP INTO LOADER.
2. SCREEN PRINT & FIRE SYSTEM APPLIES BACK GRID.
   OPTICAL SCANNER VALIDATES PATTERN. 0.5% REJECTS REWORKED.
   REJECTS ARE LOADED INTO A CASSETTE BY BELT->CASSETTE STACKER FOR REWORK.
3. CASSETTE TRANSFERRED TO FRONT METALLIZATION PROCESS.
4. REJECTS ARE REWORKED & RECYCLED.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT	UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
SCREEN PRINT & FIRE SYSTEM-2	1800.00	SH/HR	100.5%	$ 200000.	80.0%	1600.
OPTICAL SCANNER	1800.00	SH/HR	100.5%	$ 50000.	80.0%	16.
BELT->CASSETTE STACKER	1800.00	SH/HR	100.5%	$ 15000.	80.0%	0.

Figure 27. Process parameters - back metallization.

PROCESS PARAMETERS:THICK AG METAL-BACK:AUTO 04/18/77 09:51:24 PAGE 51.1

LABOR
(DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	SCREEN PRINT & FIRE SYSTEM-2	2.000E-01		
MAINTENANCE	SCREEN PRINT & FIRE SYSTEM-2	2.000E-01		
MAINTENANCE	OPTICAL SCANNER	1.000E-02		
FOREMAN	DL	1.000E-01		

SUPPLIES/EXPENSES

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	UNITS	BASE	
ELECTRICITY	0.0	2.900E+01	KWH.	PER AVAILABLE INVESTMENT-HOUR OF SCREEN PRINT & FIRE SYSTEM-2	
ELECTRICITY	0.0	1.000E-01	KWH.	PER AVAILABLE INVESTMENT-HOUR OF OPTICAL SCANNER	
SCREENS	0.0	1.920E+00	$	PER AVAILABLE INVESTMENT-HOUR OF SCREEN PRINT & FIRE SYSTEM-2	
SQUEEGEES	0.0	4.000E-01	$	PER AVAILABLE INVESTMENT-HOUR OF SCREEN PRINT & FIRE SYSTEM-2	
SOLVENT-INK	0.0	1.440E-01	CM**3	PER INPUT UNIT. % UNITS=	101.0%
THERMOCOUPLE,ETC.	0.0	6.060E-04	$	PER INPUT UNIT. % UNITS=	101.0%
INK AG-BACK GRID	0.0	1.280E-02	$	PER INPUT UNIT. % UNITS=	100.0%
INK AG-BACK GRID LOST	0.0	5.380E-03	$	PER INPUT UNIT. % UNITS=	0.5%

Figure 27. Continued.

- Complex in bath of H_2O-C_3H_7OH (wetting agent)-NH_4OH (neutralizer)-NH_4Cl (complexant).

4 First Plating and Mask Removal

- Immerse in bath containing $NiCl_2$, NaH_2PO_2, $Na_3C_6H_5O_7$, NH_4Cl, NH_4OH, and H_2O.
- Plate at 80°C for 45 s to deposit a P-containing Ni film of 500 to 750 Å thickness.
- Rinse in deionized water.
- Remove organic mask coating by solvent extraction.

5 Sintering

- Transfer the wafers onto conveyor belt and into furnace.
- Expose to 550° to 600°C in an atmosphere of N_2-H_2 to create nickel silicide.

6 Nickel Stripping

- Immerse in HNO_3.
- Rinse in deionized water.
- Apply light oxide etch in HF-NH_4F-H_2O solution.
- Rinse in deionized water.

7 Second Plating

- Re-immerse in nickel plating bath to deposit 0.3 to 0.5 μm of Ni (P).
- Rinse in deionized water.

8 Fluxing and Solder Deposition

- Immerse in flux solution.
- Drain, dry, and preheat the wafers.
- Introduce into 5% Sn-95% Pb solder bath at 350°C.
- Hold in bath for an optimal residence time.
- Withdraw at a controlled velocity.

9 Final Cleaning

- Remove flux residue by immersion in ultrasonic cleaning bath.
- Rinse in deionized water.
- Dry mechanically.

(3) Cost Estimation - Estimates of production cost were based on the assumption that 1×10^8 wafers of 3-in. diameter are to be processed in a three-shift, 24-hour operation of 345 days per year. Unit batches of 1000 wafers would be

processed automatically through the process sequence outlined in the previous section. Calculation of the time requirements for each process step indicates that five separate production lines operating in parallel would be required, each line producing 2×10^7 wafers per year. Not considering the yield factor, cost per wafer has been computed as approximately $0.30, of which 64% accounts for materials, 19% for equipment, and 17% for labor. The product yield is estimated to be no better than 95% due to the large number of process steps. It is quite obvious from these figures that this method of metallization is considerably more expensive than the screen-printing process, as had been predicted from preliminary estimates.

c. Metal Thickness - A central goal of the analyses performed under this contract is the maximization of the cost effectiveness of every step in module fabrication. The attainment of that goal requires the simultaneous minimization of cost and maximization of power delivered within the constraints that may be imposed by the technologies used. The analytic procedure described here provides a general, quantitative framework for such optimizations. This procedure begins by the careful characterizations of the two contributing factors to the $/W cost (a) the cost per unit area for every "step" and (b) the power loss associated with each step. It turns out that the different characters of these two factors have a profound impact on the optimization. The notion of a succession of independent "steps" forming a complete module is vital; experience shows that many fabrication process steps are independent to the first order and that those processes which interact strongly can be grouped into a single "step" that can be analyzed as a whole. For example, the fine grid metallization pattern can be optimized without reference to the junction characteristics and the bus bar can be analyzed independently of the fine grid pattern under most conditions.

This procedure is derived and applied to the important problems of fine grid and bus bar metallizations where the effect is dramatic. It is extremely important to maximize the performance of the system, and additional costs such as adding considerable Ag to recover a few percent of system performance can be cost effective. Below we will derive the criterion.

These applications provide instructive design specifications and indicate the generality of the basic approach. Among the other "steps" that may

be amenable to this type of analysis are the quantity and quality of the Si itself.

(1) General Derivation - The quantity to be minimized in all cases is the total cost per watt

$$\frac{\$}{W} = \frac{K}{G_o} \tag{1}$$

where K ≡ total cost per unit of module area and G_o ≡ output power per unit of module area. We first treat the cost factor and show the nontrivial result that it may be expressed as

$$K = \sum_{j=1}^{n} C_j \tag{2}$$

where there are n of the independent "steps" in the entire fabrication process *including* the silicon cost, and the C_j are a set of effective step costs per unit area that are, in general, not simply the individual step costs.

Equation (2) is proved by the following argument. Let D ≡ total cost of fabricating A_p cm^2 of complete modules that have cell coverage fraction ϕ so that ϕA_p = total cell area. Then we separate the steps into two groups, those involving the full module area and those involving only the cell area

$$D = A_p \left[\frac{k_n}{Y_n} + \frac{k_{n-1}}{Y_n Y_{n-1}} + \cdots + \frac{k_i}{Y_n \cdots Y_i} \right] \text{ for module steps}$$

$$+ \phi A_p \left[\frac{k_{i-1}}{Y_n \cdots Y_{i-1}} + \cdots + \frac{k_1}{Y_n \cdots Y_1} \right] \text{ for cell steps}$$

where k_i ≡ actual cost/unit area of performing step i and Y_i ≡ yield of step i. This shows the well-known impact that each yield factor has on all *preceding* steps. Now we define

$$C_j \equiv \begin{cases} \dfrac{k_j}{Y_n \cdots Y_j} & \text{for all } \textit{module} \text{ steps} \\ \phi \dfrac{k_j}{Y_n \cdots Y_j} & \text{for all } \textit{cell} \text{ steps} \end{cases} \tag{3}$$

Since $K = D/A_p$, these definitions lead to Eq. (2) and show quantitatively what the C_j are. To deal with any individual step m, we simply subtract out its cost contribution per unit module area

$$K' \equiv K - C_m \tag{4}$$

Next we treat the output power density of the module G_o by relating it to G, the power density potentially available:

$$G_o = FG \tag{5}$$

where F is a fraction that may exceed one, depending on the choice that is made for G; that choice is quite arbitrary and might correspond to a 10% module efficiency or any other convenient value. The feature of major importance here is that F is generally the cumulative *product* (not sum) of the individual step factors

$$F = \prod_{j=1}^{n} f_j \tag{6}$$

where each f_j must be self-consistently defined as the fraction of potentially available power that is actually obtained after step j. (These f_j are the same as "performance indexes" in our first report.) To deal with an individual step m we now must separate it by dividing by its performance contribution

$$F' \equiv \frac{F}{f_m} \tag{7}$$

Now using these relations in Eq. (1)

$$\frac{\$}{W} = \frac{K}{G_o} = \frac{K}{FG} = \frac{1}{F'G}\left(\frac{K' + C_m}{f_m}\right) = \frac{K'}{F'G}\left(\frac{1 + C_m/K'}{f_m}\right)$$

$$= \frac{K'}{F'G}\left(\frac{1 + \kappa_m}{f_m}\right) \tag{8}$$

where $\kappa_m \equiv C_m/K'$ is the cost fraction of step m.

Equation (8) shows a result of first importance: *every step-efficiency factor f_m has its fractional impact on the TOTAL cost per watt.* This is a

direct consequence of the multiplicative roles of the f_j in contrast to the additive contributions of the cost terms. In physical terms it says that any loss in power must in effect be paid for by making more complete modules. It follows then that no step can be optimized properly by considering only its own cost and performance; rather an equation of the form of Eq. (8) must be minimized.

Next we develop the appropriate optimization conditions for Eq. (8). To aid in this we introduce the fractional power *loss* associated with any step $\lambda_j \equiv 1 - f_j$. Using this in Eq. (8) gives

$$\frac{\$}{W} = \frac{K'}{F'G}\left[\frac{1 + \kappa_m}{1 - \lambda_m}\right] \tag{9}$$

This is the form in which we minimize the \$/W contribution of step m by differentiating with respect to any relevant variable of step m. It is clear that when such a derivative is set equal to zero, the prefactors K'/F'G always drop out since by definition they cannot contain the variable of step m. Thus only the term in brackets in Eq. (9) need be minimized. It is trivial to show that the condition for minimization is

$$\frac{1}{1 + \kappa_m}\frac{d\kappa_m}{dx} = -\frac{1}{1 - \lambda_m}\frac{d\lambda_m}{dx} \tag{10}$$

where x represents any appropriate variable for step m. In nearly all cases that will be acceptable we will find that $\kappa_m << 1$ (i.e., $C_m << K'$) and $\lambda_m << 1$. Then we obtain the simplified approximate relation

$$\frac{d\kappa_m}{dx} = -\frac{d\lambda_m}{dx} \tag{11}$$

We note also that in this approximation

$$\frac{\$}{W} \simeq \frac{K'}{F'G}\left[1 + \kappa_m + \lambda_m\right] \tag{12}$$

and we can set $K' \simeq K$ and $F' \simeq F$.

This is the general procedure. It can be applied to every fabrication step for which there is information enough to evaluate both κ and λ.

(2) Application to Front Metallizations - The optimization procedure described above is now applied first to the bus bar and then to the fine grid on the front of solar cells by finding the optimum geometry for each that minimizes the cost/W. We make use of a fortuitous result for these metallization steps: ϕ, the cell coverage fraction of the module, $\underset{\sim}{\sim}$ 0.83 and the product of the estimated yields for all steps following metallization is $\underset{\sim}{\sim}$ 0.87 so that in Eq. (3) we find that $C_m \underset{\sim}{\sim} k_m$. Furthermore, the metallization process to be evaluated, screen-printed Ag, has a cost that can be expressed as $C_m \underset{\sim}{\sim} h + \beta v_m$ where the contribution h is independent of the amount of metal (it is basically machinery and handling costs) and v_m is the volume of metal used, with β an appropriate coefficient. So differentiating as in Eq. (11) with amount of metal as the variable, causes the term h to drop out and only the metal cost need be evaluated in C_m, hence κ_m.

The metal cost/cm^2 = pv_m/A where $p \equiv$ price/cm^3 of metal in its final condition (i.e., after firing) and $A \equiv$ cell area. But $v_m = ta_m = tSA$ where $a_m \equiv$ area of metal, $t \equiv$ metal thickness, and $S \equiv$ shadow fraction of metal on cell. So

$$C_m = pSt \tag{13}$$

$$\kappa_m = pSt/K' \tag{14}$$

Before proceeding to specific power loss evaluations we note that our calculations have been revised to optimize the \$/W for performance averaged over a day rather than just at solar noon. This reduces all resistive losses by a factor of $\pi/4$.

First this optimization procedure is applied to the bus bar; we limit consideration to a single, central bar for simplicity. It has already been shown in Quarterly Report No. 3 [1] that when the fine grid line length ℓ is determined (by cell size, for example), the treatment of the bus bar becomes independent of the fine grid design. For the bus bar the only sources of loss are the shadowing and resistive drop of the metal; it can be shown that there is no way of simultaneously optimizing both the metal thickness and the shadow fraction of the bus bar. This can be seen physically by the recognition that minimum loss for any metal volume would lead to zero shadow fraction (i.e.,

bar width) and infinite thickness. Therefore, one additional constraint must be imposed on the problem. We choose this constraint as a condition that will give the *thickest* line that seems printable. (The bus bar will have to be printed separately from the fine grid although they can be fired together.) One way of achieving this thick-bar condition is to require that its thickness t_2 always be 1/4 of the line width W. (Since the thickness shrinks roughly in half during firing, this represents a thickness/width ratio of ∿1/2 at the printing, a reasonable upper limit on t_2.)

The shadow fraction of the bus bar is $S_2 = W/\ell_{eff} = A/L$ with L ≡ bus bar length. Thus, since $W = 4t_2$

$$S_2 = 4t_2/\ell_{eff} \tag{15}$$

and from Eqs. (13) and (14)

$$C_m = pS_2t_2 = 4pt_2^2/\ell_{eff} \tag{16}$$

$$\kappa_m = 4pt_2^2/K'\ell_{eff} \tag{17}$$

so that

$$\frac{d\kappa_m}{dt} = \frac{8pt_2}{K'\ell_{eff}} \tag{18}$$

The fractional loss is the sum of shadow and line drop

$$\lambda_m = S_2 + \frac{J}{V}\frac{\rho_m}{S_2t_2}\frac{L^2}{3} = \frac{4t_2}{\ell_{eff}} + \frac{J}{V}\frac{\rho_m}{4t_2^2}\frac{L^2}{3}\ell_{eff} \tag{19}$$

where ρ_m ≡ metal resistivity. Then

$$\frac{d\lambda_m}{dt} = \frac{4}{\ell_{eff}} - \frac{1}{t^3}\left(\frac{J}{V}\frac{\rho_m}{6}L^2\ell_{eff}\right) \tag{20}$$

Now invoking the optimization condition (11), we obtain an equation for the optimum bar thickness t_{2opt}.

$$\frac{8p}{K'\ell_{eff}}\, t_{2opt} + \frac{4}{\ell_{eff}} - \frac{1}{t_{2opt}^3}\left(\frac{J}{V}\,\frac{\rho_m}{6}\, L^2\ell_{eff}\right) = 0 \qquad (21)$$

which must be solved numerically. For a 7.6-cm (3-in.) wafer, L = 7.6, ℓ_{eff} = 6 cm. We take also J/V = 0.05 $(\Omega\text{-cm}^2)^{-1}$, p = \$1.30/cm^3 and $\rho_m = 3.2 \times 10^{-6}$ Ω-cm for screen-printed Ag and K' = \$0.0125/cm^2 (∿\$1/W). This leads to t_{2opt} = 150 μm so that W ≳ 0.60 mm and S_2 = 0.010. The total fractional loss due to the bar is evaluated now by Eq. (19) giving λ_m = 0.03 while Eq. (17) gives κ_m = 0.015.

Next we treat the fine grid pattern using the same basic approach, but we find the problem significantly more complicated because there are four power-loss terms aside from the cost term. First we note that C_m and κ_m are given by the same relations as for the metal of the bus bar, Eqs. (13) and (14). As shown in Quarterly Report No. 3 [1], the fractional power losses are given by

$$\lambda_m = S_1 + \frac{J}{V}\left[\frac{\rho_s}{S_1^2}\,\frac{w^2}{12} + \frac{\rho_c}{S_1} + \frac{\rho_m \ell^2}{3\, S_1 t_1}\right] \qquad (22)$$

where w ≡ the fine line width, ρ_s ≡ Si sheet resistivity (Ω/□), ρ_c ≡ metal-Si specific contact resistance (Ω-cm^2). (We have transformed the formulas of Quarterly Report No. 3 to express all the losses in terms of S rather than the line spacing d.) We fix w = 125 μm as the minimum printable width.

Now the minimization of \$/W requires that we optimize both t_1 and S_1 simultaneously. (In contrast to the bus bar case, this is possible here.) To do this we use the form of \$/W given by Eq. (12) and minimize $(\kappa_m + \lambda_m)$ with respect to both variables t_1 and S_1. Partial differentiation of $(\kappa_m + \lambda_m)$ with respect to t_1 gives, when set equal to zero, the first condition

$$t_{1opt} = \frac{\ell}{S_1}\sqrt{\frac{K' J \rho_m}{3\, pV}} \qquad (23)$$

This has the important consequence, when substituted into $(\kappa_m + \lambda_m)$, that

$$\kappa_m(\text{cost fraction}) = \text{line loss fraction} = \ell \sqrt{\frac{pJ\rho_m}{3\ KV}}$$

They are thus *independent* of S_1 and t_1 so now differentiation of $(\kappa_m + \lambda_m)$ with respect to S_1 gives the surprisingly simple equation for S_{1opt}

$$S_{1opt}^3 - \left(\frac{J}{V}\rho_c\right) S_{1opt} - \left(\frac{J}{V}\frac{\rho_s w^2}{6}\right) = 0 \qquad (24)$$

This is a remarkable result in that the optimum shadow fraction is independent of the metal resistivity, length, price, and the module cost. In fact, when ρ_c is small ($\lesssim 10^{-3}\ \Omega\text{-cm}^2$)

$$S_{1opt} = \left(\frac{J\rho_s w^2}{6V}\right)^{1/3} \qquad (25)$$

so S_1 varies as the cube root of ρ_s.

The metal thickness, given by Eq. (23) once S_1 is found, is the only place where the costs and other parameters of the metal are found. Other useful consequences of these results are that varying the cell size has no effect on S_{1opt} and a simple linear effect on t_{1opt} through ℓ.

Taking again the example of the 7.6-cm wafer, with ℓ = 3 cm, J/V = 0.05 $(\Omega\text{-cm}^2)^{-1}$ and ρ_s = 50 Ω/□ for the Si, $\rho_c = 10^{-3}\ \Omega\text{-cm}^2$ and using w = 125 μm, we find S_1 = 0.040. Then using the other parameter values given after Eq. (21), κ_m = 0.007 and t_{1opt} = 16 μm. With these optimized values of t_1 and S_1 we can readily calculate λ_m = 0.068. (This entire optimization and evaluation is performed numerically with a straightforward computer program.)

Combining now the optimized contributions of the fine grid and the bus bar

$$\lambda_{Tot} = \lambda_1 + \lambda_2 = 0.068 + 0.030 = 0.098$$
$$\kappa_{Tot} = \kappa_1 + \kappa_2 = 0.007 + 0.015 = 0.022 \qquad (26)$$

so the performance penalties far outweigh the cost contributions. These terms are to be used in Eq. (12) to evaluate the cost/W contributions of the two metallizations under optimum conditions.

An illustration of the use of these results appears in Fig. 28 for 7.6-cm wafers with total module cost per W as the independent variable. The lowest curve shows the cost of the optimum amount of Ag to be used as the module or system cost changes. It can be seen that for more expensive systems, it is worthwhile to increase greatly the amount of Ag to obtain a gain in performance.

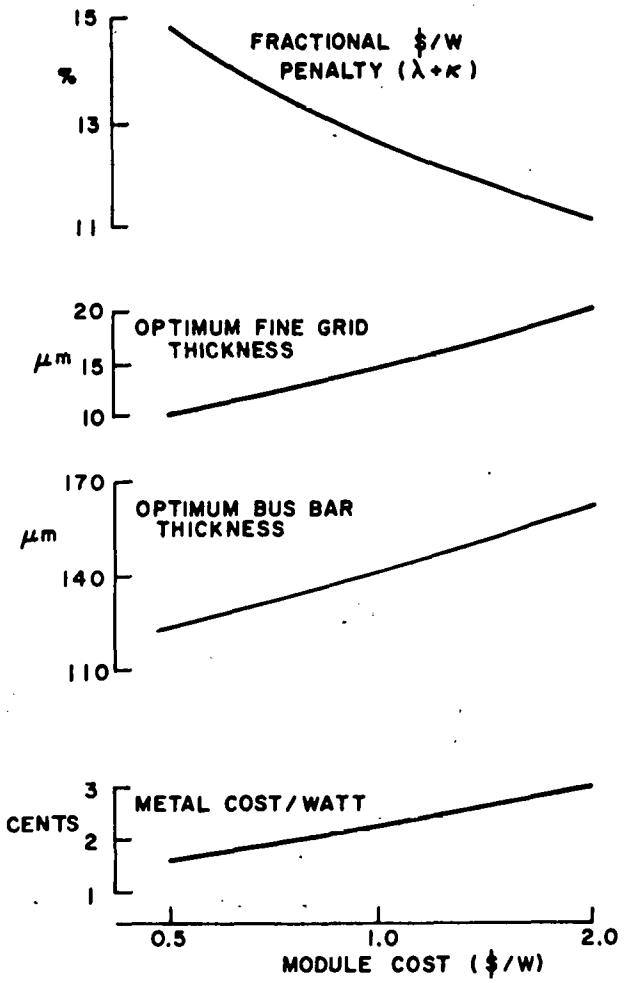

Figure 28. Effect of total module cost in $/W (plotted logarithmically) on several front metallization parameters of 7.6-cm-diam cells with screen-printed Ag lines having straight, parallel sides. The curve ($\lambda + \kappa$) is obtained from totals like those in Eq. (26).

Another use of these calculations is in connection with the question of how large should the individual cells be; this will become an important question as large-area sheets become available. Apart from any other considerations, it is clear qualitatively that as cell size increases, resistance losses will increase and the amount of Ag needed *per* cm^2 will increase. It is necessary therefore to determine quantitatively what impact those increases will have on the $/W because they will have to be offset by potential benefits in handling fewer cells (e.g., fewer interconnections in the module). We have calculated the variation in optimum $/W as a function of cell size, using as reference a $1/W module with 7.6-cm (3-in.) cells. The results shown in Fig. 29 indicate, for example, that an increase from 3- to 5-in. (12.7-cm) wafers requires that 4% of the $/W must be gained elsewhere in the fabrication just to compensate for the penalty arising from the front metals alone; the back contact metals will undoubtedly add a few percent more penalty, but there is not sufficient information available now for the quantitative evaluation. In our cost summary we have used the same amount of metal on the back as on the front. See subsection D below for a discussion of cell size implications.

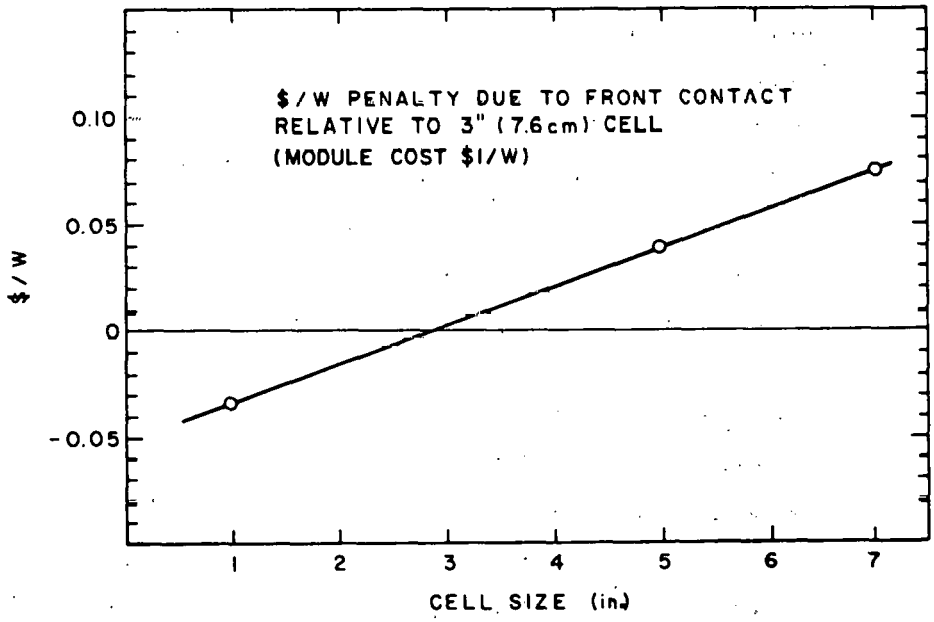

Figure 29. Calculated penalty in $/W due to optimized cost and performance contributions of combined fine grid and bus bar on cell front as a function of cell size. The penalty is shown as a change from a reference module cost of $1/W for all cell sizes with the zero arbitrarily set at the 3-in. (7.6-cm) wafer.

8. Junction Formation

Ion implantation is now a well-established process in the semiconductor industry. Its application to the fabrication of solar cells has been successfully demonstrated with reported AM-1 efficiencies in the 10 to 13% range with higher efficiency expected in the near future. The major advantages of ion implantation applied to high-volume production of solar cells are control, reproducibility, and the elimination or reduction of wet chemicals and gases required by other junction-formation processes.

In this section, a broad outline is given of a proposed ion-implantation process capable of the high throughput required for large-scale, low-cost solar cell production.

First, it is assumed that advances in the development of ion implanters will result in implant machines capable of producing 10-mA beams of both n and p-type dopants in a sequential operation. This is not an unreasonable assumption since production machines are now available which can deliver more than 2 mA of phosphorus. A 10-mA machine could process approximately 100 cm^2 of silicon area in 1 s, which approximately equals the area of both sides of a 3-in.-diam wafer, so that 3600 wafers could theoretically be implanted in 1 h. This calculation assumes dose requirements of $\sim 1 \times 10^{15} cm^{-2}$ of phosphorus on the top side and $5 \times 10^{14} cm^{-2}$ boron on the back.

Since material consumption is low using an ion-implantation process, major cost reductions can be achieved by maximum use of automation. The system described here processes 2000 3-in. wafers/h, a reduction from the 3600/h, allowing time for beam scanning and beam loss at edges. A schematic block diagram of one possible embodiment of such a system is shown in Fig. 30.

In this system wafers are manually moved to the implant station in two 500-wafer cartridges, and one is automatically transferred to 50-wafer cassettes. The two input chambers are air-locked and operate in "push-pull" fashion so that no time is lost during transfer loading from cassettes to the platens. The platens are designed to hold several wafers during implant and to provide for a masked implant (planar junction) on the active side of the cell and a full-area implant on the reverse side. It is assumed that the input chamber pump-down time is 1 min. The platens then move, belt driven, from either chamber to the beam slit and are implanted from opposite sides.

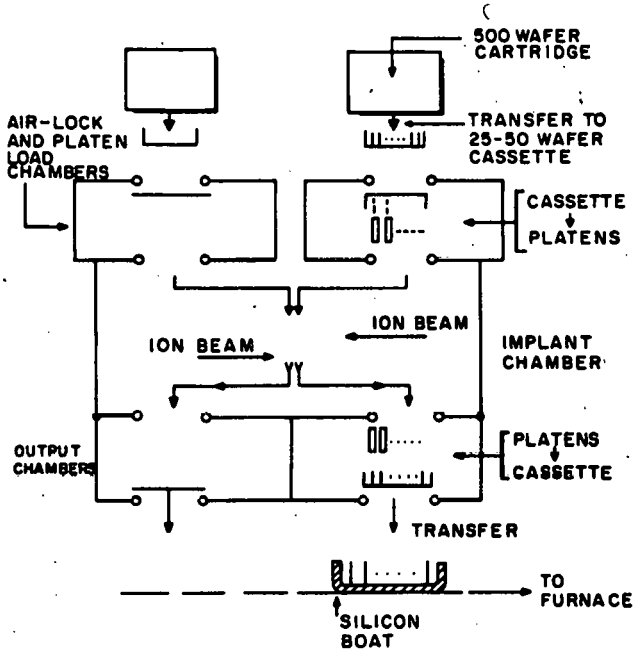

Figure 30. Schematic block diagram - ion implantation and junction formation. (Transfer to silicon boat must include flipping wafers so that like sides face.)

Wafer feed can proceed in either direction, so that when the first 50 wafers are done, the second air-lock chamber begins to discharge wafers. Implanted wafers then move, again belt driven, to the output chambers, where the wafers are transferred to cassettes and then to silicon boats.

After implantation, junction annealing and drive-in are required. The silicon boats ride on a continuous belt through a multizone diffusion furnace. The time and temperature requirements for annealing and drive-in will vary with the type of dopant used in the junction formation. A typical sequence for an n/p/p+ solar cell with phosphorus and boron dopants is 15 min at 1000°C with temperature gradients before and after the 1000°C hot-zone to allow for slow warm-up, cooling, and annealing of the junction.

The process parameters for the ion-implantation step, diffusion step, and inspection step are shown in Figs. 31, 32, and 33.

9. Process: Z Wafer Cleaning

This process is designed to assure a clean surface on the silicon sheet before it is started through the automated array process. It consists of a

PROCESS PARAMETERS:ION IMPLANTATION:2 SIDES 04/18/77 09:51:24 PAGE 29

ESTIMATE DATE:01/12/77 BY:RCA ESTIMATES CLASS:ION IMPLANTATION
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:FUTURE MATERIAL FORM:3" WAFER.
INPUT UNIT:SHEETS OUTPUT UNIT:SHEETS TRANSPORT IN:500 SHEET CASSETTE TRANSPORT OUT:SILICON BOAT
PROCESS YIELD: 99.0% YIELD GROWTH PROFILE: 0
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:FRACTION OF INPUT UNIT VALUE
PERFORMANCE FACTORS-I(R)/I(SC): 1.000000E+00 V(R)/V(DC): 1.000000E+00 F(R)/F: 1.000000E+00

INPUT UNITS:	0.	0.	0.
FLOOR SPACE,FT**2:	0.	0.	0.

DESCRIPTION:ION IMPLANTATION-BOTH SIDES

ASSUMPTIONS:

1. PROCESS FOLLOWED BY DIFFUSION STEP
2. DOUBLE IMPLANTER. ONE IMPLANTER FOR EACH SIDE OF WAFER.
3. FRONT SIDE OF ONE WAFER IMPLANTED SIMULTANEOUSLY WITH BACK SIDE OF A SECOND WAFER.
3. 10 GAL/MIN OF COOLING WATER AT 20 DEG. C. NEEDED PER IMPLANTER.

PROCEDURE

1. CARTRIDGE FEED SYSTEM FEEDING IMPLANTER.
2. FIRST IMPLANTER FEEDS SECOND IMPLANTER FOR BACK SIDE IMPLANTATION
3. SECOND IMPLANTER UNLOADS DIRECTLY INTO SILICON DIFFUSIION POAT.
   ALTERNATE WAFERS ARE FLIPPED DURING LOAD SO THAT LIKE SIDES FACE.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
ION IMPLANTER(C)	2000.00 SH/HR	100.0%	$ 700000.	85.0%	850.

LABOR

(DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	ION IMPLANTER(C)	4.000E-01		
MAINTENANCE	ION IMPLANTER(C)	1.000E-01		
FOREMAN	DL	1.000E-01		

SUPPLIES/EXPENSES

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	UNITS	BASE
ELECTRICITY	0.0	4.000E+01	KWH.	PER AVAILABLE INVESTMENT-HOUR OF ION IMPLANTER(C)
LIQUID NITROGEN	0.0	1.000E+04	CM**3	PER AVAILABLE INVESTMENT-HOUR OF ION IMPLANTER(C)
FILAMENTS/INSULATORS	8.000E+03	0.0	$	PER AVAILABLE INVESTMENT-HOUR OF ION IMPLANTER(C)
WATER-COOLING	0.0	2.400E+06	CM**3	PER AVAILABLE INVESTMENT-HOUR OF ION IMPLANTER(C)
ION SOURCE GAS	0.0	2.280E+00	$	PER AVAILABLE INVESTMENT-HOUR OF ION IMPLANTER(C)

FOR INVESTMENT OR LABOR BASES, "FIXED PART" IS MULTIPLIED BY NO. OF BASE UNITS PRESENT.

Figure 31. Process parameters - ion implantation.

PROCESS PARAMETERS:DIFFUSION 04/18/77 09:51:24 PAGE 19

ESTIMATE DATE:01/12/77 BY:FRED MAYER, X6334, SOMERVILLE, ZONE 8 CLASS:DIFFUSION
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:FUTURE MATERIAL FORM:3" WAFER.
INPUT UNIT:SHEETS OUTPUT UNIT:SHEETS TRANSPORT IN:SILICON BOAT TRANSPORT OUT:500 SHEET CASSETTE
PROCESS YIELD: 95.0% YIELD GROWTH PROFILE: 0
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:FRACTION OF INPUT UNIT VALUE
PERFORMANCE FACTORS-I(R)/I(SC): 1.000000E+00 V(R)/V(OC): 1.000000E+00 F(R)/F: 1.000000E+00

INPUT UNITS:	0.	0.	0.
FLOOR SPACE,FT**2:	0.	0.	0.

DESCRIPTION:DOPANTS ARE DRIVEN INTO SILICON BY HEAT TREATMENT IN FURNACE

ASSUMPTIONS:

1. 3" DIAMETER WAFER, 12-14 MILS THICK,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. DIFFUSION VIA ION IMPLANTATION OR DOPED OXIDE.
3. COIN STACK APPROACH (NOT CONSIDERED) NEEDED FOR MORE VOLATILE SOURCES.
4. 40 MINUTE DIFFUSION TIME AT 1000 C. AND 90 MINUTE PREPROGRAMMED COOLING TO 750 C. + 10 MIN. HOLD AT 600C. + AIR QUENCH.
5. 250 SILICON BOATS, EACH 12" LONG AND 4" WIDE AT $550 EACH NEEDED. 100 WAFERS/BOAT. 3 YR. LIFE.
6. FURNACE HAS 12" BELT, 15' HEAT ZONE, 55' COOLING SECTION, 20' LOAD/UNLOAD SECTION. 30 FT./HR BELT RATE.
7. ALTERNATE WAFERS MUST BE FLIPPED SO THAT LIKE SIDES FACE.
8. P-SIDE AND N-SIDE OF WAFER MUST BE EASILY DIFFERENTIABLE.
9. 100 WAFERS IN EACH INCOMING SILICON BOAT.

PROCEDURE

1. INCOMING WAFERS WITH DIFFUSION SOURCE APPLIED TO BOTH SURFACES. WAFERS HAVE BEEN LOADED INTO A SILICON BOAT BY PRECEDING STEP.
2. BOATS PLACED ONTO MOVING BELT FURNACE.
3. DIFFUSION FOR 40 MIN. AT 1000 C.
4. FORCE AIR COOL OF WAFERS TO ROOM TEMPERATURE.
5. LOADER-FLIPPER TRANSFER OF WAFERS INTO 500 WAFER CASSETTE.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT	UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
LINDBERG FURNACE-12" BELT	9000.00	SH/HR	100.0%	$ 72000.	95.0%	800.
250 12"-SILICON BOATS	9000.00	SH/HR	100.0%	$ 137500.	95.0%	0.
CASSETTE LOADER-FLIPPER	3000.00	SH/HR	100.0%	$ 20000.	95.0%	0.

LABOR

(DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	LINDBERG FURNACE-12" BELT	1.000E+00		
MAINTENANCE	LINDBERG FURNACE-12" BELT	1.000E-01		
MAINTENANCE	CASSETTE LOADER-FLIPPER	1.000E-01		
FOREMAN	DL	5.000E-02		

SUPPLIES/EXPENSES

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	UNITS	BASE
ELECTRICITY	0.0	1.000E+02	KWH.	PER AVAILABLE INVESTMENT-HOUR OF LINDBERG FURNACE-12" BELT
WATER-COOLING	0.0	8.000E+05	CM**3	PER AVAILABLE INVESTMENT-HOUR OF LINDBERG FURNACE-12" BELT
NITROGEN	0.0	4.500E+07	CM**3	PER AVAILABLE INVESTMENT-HOUR OF LINDBERG FURNACE-12" BELT

Figure 32. Process parameters - diffusion.

PROCESS PARAMETERS:POST DIFFUSION INSPECTION:10% 04/18/77 09:51:24 PAGE 32

ESTIMATE DATE:12/22/76 BY:DAVE RICHMAN, X3207, RCA LABS, E-321A CLASS:TEST
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:FUTURE MATERIAL FORM:3" WAFER.
INPUT UNIT:SHEETS OUTPUT UNIT:SHEETS TRANSPORT IN:500 SHEET CASSETTE TRANSPORT OUT:500 SHEET CASSETTE
PROCESS YIELD: 99.0% YIELD GROWTH PROFILE: 0
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:VALUE IN$
PERFORMANCE FACTORS-I(R)/I(SC): 1.000000E+00 V(R)/V(OC): 1.000000E+00 F(R)/F: 1.000000E+00

INPUT UNITS:	0.	0.	0.
FLOOR SPACE,FT**2:	0.	0.	0.

DESCRIPTION:POST DIFFUSION 4-POINT PROBE RESISTIVITY MEASUREMENT:10% SAMPLE.

ASSUMPTIONS:

1. 3" DIAMETER WAFER, 12-14 MILS THICK,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. 100% WAFER SHEET RESISTIVITY TEST.

PROCEDURE

1. OPERATOR LOADS CASSETTE INTO MACHINE.
2. WAFERS AUTOMATICALLY FED TO TEST EQUIPMENT.
3. WAFERS SORTED INTO MAGAZINES.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
SILTEC WAFER SORTER-PROBE	1450.00 SH/HR	10.0%	$ 150000.	80.0%	200.

LABOR

(DL=DIRECT LABOR PERSONSTYL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	SILTEC WAFER SORTER-PROBE	2.500E-01		
MAINTENANCE	SILTEC WAFER SORTER-PROBE	2.000E-01		
FOREMAN	DL	1.000E-01		

SUPPLIES/EXPENSES

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	UNITS	BASE
ELECTRICITY	0.0	5.000E+00	KWH.	PER AVAILABLE INVESTMENT-HOUR OF SILTEC WAFER SORTER-PROBE

Figure 33. Process parameters - inspection.

hot Caro's acid immersion followed by three cascade rinses in deionized water and spin drying.

Caro's acid is especially effective for eliminating any organic or metallic contamination but does not remove particles such as silicon chips. This step may not be necessary depending on the condition of the incoming wafers. It is included to show what the costs of such a cleaning or etching procedure can be if the system is automated. Process parameters are shown in Fig. 34.

D. EFFECT OF SHEET SIZE ON MANUFACTURING COST

All of the analyses have considered 3-in. wafers since the most realistic projections could be made with equipment which exists to handle this material. In this section we will estimate the effect of increasing the wafer size to 5 in.

In the most optimistic (and unrealistic) case, we will assume that there will be no increase in labor or capital cost per unit handled so that each of the processes produces 25/9 W where it produced 1 W before. The material and expense items in terms of $/W in general will remain the same. However, the metallization cost will increase due to the increased current-handling requirements. We have calculated the optimum metallization pattern based on an overall system of $1/W. The cost of the metal increases by $0.046/W. Figure 35 is a summary of this comparison. It is important to emphasize that the performance of these larger cells is poorer, even in the optimized case, than the 3-in. cells, and, therefore, there is a penalty to pay at the system level. The performance is 2.3% poorer. Since the system is assumed to cost $1/W, we will add this penalty, $0.023/W, to the cost of the array module. In this "best case" analysis, the costs for array modules based on 3-in. and 5-in. wafers are almost identical.

A somewhat more detailed estimate is given in Fig. 36. In this case, we assume that the cassettes handling the larger wafers have larger spacing between cells and the wafers must be handled more slowly. It is clear that in processes such as ion implantation, the rate of which is beam limited, there is no change in the capital expenses. In each case we have estimated the reduction in labor capital, materials, and expense. Again we must add $0.023/W

PROCESS PARAMETERS:SYSTEM "Z" WAFER CLEANING 04/18/77 09:51:24 PAGE 2

ESTIMATE DATE:01/12/77 BY:FRED MAYER, X6334, SOMERVILLE, ZONE 8 CLASS:CLEANING
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:NEAR FUTURE MATERIAL FORM:3" WAFER,
INPUT UNIT:SHEETS OUTPUT UNIT:SHEETS TRANSPORT IN:500 SHEET CASSETTE TRANSPORT OUT:500 SHEET CASSETTE
PROCESS YIELD: 99.0% YIELD GROWTH PROFILE: 0
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:FRACTION OF INPUT UNIT VALUE
PERFORMANCE FACTORS-I(R)/I(SC): 1.000000E+00 V(R)/V(OC): 1.000000E+00 F(R)/F: 1.000000E+00

INPUT UNITS:	0.	0.	0.
FLOOR SPACE,FT**2:	0.	0.	0.

DESCRIPTION:WAFERS ARE CLEANED IN SULFURIC/HYDROGEN PEROXIDE MIXTURE

ASSUMPTIONS:

1. 3" DIAMETER WAFER, 12-14 MILS THICK,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. NOTE: DOES NOT REMOVE PARTICLES (DUST,SILICON CHIPS,ETC.)
3. 500 WAFERS/TEFLON CASSETTE
4. 1 TEFLON BOAT PER TANK; 2 TANKS PER HOOD.
5. 7.5 CYCLES/HR X 2 BOATS/CYCLE X 500 WAFERS/BOAT=7500 WAFERS/HR.
   (8 MIN. DRYING CYCLE IS LIMITING FACTOR.)
6. 1 OPERATOR REQUIRED FOR 2 HOODS.
7. NOTE: SYSTEM COST ESTIMATED TO BE $30,000. $15,000 FOR BACKUP.
   TOTAL SYSTEM COST=$45,000 WITH BACKUP.

PROCEDURE

1. TEFLON CASSETTE MANUALLY INSERTED IN TANK (1 MIN.)
2. 7 MINUTES IN HOT CAROS ACID.
3. AUTOMATIC TRANSFER TO 1ST CASCADE RINSE, 8 MINUTE RINSE.
4. AUTOMATIC TRANSFER TO 2ND & 3RD RINSES, EACH ABOUT 3 MINUTES.
5. AUTOMATIC TRANSFER TO HOT AIR TUNNEL. DRY FOR 8 MINUTES.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT	UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
SYSTEM "Z" STATION(B)	7500.00	SH/HR	100.0%	$ 45000.	85.0%	200.

LABOR

(DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	SYSTEM "Z" STATION(B)	5.000E-01		
MAINTENANCE	SYSTEM "Z" STATION(B)	5.000E-02		
FOREMAN	DL	5.000E-02		

SUPPLIES/EXPENSES

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	UNITS	BASE
ELECTRICITY	0.0	3.500E+01	KWH.	PER AVAILABLE INVESTMENT-HOUR OF SYSTEM "Z" STATION(B)
SULFURIC ACID	0.0	2.310E-01	GM.	PER INPUT UNIT. % UNITS= 100.0%
HYDROGEN PEROXIDE	0.0	2.100E-01	CM**3	PER INPUT UNIT. % UNITS= 100.0%
DE-IONIZED WATER	0.0	1.000E+06	CM**3	PER AVAILABLE INVESTMENT-HOUR OF SYSTEM "Z" STATION(B)

Figure 34. Process parameters - Z wafer cleaning.

	3-in. Cell ($/W)	5-in. Cell ($/W)
Materials & Expense	0.152	0.198
Labor Overhead Interest Depreciation	0.112	0.040
System Performance Degradation Cost		0.023
Final Comparison	0.264	0.261

Figure 35. "Best case" array module manufacturing cost summary, 3- and 5-in. cells.

for the reduction in panel performance. There is an increase of about 10% in the manufacturing cost of array modules based on 5-in. wafers compared with modules based on 3-in. wafers.

This result is due to the interconnect technology. In these panels, the cells are interconnected with one contact at the rim of the cell. In the event that numerous contact points are made within the cell area, the optimum metallization design will change and this result can be reversed. We have not analyzed the effect on panel design, panel life, and panel performance of these contacts to crossing the face of the cell. However, because of the enormous cost of the metallization step in the present configuration, such an analysis is surely appropriate.

E. FACTORY LEVEL OVERHEAD COSTS

In none of the manufacturing cost analyses presented above are factory overhead, distribution, advertising, or profit considered. For the process sequence, Ion Implantation (C) factory level overhead costs will now be estimated.

	3-in. Cell ($/W)	5-in. Cell ($/W)	Notes
Cleaning	0.003	0.002	Down linearly with radius
Ion Implantation	0.029	0.026	Labor down linearly, rest same
Diffusion	0.009	0.005	All linear decreases
Metallization	0.094	0.132	Labor down linearly, metal up by 4.6¢/W, machines same
AR Coating	0.011	0.007	Material same, rest linear decrease
Test	0.012	0.004	Squared reduction in all costs
Interconnect	0.016	0.010	Linear reduction in all costs
Panel Assembly & Packaging	0.089	0.089	Unchanged
	0.264	0.275	
Penalty due to System Performance Degradation		0.023	
TOTAL	0.264	0.298	

Figure 36. Detailed array module manufacturing cost estimate, 3- and 5-in. cells.

We have evaluated the factory level costs for two factories, one producing 50 MW/year and the other, 500 MW/year. A summary of these evaluations, which appear as Fig. 37, is given below.

	$/W	
	50 MW	500 MW
Support Personnel	0.035	0.010
Cassette Depreciation	0.002	0.002
Heating, Lighting, and Air-Conditioning	0.004	0.003
Insurance (building & all capital)	0.002	0.002
Local Taxes	0.005	0.004
Factory Depreciation	0.008	0.006
Factory Interest	0.014	0.012
Support Equipment Depreciation	0.002	0.000
Support Equipment Interest	0.001	0.000
	0.072	0.039

The manufacturing cost as a function of factory size is shown in Fig. 38.

	50 MW	500 MW
These costs are	0.264	0.253
Total	0.336	0.292

It will be noticed that this entire factory and the capital equipment are financed by debt. In order to remove considerations of debt ratio (% of assets financed by debt) from an estimate of profit, we will assume the following relationship:

$$\frac{\text{Net profit after taxes + after tax interest}}{\text{Assets less accumulated depreciation}} = 15\%$$

For this manufacturing facility, the before-tax profit in the first year of operations is then $0.05/W.

These estimates of the array module manufacturing cost, including factory level overhead, have been done in considerable detail. In every case the financial assumptions have been made using data from a wide variety of sources, and reasonable values reflecting the general industry have been assumed. This is RCA's estimate of the cost, not RCA's cost.

Assumptions:
(1) 3-in. wafers
(2) 15% cell efficiency, 0.717 W/wafer.
(3) Overall process yield: 82.2%
(4) Cafeteria run by outside firm using company facilities, but food company personnel. No cost to factory other than cost of facilities (depreciation, allocated interest, and taxes).
(5) 345 working days per year.
(6) Two 12-h shifts per day. 10% shift premium for night shift.

Work Schedule

Four groups of personnel; two for night shift and two for day shift. Schedule is 4 working days, 3 days off, 3 working days, 4 days off.
Other schedules could also be inplemented. Salaried people work a 5-day, 40-h week.

	50 MW-YR			500 MW/YR			
INVESTMENT	#	$	$/W	#	$/W	$	NOTES
PLANT:							
Process	54K ft^2	5400K	0.108	464K ft^2	46400K	0.093	@ $100/$ft^2$
Offices	10K ft^2	600K	0.012	15K ft^2	900K	0.002	
Cafeteria	5K ft^2	300K	0.006	25K ft^2	1500K	0.003	
Array Storage	0.5K ft^2	30K	0.001	4K ft^2	240K	0.000	@ $60/$ft^2$
Wafer Storage	10K ft^2	600K	0.012	100K ft^2	6000K	0.012	
Chemical Storage	10K ft^2	600K	0.012	100K ft^2	6000K	0.012	
Maint. Shops	5K ft^2	30K	0.001	50K ft^2	3000K	0.126	
TOTAL	95K ft^2	7560K	0.151	758K ft^2	64,040K	0.128	
LAND	160K ft^2	40K	0.001	1200K ft^2	300K	0.001	
Parking & Receiving	60K ft^2	60K	0.001	400K ft^2	400K	0.001	
Office Equipment		20K	0.000		50K	0.000	
Purchased Material Inspection & Q/C Equipment		500K	0.010		1000K	0.002	
Minicomputers for Payroll & MIS	2	250K	0.005	3	375K	0.001	
Cassettes	3500	350K	0.007	35000	3500K	0.007	1 week production
GRAND TOTAL	-	72,877K	0.458	-	133,705K	0.388	
PERSONNEL							
PLANT ADMINISTRATION							
Factory Mgr	1	50K	0.001	1	80K	0.000	
Ass't. Mgr	1	40K	0.001	3	180K	0.000	
Secretaries	1	10K	0.000	3	30K	0.000	
Receptionist	1	10K	0.000	1	10K	0.000	
Industrial Relations	1	18K	0.000	5	75K	0.000	
Secretaries	1	10K	0.000	3	30K	0.000	
Financial Services	2	60K	0.001	3	80K	0.000	
Secretaries	1	10K	0.000	2	20K	0.000	
Accounting Services	2	45K	0.001	3	65K	0.000	
Secretaries/Clerks	4	40K	0.001	8	80K	0.000	
Computer Service	2	40K	0.001	3	60K	0.000	
Computer Operators	1/shift	48K	0.001	2/shift	96K	0.000	
Purchasing	2	45K	0.001	3	65K	0.000	
Secretaries	1	10K	0.000	3	30K	0.000	
FACILITIES							
Guards	3/shift	144K	0.003	15/shift	720K	0.001	
Maintenance	3/shift	200K	0.004	15/shift	1000K	0.002	
Janitors	3/shift	100K	0.002	10/shift	80K	0.000	
Warehouse	1	25K	0.001	1	K	0.000	
Material Handlers	3/shift	144K	0.003	15/shift	720K	0.001	
Dispensary	1/shift	60K	0.001	2/shift	120K	0.000	
Industrial Engineering	10	250K	0.005	20	500K	0.001	
Quality Control & Purchased Material Inspection	5/shift	360K	0.007	15/shift	1080K	0.002	
Support People	107	1719K	0.034	314	5146K	0.010	
Direct Labor Process	106	1531K	0.031	912	13183K	0.027	
Indirect Labor Process	46	726K	0.014	408	6529K	0.013	
TOTAL PEOPLE	259	3976K	0.080	1634	24,858K	0.050	
EXPENSES							
Cassettes, Depr.		87.5K	0.002		875K	0.002	4-yr life
Heating & A/C		113K	0.002		1065K	0.002	
Lighting		75K	0.002		600K	0.001	3W/ft^2
Insurance		115K	0.002		1018K	0.002	0.5% of asset value
Local Taxes		230K	0.005		1942K	0.004	3% of plant and land
Factory Depr.		381K	0.008		3222K	0.006	20-yr life
Factory Interest		686K	0.014		5800K	0.012	9%
Support Equipment Depreciation		110K	0.002		204K	0.000	7-yr life
Support Equipment Interest		69K	0.001		128K	0.000	9%

Figure 37. Factory cost evaluations.

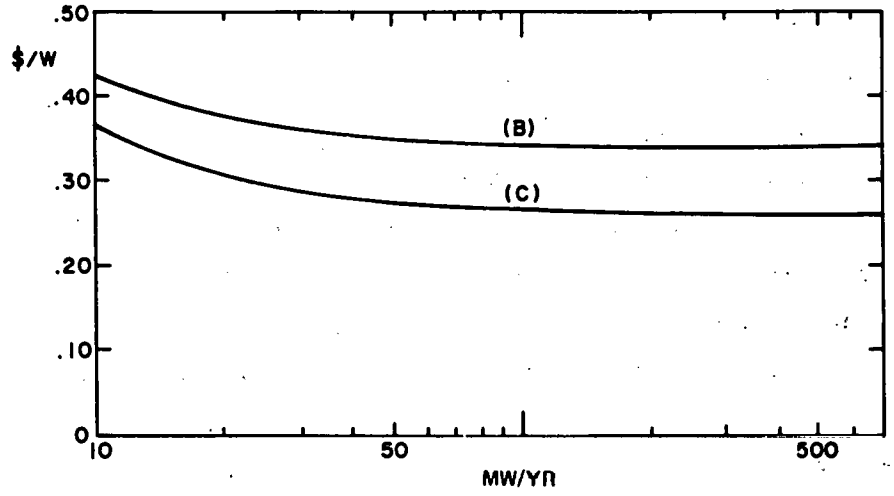

Figure 38. Manufacturing cost as a function of factory size.

For purposes of illustration it is interesting to assume a price for the silicon material which has not been included in any of this analysis. We assume silicon wafers are available for \$20 to \$40/M^2.

	500 MW/yr	
Silicon cost	\$20/M^2	\$40/M^2
Manufacturing cost + Factory level overhead	\$0.292/W	\$0.292/W
Yielded silicon cost	0.162/W	0.324/W
Profit	0.05/W	0.05/W
	0.504/W	0.666/W

We would like to assure the reader that the similarity between the goals of the LSSA program and these results is completely coincidental. It perhaps bespeaks the wisdom of the planners who established the goals in the first place. A selling price of \$0.50/W turns out to have been a very meaningful goal. As further studies are conducted, this may turn out to be a transitory coincidence as even lower costs are achieved!

F. SHEET ALTERNATIVES

Assessing the state of the technology for preparing single-crystal silicon sheet at this time leads to the same conclusions as we have found previously. Only wafers cut from Czochralski-pulled ingots will be available in the quantity and with the quality required by the near-term needs of the Automated Array Processing Task of the Low Cost Silicon Solar Array Project. There is, however, the ever-present question of cost. In the analysis above, the wafers are assumed to cost \$0.16 to \$0.32/W and the resulting solar cells are 15% efficient. The effect of lower efficiency impacts the total system cost. If we assume that the total system cost is \$1/W, a 30% reduction in cell efficiency increases the system cost by \$0.40/W. Even if the material which provided this performance were free, there is still a net increase in the system cost. At a system cost of \$0.50/W, such free material will result in a cost saving compared with the higher assumed price of wafers. It seems that 15% efficiency is a useful goal. Only Czochralski-pulled material and epitaxially grown layers of single-crystal silicon have been able to demonstrate cells of this efficiency.

Ribbon techniques have made steady progress during the year. Cells in the 10 to 12% efficiency range have been fabricated in ribbon material. However, before such material will be suitable for the Automated Array Assembly Task, several further advances will be required. The included particle count must be reduced or the location at which the particles appear must be controlled so that they can be removed from the active cell area. The residual strain must be reduced to the point where the mechanical stability of the ribbon will be sufficient to prevent a high yield loss due to cracking. Also, the strain should be low enough so that the ribbon does not shatter on being cut or scribed to be divided into sections of a given length.

It is the higher efficiency requirement which will be the most restrictive for any silicon sheet forming technique. Such a high efficiency will require that the silicon be prepared from a very high purity SiO_2 container or one with which it has little interaction. Any appeciable solubility of impurities is going to limit the cell efficiency either through degradation of lifetime or degradation of junction properties. Even the recently reported high efficiency cells prepared in polycrystalline silicon used a high purity grade of poly to achieve their outstanding result. Therefore, any technique in which the surface-to-volume ratio of the silicon in contact with a container is high

must be evaluated very carefully to assure that good cystallinity is not being acheived at a sacrifice to bulk electronic properties.

At this time, methods which are "containerless," i.e., ribbon-to-ribbon zone refining, regular float zone refining, or CVD, are either not fully developed or too expensive in their present form.

Thus, only wafers sliced from ingots are presently available as starting sheet for array processing. Further, it would appear that with new wafering methods and cheaper poly, a significant reduction in cost of this material can be achieved.

G. CONCLUSIONS - GENERAL TECHNOLOGY AND COST ANALYSIS

As a result of an extensive and detailed examination of the present day art in semiconductor manufacturing we conclude that:

(1) The goal of a selling price of \$0.50/W for a volume of 500 MW/year in 1986 is attainable assuming \$20/M^2 for silicon sheet.

(2) The most cost-effective panel design is a double-glass panel.

(3) The highest performance (for aging) panel design is a double-glass panel.

(4) Automated interconnection using gap welding, ultrasonic bonding, or spot reflow soldering are all cost effective.

(5) Application of antireflection coating using automated spray-on equipment is cost effective.

(6) Screen-printed Ag metallization is cost effective although a serious cost component.

(7) Several junction-formation technologies are cost effective. Ion implantation has a slight advantage.

Principal problem areas are:

(1) Maintenance of high cell efficiency at high yield. 15% with 82% yield was assumed in our analysis.

(2) Achievement of high mechanical yield with automated handling equipment.

(3) Development of low-cost screening inks which reliably provide low contact resistance, stable metallization.

(4) Demonstration of reliable automated interconnect technology.

(5) Demonstration of glass encapsulation techniques suitable for 20-year life.

(6) Minimizing factory level overhead. Marketing, sales, distribution, service, and warranty costs have not been considered.

SECTION III

ANALYSIS AND FACTORY DESIGN FOR 1982

A. PROCESS SELECTION

It was fairly obvious before we embarked on the cost analysis that the cost of preparing the silicon sheet was going to be a large fraction of the array costs. First, since it is apparent that the polycrystalline silicon cost (unyielded) is $0.01/W/mil thickness based on $25/kg, it is important to increase yield by reducing kerf loss. The second thing that is apparent is the large expense item of quartz liners at $190 each, and if each is used to grow a single 10-kg boule and then discarded, it adds $19 to the basic $25/kg cost of polycrystalline. It is also important therefore to increase the use of each liner by going to multiple-ingot-pulls.

The impact of these various approaches is shown in Table 5 for a 30-MW factory. A 0.010-in.-thick etched wafer at 12% efficiency is assumed. All dollar values ($/W) are yielded to the processes that follow.

Note that the significant savings of the multiple pull vs the single pull is in the "expense" item. This reflects the more efficient use of quartz liners. Going from an inside diameter with a 0.010-in. kerf and a 0.003-in. etch to a wire saw with a 0.008-in. kerf only requiring a 0.001-in. etch shows its most significant saving in material cost. Reducing the kerf further, however, increases the cost rather than decreasing it because the necessary saw is much slower and the wires do not last as long. Further, more machines are required, and, as a result, there is more labor cost. Thus savings in the cost of the yielded boule are more than offset by slicing costs.

The desired process is quite apparent based on the studies discussed above. It is multiple pull, 0.008-in. wire sawing, $POCl_3$ diffusion, and double-glass panel assembly. The cost details of these processes are outlined in Table 6. Process parameters are given in Figs. 39 through 53.

B. PROCESSING SEQUENCE FOR CELL FABRICATION

A matrix of processing sequences and factory production levels has been cost-analyzed as follows. All processes were constant with respect to screen-printed silver metallization, spray-on AR coating, and double-glass panel

TABLE 5. COMPARISON OF COST ITEMS FOR SINGLE VS MULTIPLE PULL AND I.D. VS WIRE SAWING OF INGOTS

	Single Pull I.D. Saw, 0.010-in. Kerf		Multiple Pull, 0.003-in. Etch		Multiple Pull and Wire Saw 0.008-in. Kerf		0.001-in. Etch 0.004-in. Kerf	
	Pull	Slice	Pull	Slice	Pull	Slice	Pull	Slice
	($/W)		($/W)		($/W)		($/W)	
Material	0.522	0	0.503	0	0.390	0	0.308	0
Expense	0.457	0.105	0.208	0.105	0.161	0.231	0.127	0.366
Labor and Overhead	0.268	0.253	0.237	0.253	0.185	0.261	0.146	0.559
Interest and Depreciation	0.071	0.10	0.066	0.10	0.053	0.058	0.041	0.186
Subtotal	1.317	0.458	1.012	0.458	0.789	0.550	0.621	1.111
TOTAL	1.775		1.467		1.339		1.732	

TABLE 6. COST DETAILS FOR COMPLETE PROCESS
(Assume 12% efficiency, 3.4-in.-diam, 0.010-in.-thick wafer)

			($/W)					
Step	Yield (%)	Process	Material	Expense	Labor and Overhead	Interest and Depreciation	Total	Investment
1	86	Czochralski Multiple Pull	0.390	0.161	0.185	0.053	0.789	0.253
2	98	Wire Saw, 0.008-in. Kerf	0	0.231	0.261	0.058	0.550	0.248
3	99	Etch & Clean	0	0.047	0.002	0	0.050	0.003
4	95	Spin-On Source	0.011	0.025	0.073	0.016	0.127	0.072
5	99	$POCl_3$ Diffusion	0	0.012	0.005	0.006	0.023	0.019
6	95	Edge Polish	0	0.004	0.003	0.001	0.008	0.005
7	99	Glass Removal	0	0.001	0.003	0.001	0.006	0.005
8	99	Inspection	0	0.000	0.006	0.007	0.013	0.03
9	98	Ag Front Metal.	0.038	0.005	0.009	0.007	0.058	0.028
10	98	Ag Back Metal.	0.037	0.011	0.021	0.013	0.083	0.055
11	99	AR Spray Coat	0.002	0	0.005	0.003	0.010	0.012
12	90	Test	0	0	0.007	0.010	0.017	0.041
13	98	Reflow Solder Interconnect	0.002	0	0.017	0.007	0.025	0.028
14	99.5	Glass-PVB Panel	0.209	0	0.024	0.005	0.239	0.023
15	100	Packaging	0.01	0	0.002	0	0.013	0.001
		Totals	0.7	0.498	0.625	0.187	2.011	0.824

```
ESTIMATE DATE:07/28/77  BY:DAVE RICHMAN, X3207, RCA LABS, E-321A                    CLASS:CRYSTAL GROWTH
CATEGORY:PROCESS DEFINITION      TECHNOLOGY LEVEL:EXISTING     MATERIAL FORM:3.40" WAFER
INPUT UNIT:KG.          OUTPUT UNIT:KG.          TRANSPORT IN:BOX          TRANSPORT OUT:BOX
PROCESS YIELD: 83.0%   YIELD GROWTH PROFILE: 0
INPUT UNIT SALVAGE FACTOR:  0.0   FACTOR GP#: 0     SALVAGE OPTION:FRACTION OF INPUT UNIT VALUE

      INPUT UNITS:        0.        0.        0.
FLOOR SPACE,FT**2:        0.        0.        0.

DESCRIPTION:CZOCHRALSKI CRYSTAL GROWTH OF 34" CRYSTAL, 3.40" DIAMETER.

                                                                  ASSUMPTIONS:
1. 3.40" DIAMETER WAFER,(100) ORIENTATION,P-TYPE,:1-5 OHM-CM.
2. POLYSILICON AT $.025/GRAM.
3. POT SIZE CAN BE INCREASED TO ACCOMODATE A 15 KG. CHARGE.
4. 3.45" DIAMETER INGOT GROWN, THEN GROUND TO 3.40".
5. ARGON FARM COST NOT INCLUDED.
6. POLYSILICON INVENTORY OF 1 MONTH PER PULLER REQUIRED:
    =1.000 KG/HR X 0.85 AVAIL. X 24 X 30 HRS/MONTH
    =600 KG INVENTORY PER PULLER AT $25/KG
    =$15,000 PER PULLER.
7. PROCESS YIELD DEFINED AS MATERIAL YIELD FOR PROCESS.
   GROWTH TIMING ESTIMATE:
    MELT DOWN              1.0 HRS.
    SEED SET               1.0 HRS.
    PULL TIME @ 4"/HR      8.5 HRS.
    COOL DOWN              1.0 HRS.
    TURN AROUND            1.0 HRS.
                          ---------
    TOTAL                 12.5 HRS.
   MATERIAL USED(BASED UPON 3.45" DIAMETER BEFORE GRINDING):
   LET F=1/4 * PI * (2.54 CM/")**3 * (2.33G/CM**3)
   30" CENTER PART: (3.45")**2 * (30") * F =          10708 G.
   4" TAPER: 0.8 * (4") * (3.45)**2 * F =              1142 G.
   POT LOSS (ESTIMATE)                                  625 G.
                                                    ----------
      TOTAL MATERIAL USED PER INGOT                   12475 G.
   GOOD MATERIAL AFTER GRINDING TO 3.40" DIAMETER & REMOVING TAPERS:
    30" CENTER SECTION: (3.40")**2 * 30" * F = 10400 G.
    MATERIAL YIELD =10400/12475 = 0.83
    AVG. GROWTH RATE = 12.475 KG./12.5 HRS. = 1.000 KG/HR.
8. QUARTZ LINER:1 LINER NEEDED EVERY 12.5 HRS.(=8.0E-02 UNITS/HR.)

                                                                  PROCEDURE
1. PRE-WEIGHED CHARGE OF SILICON AND DOPANT PLACED IN QUARTZ CRUCIBLE.
2. SILICON CHARGE & DOPANT HEATED TO PROPER GROWTH TEMPERATURE.
3. ROD WITH SEED PLACED IN CONTACT WITH MELT.
4. ROD ROTATED UNTIL MELT COMES TO EQUILIBRIUM.
5. ROTATING ROD SLOWLY WITHDRAWN, CAUSING SILICON TO FREEZE ONTO SEED.
6. INGOT IS REMOVED FROM CRYSTAL GROWER WHEN GROWTH STOPS.
7. INGOT ENDS ARE CUT OFF YIELDING A 30" CRYSTAL.
8. INGOT IS GROUND TO PROPER DIAMETER.
```

Figure 39. Process parameters - Czochralski multiple pull.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT	UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA, FT**2
SILTEC CRYSTAL PULLER-860	1.00	KG/HR	100.0%	$ 80000.	85.0%	450.
CRYSTAL PULLER SPARE PARTS	1.00	KG/HR	100.0%	$ 5750.	85.0%	0.
ARGON GAS INSTALLATION	5.00	KG/HR	100.0%	$ 15000.	85.0%	0.
4-POINT PROBE	10.00	KG/HR	100.0%	$ 5000.	85.0%	0.
CENTER GRINDER	10.00	KG/HR	100.0%	$ 18000.	85.0%	0.
CENTERLESS GRINDER	10.00	KG/HR	100.0%	$ 24000.	85.0%	0.
CUTOFF SAW	4.00	KG/HR	100.0%	$ 2400.	85.0%	0.
WATER RE-CIRCULATOR	6.00	KG/HR	100.0%	$ 12000.	85.0%	0.
LIFETIME TEST SET	10.00	KG/HR	100.0%	$ 5000.	85.0%	0.
ANNEALING FURNACE	4.00	KG/HR	100.0%	$ 4500.	85.0%	0.
REICHERT MICROSCOPE	10.00	KG/HR	100.0%	$ 9000.	85.0%	0.
NIKON COMPARATOR	10.00	KG/HR	100.0%	$ 6500.	85.0%	0.
MISCELLANEOUS CP	10.00	KG/HR	100.0%	$ 18000.	85.0%	0.
POLYSILICON INVENTORY	1.00	KG/HR	100.0%	$ 15000.	85.0%	0.

LABOR

(DL=DIRECT LABOR PERSONS; TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	SILTEC CRYSTAL PULLER-860	4.000E-01		
MAINTENANCE	SILTEC CRYSTAL PULLER-860	1.500E-01		
ENGR. SUPPORT	SILTEC CRYSTAL PULLER-860	6.000E-02		
TECHNICIAN	SILTEC CRYSTAL PULLER-860	1.800E-01		
QUALITY CONTROL	SILTEC CRYSTAL PULLER-860	6.000E-02		
MACH. ATTENDANT	SILTEC CRYSTAL PULLER-860	2.500E-01		
CLERICAL	SILTEC CRYSTAL PULLER-860	8.300E-02		
FOREMAN	CL	1.000E-01		

SUPPLIES/EXPENSES

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	UNITS	BASE
POLYSILICON	0.0	1.000E+03	GM.	PER INPUT UNIT. % UNITS= 100.0%
DOPE CELL	0.0	5.880E-02	UNITS	PER AVAILABLE INVESTMENT-HOUR OF SILTEC CRYSTAL PULLER-860
SEED	0.0	3.270E-03	UNITS	PER AVAILABLE INVESTMENT-HOUR OF SILTEC CRYSTAL PULLER-860
ELECTRICITY	0.0	6.000E+01	KWH.	PER AVAILABLE INVESTMENT-HOUR OF SILTEC CRYSTAL PULLER-860
ELECTRICITY	0.0	6.000E+00	KWH.	PER AVAILABLE INVESTMENT-HOUR OF CENTER GRINDER
ELECTRICITY	0.0	6.000E+00	KWH.	PER AVAILABLE INVESTMENT-HOUR OF CENTERLESS GRINDER
ELECTRICITY	0.0	3.000E+00	KWH.	PER AVAILABLE INVESTMENT-HOUR OF CUTOFF SAW
ELECTRICITY	0.0	4.000E+00	KWH.	PER AVAILABLE INVESTMENT-HOUR OF WATER RE-CIRCULATOR
ELECTRICITY	0.0	1.000E+00	KWH.	PER AVAILABLE INVESTMENT-HOUR OF LIFETIME TEST SET
ELECTRICITY	0.0	1.500E+01	KWH.	PER AVAILABLE INVESTMENT-HOUR OF ANNEALING FURNACE
ELECTRICITY	0.0	1.000E+00	KWH.	PER AVAILABLE INVESTMENT-HOUR OF 4-POINT PROBE
ELECTRICITY	0.0	5.000E+00	KWH.	PER AVAILABLE INVESTMENT-HOUR OF MISCELLANEOUS CP
QUARTZ LINER	0.0	8.000E-02	UNITS	PER AVAILABLE INVESTMENT-HOUR OF SILTEC CRYSTAL PULLER-860
GRAPHITE CRUCIBLE HOLDER	0.0	4.900E-03	UNITS	PER AVAILABLE INVESTMENT-HOUR OF SILTEC CRYSTAL PULLER-860
ARGON	0.0	2.270E+06	CM**3	PER AVAILABLE INVESTMENT-HOUR OF SILTEC CRYSTAL PULLER-860
SHOP SUPPLIES	0.0	6.500E-01	$	PER AVAILABLE INVESTMENT-HOUR OF SILTEC CRYSTAL PULLER-860
MISCELLANEOUS SUPPLIES	0.0	6.500E-01	$	PER AVAILABLE INVESTMENT-HOUR OF SILTEC CRYSTAL PULLER-860
MISCELLANEOUS CRYSTAL GROWT-	0.0	1.390E+00	$	PER AVAILABLE INVESTMENT-HOUR OF SILTEC CRYSTAL PULLER-860

Figure 39. Continued.

```
ESTIMATE DATE:07/28/77  BY:DAVE RICHMAN, X3207, RCA LABS, E-321A                    CLASS:CRYSTAL GROWTH
CATEGORY:PROCESS DEFINITION       TECHNOLOGY LEVEL:NEAR FUTURE  MATERIAL FORM:3.40" WAFER
INPUT UNIT:KG.          OUTPUT UNIT:KG.          TRANSPORT IN:BOX          TRANSPORT OUT:BOX
PROCESS YIELD: 86.0%   YIELD GROWTH PROFILE: C
INPUT UNIT SALVAGE FACTOR:  0.0   FACTOR GP#: 0     SALVAGE OPTION:FRACTION OF INPUT UNIT VALUE

      INPUT UNITS:        0.        C.        0.
FLOOR SPACE,FT**2:        0.        0.        0.

DESCRIPTION:CZOCHRALSKI CRYSTAL GROWTH: 34" CRYSTAL, 3.40" DIAMETER, 4 PULLS.

                                                                  ASSUMPTIONS:
1. 3.40" DIAMETER WAFER,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. QUARTZ LINER: 1 LINER NEEDED EVERY 44 HRS. (=2.27E-02 UNITS/HR.)
3. POLYSILICON AT $.025/GRAM.
4. POT SIZE CAN BE INCREASED TO ACCOMODATE A 15 KG. CHARGE.
   POT CAN BE REFILLED WITHOUT COOLING DOWN.
   4 34" PULLS FROM POT BEFORE COOLING DOWN.
5. 3.45" DIAMETER INGOT GROWN, THEN GROUND TO 3.40".
6. ARGON FARM COST NOT INCLUDED.
7. POLYSILICON INVENTORY OF 1 MONTH PER PULLER REQUIRED:
   =1.090 KG/HR X 0.85 AVAIL. X 24 X 30 HRS/MONTH
   =670 KG INVENTORY PER PULLER AT $25/KG
   =$16,750 PER PULLER.
8. PROCESS YIELD DEFINED AS MATERIAL YIELD FOR PROCESS.
   GROWTH TIMING ESTIMATE:
    MELT DOWN              1.0 HRS.
    SEED SET               1.0 HRS.
    PULL TIME @ 4"/HR      8.5 HRS.
    TURN AROUND            1.0 HRS.
    SEED SET               1.0 HRS.
    PULL TIME @ 4"/HR      8.5 HRS.
    TURN AROUND            1.0 HRS.
    SEED SET               1.0 HRS.
    PULL TIME @ 4"/HR      8.5 HRS.
    TURN AROUND            1.0 HRS.
    SEED SET               1.0 HRS.
    PULL TIME @ 4"/HR      8.5 HRS.
    COOL DOWN              1.0 HRS.
    TURN AROUND            1.0 HRS.
                          -------
    TOTAL                 44.0 HRS.
   MATERIAL USED(BASED UPON 3.45" DIAMETER BEFORE GRINDING):
   LET F=1/4 * PI * (2.54 CM/")**3 * (2.33G/CM**3)
   30" CENTER PART: (3.45")**2 * (30") * F =10708 G.; X 4=  42832.
   4" TAPER: 0.8 * (4") * (3.45)**2 * F =    1142 G.; X 4=   4568.
   POT LOSS (ESTIMATE)                        625 G.; X 1=    625.
                                                            -------
      TOTAL MATERIAL USED PER 4 INGOTS                      48025. G.
   GOOD MATERIAL AFTER GRINDING TO 3.40" DIAMETER & REMOVING TAPERS:
    30" CENTER SECTIONS: 4*(3.40")**2 * 30" * F = 41600 G.
    MATERIAL YIELD = 41600/48025 = 0.86
    AVG. GROWTH RATE = 48.025 KG./44.0 HRS. = 1.090 KG/HR.
```

Figure 39. Continued.

PROCEDURE

1. PRE-WEIGHED CHARGE OF SILICON AND DOPANT PLACED IN QUARTZ CRUCIBLE.
2. SILICON CHARGE & DOPANT HEATED TO PROPER GROWTH TEMPERATURE.
3. ROD WITH SEED PLACED IN CONTACT WITH MELT.
4. ROD ROTATED UNTIL MELT COMES TO EQUILIBRIUM.
5. ROTATING ROD SLOWLY WITHDRAWN, CAUSING SILICON TO FREEZE ONTO SEED.
6. INGOT IS REMOVED FROM CRYSTAL GROWER WHEN GROWTH STOPS.
7. INGOT ENDS ARE CUT OFF YIELDING A 3CM CRYSTAL.
8. INGOT IS GROUND TO PROPER DIAMETER.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT	UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
SILTEC CRYSTAL PULLER-860	1.09	KG/HR	100.0%	$ 80000.	85.0%	450.
POT REFILLER	1.09	KG/HR	100.0%	$ 5000.	85.0%	0.
CRYSTAL PULLER SPARE PARTS	1.09	KG/HR	100.0%	$ 5750.	85.0%	0.
ARGON GAS INSTALLATION	5.45	KG/HR	100.0%	$ 15000.	85.0%	0.
4-POINT PROBE	10.90	KG/HR	100.0%	$ 5000.	85.0%	0.
CENTER GRINDER	10.90	KG/HR	100.0%	$ 18000.	85.0%	0.
CENTERLESS GRINDER	10.90	KG/HR	100.0%	$ 24000.	85.0%	0.
CUTOFF SAW	4.36	KG/HR	100.0%	$ 2400.	85.0%	0.
WATER RE-CIRCULATOR	6.54	KG/HR	100.0%	$ 12000.	85.0%	0.
LIFETIME TEST SET	10.90	KG/HR	100.0%	$ 5000.	85.0%	0.
ANNEALING FURNACE	4.36	KG/HR	100.0%	$ 4500.	85.0%	0.
REICHERT MICROSCOPE	10.90	KG/HR	100.0%	$ 5000.	85.0%	0.
NIKON COMPARATOR	10.90	KG/HR	100.0%	$ 6500.	85.0%	0.
MISCELLANEOUS CP	10.90	KG/HR	100.0%	$ 18000.	85.0%	0.
POLYSILICON INVENTORY(B)	1.09	KG/HR	100.0%	$ 16750.	85.0%	0.

LABOR

(DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	SILTEC CRYSTAL PULLER-860	4.000E-01		
MAINTENANCE	SILTEC CRYSTAL PULLER-860	1.500E-01		
ENGR. SUPPORT	SILTEC CRYSTAL PULLER-860	6.000E-02		
TECHNICIAN	SILTEC CRYSTAL PULLER-860	1.800E-01		
QUALITY CONTROL	SILTEC CRYSTAL PULLER-860	6.000E-02		
MACH. ATTENDANT	SILTEC CRYSTAL PULLER-860	2.500E-01		
CLERICAL	SILTEC CRYSTAL PULLER-860	8.300E-02		
FOREMAN	DL	1.000E-01		

Figure 39. Continued.

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	UNITS	BASE
		SUPPLIES/EXPENSES		
POLYSILICON	C.0	1.CCCE+03	GM.	PER INPUT UNIT. % UNITS= 100.0%
CCPE CELL	C.0	5.88CE-02	UNITS	PER AVAILABLE INVESTMENT-HOUR CF SILTEC CRYSTAL PULLER-860
SEED	C.0	3.270E-03	UNITS	PER AVAILABLE INVESTMENT-HOUR OF SILTEC CRYSTAL PULLER-860
ELECTRICITY	C.0	6.CCCE+01	KWH.	PER AVAILABLE INVESTMENT-HOUR OF SILTEC CRYSTAL PULLER-86C
ELECTRICITY	C.0	6.000E+00	KWH.	PER AVAILABLE INVESTMENT-HOUR CF CENTER GRINDER
ELECTRICITY	C.0	6.000E+00	KWH.	PER AVAILABLE INVESTMENT-HOUR OF CENTERLESS GRINDER
ELECTRICITY	C.0	3.00CE+0C	KWH.	PER AVAILABLE INVESTMENT-HCUR CF CUTOFF SAW
ELECTRICITY	C.0	4.000E+00	KWH.	PER AVAILABLE INVESTMENT-HOUR CF WATER RE-CIRCULATOR
ELECTRICITY	C.0	1.0CCE+0C	KWH.	PER AVAILABLE INVESTMENT-HOUR OF LIFETIME TEST SET
ELECTRICITY	C.0	1.5CCE+01	KWH.	PER AVAILABLE INVESTMENT-HCUR CF ANNEALING FURNACE
ELECTRICITY	C.0	1.000E+00	KWH.	PER AVAILABLE INVESTMENT-HOUR OF 4-POINT PROBE
ELECTRICITY	C.0	5.C0CE+00	KWH.	PER AVAILABLE INVESTMENT-HOUR OF MISCELLANEOUS CP
QUARTZ LINER	C.0	2.270E-02	UNITS	PER AVAILABLE INVESTMENT-HOUR CF SILTEC CRYSTAL PULLER-860
GRAPHITE CRUCIBLE HCLDER	C.0	4.900E-03	UNITS	PER AVAILABLE INVESTMENT-HOUR OF SILTEC CRYSTAL PULLER-86C
ARGCN	C.0	2.27CE+0C	C**3	PER AVAILABLE INVESTMENT-HCUR CF SILTEC CRYSTAL PULLER-86C
SHOP SUPPLIES	C.0	6.500E-01	$	PER AVAILABLE INVESTMENT-HOUR CF SILTEC CRYSTAL PULLER-860
MISCELLANEOUS SUPPLIES	C.0	6.50CE-01	$	PER AVAILABLE INVESTMENT-HOUR CF SILTEC CRYSTAL PULLER-86C
MISCELLANEOUS CRYSTAL GRCWTH	C.0	1.39CE+0C	$	PER AVAILABLE INVESTMENT-HOUR CF SILTEC CRYSTAL PULLER-860

Figure 39. Continued.

ESTIMATE DATE:09/20/77 BY:DAVE RICHMAN, X3207, RCA LABS, E-321A CLASS:WAFER SAWING
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:NEAR FUTURE MATERIAL FORM:3.40" WAFER
INPUT UNIT:KG. OUTPUT UNIT:SHEETS TRANSPORT IN:BOX TRANSPORT OUT:500 SHEET CASSETTE
PROCESS YIELD: 98.0% YIELD GROWTH PROFILE: C
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:FRACTION OF INPUT UNIT VALUE
CELL THICKNESS:10.0 MILS. CELL ETCH LOSS: 1.0 MILS. CELL KERF LOSS: 8.0 MILS.

INPUT UNITS:	C.	C.	0.
FLOOR SPACE,FT**2:	0.	0.	0.

DESCRIPTION:SLICING OF 15" CRYSTAL INTO 3.40" DIAMETER WAFERS

ASSUMPTIONS:

1. 3.40" DIAMETER WAFER,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. 15" LONG CRYSTAL, 19 MILS PER SLICE.
   (30" CRYSTAL IS ASSUMED TO BE SAWED INTO TWO 15" CRYSTALS.)
   19 MILS= 10 MILS FINAL WAFER + 1 MILS ETCH LOSS + 08 MILS KERF.
3. WAFERS PLACED INTO CASSETTE AUTOMATICALLY AFTER SAWING.
4. OTHER INVESTMENTS:
   GRAPHITE STICK CRYSTAL MOUNTING FEATURE:$360, 7 YR. LIFE.
   CRYSTAL MOUNTING BLOCK:$85, 1 YR. LIFE.
   GRAPHITE PLUG:$2, 1 YR. LIFE.
   ALUMINUM BLOCK:$8, 7 YR. LIFE.
5. EXPENSE ITEMS:
   CRYSTAL MOUNTING COST AT $.08/IN. FOR STYCAST=$2.00E-3/WAFER: ($.08 X 30")/(40 WAFERS/IN. X 30"/CRYSTAL)
   BLADE COST=$10.51/M**2 X (1M/100CM)**2 * (58.58CM**2/WAFER) * 23.6 WAFERS/HR =$1.46/HR.
   SLURRY COST:$7.48/M**2 X (1M/100CM)**2 X (58.58CM**2/WAFER) * 23.6 WAFERS/HR = $1.04/HR.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT	UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
VARIAN MULTIBLADE SAW	23.60	SH/HR	100.0%	$ 20000.	85.0%	60.
DISHING GAUGE	165.20	SH/HR	100.0%	$ 150.	85.0%	0.
GRAPHITE STICK CRYSTAL MOUNT	23.60	SH/HR	100.0%	$ 360.	85.0%	0.
CRYSTAL MOUNTING BLOCK	23.60	SH/HR	100.0%	$ 85.	85.0%	0.
GRAPHITE PLUG	23.60	SH/HR	100.0%	$ 2.	85.0%	0.
ALUMINUM BLOCK	23.60	SH/HR	100.0%	$ 8.	85.0%	0.

LABOR
(DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	VARIAN MULTIBLADE SAW	1.000E-01		
MAINTENANCE	VARIAN MULTIBLADE SAW	1.500E-01		
MACH. ATTENDANT	VARIAN MULTIBLADE SAW	6.300E-02		
FOREMAN	DL	1.000E-01		

SUPPLIES/EXPENSES

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	UNITS	BASE
SAW BLADES-VARIAB	0.0	1.460E+00	$	PER AVAILABLE INVESTMENT-HOUR OF VARIAN MULTIBLADE SAW
SLURRY	0.0	1.040E+00	$	PER AVAILABLE INVESTMENT-HOUR OF VARIAN MULTIBLADE SAW
MOUNTING MATERIAL	0.0	6.560E-02	$	PER AVAILABLE INVESTMENT-HOUR OF VARIAN MULTIBLADE SAW
ELECTRICITY	0.0	4.400E+00	KWH.	PER AVAILABLE INVESTMENT-HOUR OF VARIAN MULTIBLADE SAW
WATER-COOLING	0.0	3.800E+04	CM**3	PER AVAILABLE INVESTMENT-HOUR OF VARIAN MULTIBLADE SAW
SLUDGE REMOVAL	0.0	7.000E-03	$	PER INPUT UNIT. % UNITS= 100.0%

Figure 40. Process parameters - wire sawing.

ESTIMATE DATE:09/20/77 BY:DAVE RICHMAN, X3207, RCA LABS, E-321A CLASS:WAFER SAWING
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:NEAR FUTURE MATERIAL FORM:3.40" WAFER
INPUT UNIT:KG. CUTPUT UNIT:SHEETS TRANSPORT IN:BOX TRANSPORT OUT:500 SHEET CASSETTE
PROCESS YIELD: 98.0% YIELD GROWTH PROFILE: 0
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:FRACTION OF INPUT UNIT VALUE
CELL THICKNESS:10.0 MILS. CELL ETCH LOSS: 1.0 MILS. CELL KERF LOSS: 4.0 MILS.

INPUT UNITS:	0.	0.	0.
FLOOR SPACE,FT**2:	C.	C.	C.

DESCRIPTION:SLICING OF 15" CRYSTAL INTO 3.40" DIAMETER WAFERS

ASSUMPTIONS:

1. 3.40" DIAMETER WAFER,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. 15" LONG CRYSTAL, 15 MILS PER SLICE.
   (30" CRYSTAL IS ASSUMED TO BE SAWED INTO TWO 15" CRYSTALS.)
   15 MILS= 10 MILS FINAL WAFER + 1 MILS ETCH LOSS + 04 MILS KERF.
3. WAFERS PLACED INTO CASSETTE AUTOMATICALLY AFTER SAWING.
4. OTHER INVESTMENTS:
   GRAPHITE STICK CRYSTAL MOUNTING FEATURE:$36C, 7 YR. LIFE.
   CRYSTAL MOUNTING BLOCK:$85, 1 YR. LIFE.
   GRAPHITE PLUG:$2, 1 YR. LIFE.
   ALUMINUM BLOCK:$8, 7 YR. LIFE.
5. EXPENSE ITEMS:
   CRYSTAL MOUNTING COST AT $.08/IN. FOR STYCAST=$2.00E-3/WAFER: ($.08 X 30")/(40 WAFERS/IN. X 30"/CRYSTAL)
   BLADE COST: $260/2000 WAFERS = $.13/WAFER.
   $.13/WAFER X 11 WAFERS/HR = $1.43/HR.
   SLURRY COST:$7.48/M**2 X (1M/100CM)**2 X (58.58CM**2/WAFER) X 11.0 WAFERS/HR = $0.48/HR.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT	UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
YASUNAGI WIRE SAW	11.00	SH/HR	100.0%	$ 30000.	85.0%	60.
DISHING GAUGE	77.00	SH/HR	100.0%	$ 150.	85.0%	0.
GRAPHITE STICK CRYSTAL MOUNT	11.00	SH/HR	100.0%	$ 360.	85.0%	0.
CRYSTAL MOUNTING BLOCK	11.00	SH/HR	100.0%	$ 85.	85.0%	0.
GRAPHITE PLUG	11.00	SH/HR	100.0%	$ 2.	85.0%	0.
ALUMINUM BLOCK	11.00	SH/HR	100.0%	$ 8.	85.0%	0.

LABOR
(DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	YASUNAGI WIRE SAW	1.00CE-01		
MAINTENANCE	YASUNAGI WIRE SAW	1.50OE-01		
MACH. ATTENDANT	YASUNAGI WIRE SAW	6.300E-02		
FOREMAN	DL	1.00OE-01		

SUPPLIES/EXPENSES

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	UNITS	BASE
SAW BLADES-YASUNAGI	0.0	1.430E+0C	$	PER AVAILABLE INVESTMENT-HOUR OF YASUNAGI WIRE SAW
SLURRY	0.0	4.800E-01	$	PER AVAILABLE INVESTMENT-HOUR OF YASUNAGI WIRE SAW
MOUNTING MATERIAL	0.0	6.960E-02	$	PER AVAILABLE INVESTMENT-HOUR OF YASUNAGI WIRE SAW
ELECTRICITY	0.0	6.000E-01	KWH.	PER AVAILABLE INVESTMENT-HOUR OF YASUNAGI WIRE SAW
WATER-COOLING	0.0	3.800E+04	CM**3	PER AVAILABLE INVESTMENT-HOUR OF YASUNAGI WIRE SAW
SLUDGE REMOVAL	0.0	7.000E-03	$	PER INPUT UNIT. % UNITS= 100.0%

Figure 40. Continued.

ESTIMATE DATE:08/02/77 BY:DAVE RICHMAN, 73207, RCA LABS, E-321A CLASS:ETCH
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:NEAR FUTURE MATERIAL FORM:3.40" WAFER
INPUT UNIT:SHEETS OUTPUT UNIT:SHEETS TRANSPORT IN:500 SHEET CASSETTE TRANSPORT OUT:500 SHEET CASSETTE
PROCESS YIELD: 99.0% YIELD GROWTH PROFILE: 0
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:FRACTION OF INPUT UNIT VALUE

INPUT UNITS:	0.	C.	C.
FLOOR SPACE,FT**2:	0.	0.	0.

DESCRIPTION:WAFERS ARE ETCHED 1.5 MILS PER SIDE TO REMOVE SAW DAMAGE.

ASSUMPTIONS:

1. 3.40" DIAMETER WAFER,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. 500 WAFERS/TEFLON CASSETTE
3. 1 TEFLON BOAT PER TANK; 2 TANKS PER SYSTEM.
4. 7.5 CYCLES/HR X 2 BOATS/CYCLE X 500 WAFERS/BOAT=7500 WAFERS/HR.
   (8 MIN. RINSE CYCLE IS LIMITING FACTOR.)
5. 1 OPERATOR REQUIRED FOR 2 SYSTEMS.
6. NOTE: SYSTEM COST ESTIMATED TO BE $30,000. $15,000 FOR BACKUP.
   TOTAL SYSTEM COST=$45,000 WITH BACKUP.
7. ACID MIXTURE COST: $5/GAL. X 1GAL./50 WAFERS = $.10/WAFER
   RECYCLE OF ACID SAVES 30%. THEREFORE, $.07/WAFER.

PROCEDURE

1. TEFLON CASSETTE MANUALLY INSERTED IN TANK (1 MIN.)
2. 3 MINUTES IN HOT HF/ACETIC/NITRIC ACID MIXTURE, WITH AGITATION.
3. AUTOMATIC TRANSFER TO 1ST CASCADE RINSE, 8 MINUTE RINSE.
4. AUTOMATIC TRANSFER TO 2ND & 3RD RINSES, EACH ABOUT 3 MINUTES.
5. AUTOMATIC TRANSFER TO HOT AIR TUNNEL. DRY FOR 8 MINUTES.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
WAFER ETCHING STATION(B)	7500.00 SH/HR	100.0%	$ 45000.	85.0%	200.

LABOR

(DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	WAFER ETCHING STATION(B)	5.00E-01		
MAINTENANCE	WAFER ETCHING STATION(B)	5.00E-02		
FOREMAN	DL	5.00E-02		

SUPPLIES/EXPENSES

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	UNITS	BASE
ELECTRICITY	0.0	3.50E+01	KWH.	PER AVAILABLE INVESTMENT-HOUR OF WAFER ETCHING STATION(B)
HF/ACETIC/NITRIC MIXTURE	0.0	7.00E-02	$	PER INPUT UNIT. % UNITS= 100.0%
DE-IONIZED WATER	0.0	1.23E+06	CM**3	PER AVAILABLE INVESTMENT-HOUR OF WAFER ETCHING STATION(B)

Figure 41. Process parameters - etch and clean.

ESTIMATE DATE:08/01/77 BY:FRED MAYER, X6334, SOMERVILLE, ZONE 8 CLASS:DIFFUSION
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:NEAR FUTURE MATERIAL FORM:3.40" WAFER
INPUT UNIT:SHEETS OUTPUT UNIT:SHEETS TRANSPORT IN:500 SHEET CASSETTE TRANSPORT OUT:SILICON BOAT
PROCESS YIELD: 95.0% YIELD GROWTH PROFILE: 0
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:FRACTION OF INPUT UNIT VALUE

INPUT UNITS:	0.	0.	0.
FLOOR SPACE,FT**2:	0.	0.	0.

DESCRIPTION:LIQUID DIFFUSION SOURCE & SILICA SPUN ONTO BACK SIDE OF WAFER

ASSUMPTIONS:

1. 3.40" DIAMETER WAFER,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. 500 WAFERS/CASSETTE
3. EACH MACHINE HAS 3 TRACKS; EACH TRACK HANDLES 240 WAFER/HR.
4. ONE OPERATOR PER 3 SPINNERS
5. NOTE:UNIFORMITY OF DIFFUSION FROM SPIN-ON NEEDS STUDY.
6. NOTE: IN-HOUSE SOURCE NEEDS TO BE DEVELOPED.
7. SPIN-ON SOURCE AT $6.00/LITER. 0.8CM**3 NEEDED FOR BACK SIDE.
   SILICA AT $6.00/LITER. 1.6CM**3 NEEDED FOR BACK SIDE.
8. BAKE OVEN LONG ENOUGH, INCLUDES MICROPROCESSOR-CONTROLLED BUFFER STORAGE TO BALANCE LOAD.
9. ROOM REQUIREMENTS: DRY,CLEAN FILTERED AIR, 2830 LITERS/HR/SYSTEM. EXHAUST WITH FUME SCRUBBER TO REMOVE TOXIC (AS) VOLATILES.

PROCEDURE

1. WAFERS ARE LOADED FROM CASSETTE TO TRACK TO SPINDLE.
2. CAPILLARY DISPENSES 0.7-0.8 CM**3 OF SOURCE(+0.2 CM**3 SPILLAGE). 15 SECOND SPIN CYCLE.
3. WAFERS UNLOADED INTO BAKE OVEN CONNECTED TO SPINNER.
4. WAFERS MOVED TO SECOND SPINNER.
5. CAPILLARY DISPENSES 0.7-0.8 CM**3 OF SILICA(+0.2 CM**3 SPILLAGE). 15 SECOND SPIN CYCLE.
6. WAFERS UNLOADED INTO BAKE OVEN CONNECTED TO SPINNER.
7. WAFERS MOVED TO THIRD SPINNER.
8. CAPILLARY DISPENSES 0.7-0.8 CM**3 OF SILICA(+0.2 CM**3 SPILLAGE). 15 SECOND SPIN CYCLE.
9. WAFERS UNLOADED INTO BAKE OVEN CONNECTED TO SPINNER.
   WAFERS UNLOADED INTO SILICON BOAT.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
III MODEL 3 SPINNER-3 TRACKS	720.00 SH/HR	100.0%	$ 40000.	85.0%	60.
III MODEL 3 OVEN-3 TRACKS IN	720.00 SH/HR	100.0%	$ 20000.	85.0%	60.
III MODEL 3 SPINNER-3 TRACKS	720.00 SH/HR	100.0%	$ 40000.	85.0%	60.
III MODEL 3 OVEN-3 TRACKS IN	720.00 SH/HR	100.0%	$ 20000.	85.0%	60.
III MODEL 3 SPINNER-3 TRACKS	720.00 SH/HR	100.0%	$ 40000.	85.0%	60.
III MODEL 3 OVEN-3 TRACKS IN	720.00 SH/HR	100.0%	$ 20000.	85.0%	60.

LABOR
(DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	III MODEL 3 SPINNER-3 TRACKS	3.330E-01		
HOURLY OPERATOR	III MODEL 3 OVEN-3 TRACKS IN	3.330E-01		
ENGR. SUPPORT	III MODEL 3 SPINNER-3 TRACKS	5.000E-03		
MAINTENANCE	III MODEL 3 SPINNER-3 TRACKS	1.500E-01		
MAINTENANCE	III MODEL 3 OVEN-3 TRACKS IN	5.000E-02		
FOREMAN	DL	5.000E-02		

Figure 42. Process parameters - spin-on source

ESTIMATE DATE:08/01/77 BY:UHL ROUNDTREE, X7022, SOMERVILLE, ZONE 8 CLASS:DIFFUSION
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:NEAR FUTURE MATERIAL FORM:3.40" WAFER
INPUT UNIT:SHEETS OUTPUT UNIT:SHEETS TRANSPORT IN:SILICON BOAT TRANSPORT OUT:500 SHEET CASSETTE
PROCESS YIELD: 99.0% YIELD GROWTH PROFILE: D
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:FRACTION OF INPUT UNIT VALUE

INPUT UNITS:	0.	0.	0.
FLOOR SPACE,FT**2=	0.	0.	0.

DESCRIPTION:DOPANT SOURCE BY DECOMPOSITION OF POCL3 IN A DIFFUSION FURNACE

ASSUMPTIONS:

1. 3.40" DIAMETER WAFER,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. BACK SIDE OF WAFER PROTECTED WITH SILICA.
3. 4-TUBE POCL3 FURNACE COSTS $70K, INCLUDING FURNACE LINERS & COILS
   PADDLES NEEDED TO LOAD & UNLOAD FURNACE.
   135FT**2 FOR FURNACE & 140FT**2 FOR OPERATOR NEEDED PER SYSTEM.
4. 25 30"-SILICON BOATS NEEDED FOR EACH 4 TUBE POCL3 FURNACE.
   BOATS COST $45 PER INCH.

PROCEDURE

1. INCOMING WAFERS LOADED IN SILICON BOATS CONTAINING 500 WAFERS.
2. BOATS LOADED INTO FURNACE VIA PADDLES.
3. 1 HR CYCLE.
4. BOATS UNLOADED FROM FURNACE VIA PADDLES.
5. WAFERS LOADED INTO 500 WAFER CASSETTE FOR TRANSFER TO NEXT STEP,
   USING CLAM-SHELL UNLOADER AND CASSETTE STACKER.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT	UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
POCL3 DIFFUSION FURNACE(B)	2000.00	SH/HR	100.0%	$ 66600.	85.0%	275.
POCL3 FURNACE LINERS(B)	2000.00	SH/HR	100.0%	$ 5600.	85.0%	0.
POCL3 FURNACE PADDLES(B)	2000.00	SH/HR	100.0%	$ 8000.	85.0%	0.
POCL3 FURNACE COILS(B)	2000.00	SH/HR	100.0%	$ 8000.	85.0%	0.
CLAM-SHELL UNLOADER	2000.00	SH/HR	100.0%	$ 3000.	85.0%	0.
CASSETTE STACKER	2000.00	SH/HR	100.0%	$ 15000.	85.0%	0.
25 30"-SILICON BOATS	2000.00	SH/HR	100.0%	$ 33750.	85.0%	0.

LABOR

(DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	POCL3 DIFFUSION FURNACE(B)	2.500E-01		
ENGR. SUPPORT	POCL3 DIFFUSION FURNACE(B)	2.500E-02		
MAINTENANCE	POCL3 DIFFUSION FURNACE(B)	1.500E-01		
MACH. ATTENDANT	POCL3 DIFFUSION FURNACE(B)	1.000E-01		
FOREMAN	DL	5.000E-02		

SUPPLIES/EXPENSES

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	UNITS	BASE
ELECTRICITY	0.0	4.000E+01	KWH.	PER AVAILABLE INVESTMENT-HOUR OF POCL3 DIFFUSION FURNACE(B)
PHOSPHORUS OXYCHLORIDE	0.0	2.940E-01	GM.	PER INPUT UNIT. % UNITS= 100.0%
NITROGEN	0.0	1.900E+03	CM**3	PER INPUT UNIT. % UNITS= 100.0%
OXYGEN	0.0	4.680E+01	CM**3	PER INPUT UNIT. % UNITS= 100.0%

Figure 43. Process parameters - $POCl_3$ diffusion.

ESTIMATE DATE:08/01/77 BY:FRED MAYER, X6334, SOMERVILLE, ZONE 8 CLASS:GRINDING
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:NEAR FUTURE MATERIAL FORM:3.40" WAFER
INPUT UNIT:SHEETS OUTPUT UNIT:SHEETS TRANSPORT IN:500 SHEET CASSETTE TRANSPORT OUT:500 SHEET CASSETTE
PROCESS YIELD: 95.0% YIELD GROWTH PROFILE: 0
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:VALUE IN$

INPUT UNITS:	0.	0.	0.
FLOOR SPACE,FT**2:	C.	C.	C.

DESCRIPTION:WAFER EDGE IS POLISHED TO MOVE P-N JUNCTION OFF EDGE.

ASSUMPTIONS:

1. 3.40" DIAMETER WAFER,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. 500 WAFERS/CASSETTE. MACHINE HOLDS 1 CASSETTE.
   NOTE: HEADWAY CONTOUR GRINDER HOLDS 10 CASSETTES, 25 WAFERS PER CASSETTE. SIMILAR COST ASSUMED FOR ABOVE SYSTEM.
3. 1 OPERATOR REQUIRED FOR 4 MACHINES.
4. NOTE: TIME FOR GRINDING NEEDS TO BE VERIFIED.
5. NOTE: CLEANLINESS HAS TO BE VERIFIED.
6. WAFERS ARE ROUND (NO FLATS).
7. 3000 WAFERS/HR, ASSUMING 5 MICRONS REMOVED PER WAFER CUT.
8. WATER CONTAINS RUST INHIBITOR AND IS CONTINUOUSLY FILTERED WITH DIATOMACIOUS EARTH FILTER.

PROCEDURE

1. OPERATOR LOADS MACHINE WITH 1 CASSETTE.
2. (5 TRACK) MACHINE EXTRACTS 5 WAFERS FROM CASSETTE.
3. 1 WAFER PLACED ON EACH TRACK (PARALLEL, IN WATER)
4. WAFER HELD AGAINST FLEXIBLE PLASTIC DISK HEAVILY LOADED WITH DIAMOND DUST. RIM POLISHED OFF.
5. WAFERS RINSED AND SPUN DRY.
6. MACHINE LOADS WAFERS INTO CASSETTE.
7. SEQUENCE REPEATED 100 ADDITIONAL TIMES PER CASSETTE.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT	UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
HEADWAY CONTOUR GRINDER	2700.00	SH/HR	100.0%	$ 54000.	85.0%	60.

LABOR
(DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	HEADWAY CONTOUR GRINDER	2.500E-01		
ENGR. SUPPORT	HEADWAY CONTOUR GRINDER	1.000E-02		
MACH. ATTENDANT	HEADWAY CONTOUR GRINDER	5.000E-02		
FOREMAN	DL	5.000E-02		

SUPPLIES/EXPENSES

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	UNITS	BASE
ELECTRICITY	0.0	3.000E-01	KWH.	PER AVAILABLE INVESTMENT-HOUR OF HEADWAY CONTOUR GRINDER
DIAMOND BLADES,ETC.	0.0	2.220E-03	$	PER INPUT UNIT. % UNITS= 100.0%

Figure 44. Process parameters - edge polish.

ESTIMATE DATE:03/01/77 BY:FRED MAYER, X4334, SOMERVILLE, ZONE 8 CLASS:ETCH
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:NEAR FUTURE MATERIAL FORM:3.40" WAFER
INPUT UNIT:SHEETS OUTPUT UNIT:SHEETS TRANSPORT IN:500 SHEET CASSETTE TRANSPORT OUT:500 SHEET CASSETTE
PROCESS YIELD: 99.0% YIELD GROWTH PROFILE: C
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:FRACTION OF INPUT UNIT VALUE

	INPUT UNITS:	0.	C.	C.
FLOOR SPACE,FT**2:		0.	0.	0.

DESCRIPTION:OXIDE IS REMOVED IN HF

ASSUMPTIONS:

1. 3.40" DIAMETER WAFER,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. 500 WAFERS/BOAT X 1 BOAT/CYCLE X 12 CYCLES/HR= 6000 WAFERS/HR.
3. 2 STATIONS PER OPERATOR
4. NEED 1000 LITERS/HR OF WATER.
5. NEED 98 ML HF PER 1000 WAFERS. COST=$1.00E-3 $/G X 1.13G/CM**3= 1.23E-3$/CM**3.

PROCEDURE

1. 1 TEFLON CASSETTE LOADED INTO ETCH TANK CONTAINING HF.
2. 5 MINUTE ETCH PERIOD.
3. AUTOMATIC TRANSFER VIA "WAFER CARTRIDGE TRANSFER ARM" TO THE FIRST RINSE TANK (SHAMBELAN DESIGN).
4. 5 MINUTE RINSE IN 1ST, 2ND, & 3RD RINSE TANKS (ALTO TRANSFER).
5. WAFERS HOT AIR DRIED.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT	UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
OXIDE STRIP STATION(B)	6000.00	SH/HR	100.0%	$ 80000.	85.0%	96.

LABOR

(DL=DIRECT LABOR PERSONS; TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	OXIDE STRIP STATION(B)	5.000E-01		
MAINTENANCE	OXIDE STRIP STATION(B)	1.500E-01		
FOREMAN	DL	5.000E-02		

SUPPLIES/EXPENSES

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	UNITS	BASE
ELECTRICITY	0.0	3.000E+01	KWH.	PER AVAILABLE INVESTMENT-HOUR OF OXIDE STRIP STATION(B)
HYDROFLUORIC ACID	0.0	9.80CE-02	CM**3	PER INPUT UNIT. % UNITS= 100.0%
DE-IONIZED WATER	0.0	1.23CE+06	CM**3	PER AVAILABLE INVESTMENT-HOUR OF OXIDE STRIP STATION(B)

Figure 45. Process parameters - glass removal.

ESTIMATE DATE:07/28/77 BY:DAVE RICHMAN, X2207, RCA LABS, E-321A CLASS:TEST
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:NEAR FUTURE MATERIAL FORM:3.40" WAFER
INPUT UNIT:SHEETS OUTPUT UNIT:SHEETS TRANSPORT IN:500 SHEET CASSETTE TRANSPORT OUT:500 SHEET CASSETTE
PROCESS YIELD: 99.0% YIELD GROWTH PROFILE: 0
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:VALUE IN$

INPUT UNITS:	0.	0.	0.
FLOOR SPACE,FT**2:	0.	0.	0.

DESCRIPTION:POST DIFFUSION 4-POINT PROBE RESISTIVITY MEASUREMENT

ASSUMPTIONS:
1. 3.40" DIAMETER WAFER,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. 100% WAFER SHEET RESISTIVITY TEST.

PROCEDURE
1. OPERATOR LOADS CASSETTE INTO MACHINE.
2. WAFERS AUTOMATICALLY FED TO TEST EQUIPMENT.
3. WAFERS SORTED INTO MAGAZINES.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
SILTEC WAFER SORTER-PROBE	1450.00 SH/HR	100.0%	$ 150000.	80.0%	200.

LABOR
(DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	SILTEC WAFER SORTER-PROBE	2.5CCE-01		
MAINTENANCE	SILTEC WAFER SORTER-PROBE	2.0CCE-01		
FOREMAN	DL	1.000E-01		

SUPPLIES/EXPENSES

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	UNITS	BASE
ELECTRICITY	0.0	5.CCCE+0C	KWH.	PER AVAILABLE INVESTMENT-HOUR OF SILTEC WAFER SORTER-PROBE

Figure 46. Process parameters - inspection.

ESTIMATE DATE:08/01/77 BY:WERNER KERN, K2054, RCA LABS, 03-076 CLASS:METALLIZATION
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:NEAR FUTURE MATERIAL FORM:3.40" WAFER
INPUT UNIT:SHEETS OUTPUT UNIT:SHEETS TRANSPORT IN:500 SHEET CASSETTE TRANSPORT OUT:500 SHEET CASSETTE
PROCESS YIELD: 98.0% YIELD GROWTH PROFILE: 0
SUBPROCESS USED:SCREEN PRINT WAFER REWORK 21.00% OF INPUT PROCESSED
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:VALUE IN$

INPUT UNITS:	0.	0.	0.
FLOOR SPACE,FT**2:	0.	C.	C.

DESCRIPTION:SCREEN PRINTING AND SINTERING CONDUCTIVE NETWORK-FRONT

ASSUMPTIONS:

1. 3.40" DIAMETER WAFER,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. BACK METALLIZATION PATTERN MUST BE SCREEN PRINTED FIRST.
3. AG PASTE: $5.42/TROY OZ. = $.1743/GM, 80% AG, WHEN AG COSTS $4.40/TROY OZ.
   DENSITY OF AG PASTE=3.75G/CM**3. (31.1G=1 TROY OZ.)
   2:1 RATIO FOR INK THICKNESS TO POST FIRING AG THICKNESS.
   NOTE: 5 MILS THINNEST LINE POSSIBLE. WIDTH GREATER THAN OR EQUAL TO 4 TIMES THICKNESS.
4. FRONT AG FINE GRID: 6% COVERAGE, 23 MICRONS THICK AFTER FIRING.
5. FRONT BUS BAR: 1% COVERAGE, 200 MICRONS THICK AFTER FIRING.
6. SCREEN PRINT & DRY SYSTEM:

ITEM	COST	POWER	COMMENTS
LOADER	10.7K	1KW	INSERTS WAFER INTO PRINTER
PRINTER	24.4K	1KW	PRINTER APPLIES PATTERN
COLLATOR	10.0K	1KW	FORMS PARALLEL ROWS FOR DRYER.
DRYER	25.0K	11KW	DRIES INK TO PREVENT SMEARING.
RELOADER	14.7K	1KW	RELOADS WAFERS INTO CASSETTE.
CASSETTES	4.0K	-	HOLDS WAFERS FOR PRINTER.
TOTALS	88.8K	15KW	

7. SCREEN PRINT & FIRE SYSTEM:

ITEM	COST	POWER	COMMENTS
LOADER	10.7K	1KW	INSERTS WAFER INTO PRINTER
PRINTER	24.4K	1KW	PRINTER APPLIES PATTERN
COLLATOR	10.0K	1KW	FORMS PARALLEL ROWS FOR DRYER.
DRYER	25.0K	11KW	DRIES INK TO PREVENT SMEARING.
FURNACE	50.0K	17KW	SINTERS PATTERN AT 550 C.
RELOADER	14.7K	1KW	RELOADS WAFERS INTO CASSETTE.
CASSETTES	4.0K	-	HOLDS WAFERS FOR PRINTER.
TOTALS	138.8K	32KW	

8. BELT->CASSETTE LOADER CAN DO 6000 WAFERS/HR.
9. SCREEN AT $23, REPLACED 3 TIMES PER DAY FOR FINE GRID.
   SCREEN IS REPLACED 2 TIMES PER DAY FOR BUS BAR SYSTEM.
   SQUEEGES AT $.40, REPLACED ONCE PER HOUR.

Figure 47. Process parameters - Ag front metallization.

PROCEDURE

1. OPERATOR LOADS CASSETTE FROM BACK METALLIZATION STEP INTO LOADER.
2. SCREEN PRINT & DRY SYSTEM APPLIES FINE GRID.
   OPTICAL SCANNER VALIDATES PATTERN. 20% REJECT ESTIMATE.
3. OPERATOR LOADS CASSETTE FOR SCREEN PRINT & FIRE SYSTEM.
4. SYSTEM APPLIES FRONT BUS BAR & FIRES. (SEPARATE PRINT STEP NEEDED SINCE PATTERN IS THICKER THAN FINE GRID.)
   OPTICAL SCANNER VALIDATES PATTERN BEFORE FIRING. 1% BUS BAR REJECTS ESTIMATED.
   REJECTS ARE LOADED INTO A CASSETTE BY BELT-X CASSETTE STACKER FOR REWORK.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT	UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
SCREEN PRINT & DRY SYSTEM	1625.00	SH/HR	121.0%	$ 88800.	80.0%	800.
OPTICAL SCANNER-EXCELLON	1625.00	SH/HR	121.0%	$ 15000.	80.0%	16.
BELT->CASSETTE STACKER	1625.00	SH/HR	121.0%	$ 15000.	80.0%	0.
SCREEN PRINT & FIRE SYSTEM	1625.00	SH/HR	101.0%	$ 138800.	80.0%	1600.
OPTICAL SCANNER-EXCELLON	1625.00	SH/HR	101.0%	$ 15000.	80.0%	16.
BELT->CASSETTE STACKER	1625.00	SH/HR	101.0%	$ 15000.	80.0%	0.

LABOR

(DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	SCREEN PRINT & DRY SYSTEM	3.330E-01		
HOURLY OPERATOR	SCREEN PRINT & FIRE SYSTEM	3.330E-01		
ENGR. SUPPORT	SCREEN PRINT & DRY SYSTEM	2.500E-02		
ENGR. SUPPORT	SCREEN PRINT & FIRE SYSTEM	2.500E-02		
MAINTENANCE	SCREEN PRINT & DRY SYSTEM	2.000E-01		
MAINTENANCE	SCREEN PRINT & FIRE SYSTEM	2.000E-01		
MAINTENANCE	OPTICAL SCANNER-EXCELLON	1.000E-02		
MAINTENANCE	BELT->CASSETTE STACKER	2.000E-01		
FOREMAN	DL	1.000E-01		

SUPPLIES/EXPENSES

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	UNITS	BASE
ELECTRICITY	0.0	1.500E+01	KWH.	PER AVAILABLE INVESTMENT-HOUR OF SCREEN PRINT & DRY SYSTEM
ELECTRICITY	0.0	3.200E+01	KWH.	PER AVAILABLE INVESTMENT-HOUR OF SCREEN PRINT & FIRE SYSTEM
ELECTRICITY	0.0	1.000E-01	KWH.	PER AVAILABLE INVESTMENT-HOUR OF OPTICAL SCANNER-EXCELLON
SCREENS	0.0	2.880E+00	$	PER AVAILABLE INVESTMENT-HOUR OF SCREEN PRINT & DRY SYSTEM
SCREENS	0.0	1.920E+00	$	PER AVAILABLE INVESTMENT-HOUR OF SCREEN PRINT & FIRE SYSTEM
SQUEEGEES	0.0	4.000E-01	$	PER AVAILABLE INVESTMENT-HOUR OF SCREEN PRINT & DRY SYSTEM
SQUEEGEES	0.0	4.000E-01	$	PER AVAILABLE INVESTMENT-HOUR OF SCREEN PRINT & FIRE SYSTEM
SOLVENT-INK	0.0	1.580E-01	CM**3	PER INPUT UNIT. % UNITS= 121.0%
SOLVENT-INK	0.0	1.580E-01	CM**3	PER INPUT UNIT. % UNITS= 101.0%
THERMOCOUPLE,ETC.	0.0	6.060E-04	$	PER INPUT UNIT. % UNITS= 121.0%
THERMOCOUPLE,ETC.	0.0	6.060E-04	$	PER INPUT UNIT. % UNITS= 101.0%
INK AG-FRONT FINE GRID	0.0	6.740E-03	$	PER INPUT UNIT. % UNITS= 100.0%
INK AG-FRONT FINE GRID COST	0.0	2.820E-03	$	PER INPUT UNIT. % UNITS= 21.0%
INK AG-FRONT BUS BAR	0.0	1.460E-02	$	PER INPUT UNIT. % UNITS= 100.0%
INK AG-FRONT BUS BAR COST	0.0	6.150E-03	$	PER INPUT UNIT. % UNITS= 1.0%

Figure 47. Continued.

ESTIMATE DATE:08/01/77 BY:WERNER KERN, X2094, RCA LABS, 03-076 CLASS:METALLIZATION
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:NEAR FUTURE MATERIAL FORM:3.40" WAFER
INPUT UNIT:SHEETS OUTPUT UNIT:SHEETS TRANSPORT IN:500 SHEET CASSETTE TRANSPORT OUT:500 SHEET CASSETTE
PROCESS YIELD: 98.0% YIELD GROWTH PROFILE: 0
SUBPROCESS USED:SCREEN PRINT WAFER REWORK 0.5% OF INPUT PROCESSED
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:VALUE IN$

INPUT UNITS:	0.	0.	0.
FLOOR SPACE,FT**2:	0.	0.	0.

DESCRIPTION:SCREEN PRINTING AND SINTERING CONDUCTIVE NETWORK-BACK

ASSUMPTIONS:

1. 3.40" DIAMETER WAFER,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. BACK METALLIZATION PATTERN MUST BE SCREEN PRINTED FIRST.
3. AG PASTE: $5.42/TROY OZ. = $.1743/GM, 80% AG, WHEN AG COSTS $4.40/TROY OZ.
   DENSITY OF AG PASTE=3.75G/CM**3. (31.1G=1 TROY OZ.)
   2:1 RATIO FOR INK THICKNESS TO POST FIRING AG THICKNESS.
   NOTE: 5 MILS THINNEST LINE POSSIBLE. WIDTH GREATER THAN OR EQUAL TO 4 TIMES THICKNESS.
4. BACK AG GRID: 25% COVERAGE, 12. MICRONS THICK AFTER FIRING.
5. SCREEN PRINT & FIRE SYSTEM:

ITEM	COST	POWER	COMMENTS
LOADER	10.7K	1KW	INSERTS WAFER INTO PRINTER
PRINTER	24.4K	1KW	PRINTER APPLIES PATTERN
COLLATOR	10.0K	1KW	FORMS PARALLEL ROWS FOR DRYER.
DRYER	29.0K	11KW	DRIES INK TO PREVENT SMEARING.
FURNACE	50.0K	17KW	SINTERS PATTERN AT 550 C.
RELOADER	14.7K	1KW	RELOADS WAFERS INTO CASSETTE.
CASSETTES	4.0K	-	HOLDS WAFERS FOR PRINTER.
TOTALS	138.8K	32KW	

6. BELT->CASSETTE LOADER CAN DO 6000 WAFERS/HR.
7. SCREEN AT $23, REPLACED 2 TIMES PER DAY.
   SQUEEGEE AT $.40, REPLACED ONCE PER HOUR.
8. 0.5% BACK REWORK ESTIMATED.
9. FIRING OF BACK NEEDED SO THAT PASTE IS NOT REMOVED IN CASE OF FRONT GRID REWORK.

PROCEDURE

1. OPERATOR LOADS CASSETTE FROM PREVIOUS STEP INTO LOADER.
2. SCREEN PRINT & FIRE SYSTEM APPLIES BACK GRID.
   OPTICAL SCANNER VALIDATES PATTERN. 0.5% REJECTS REWORKED.
   REJECTS ARE LOADED INTO A CASSETTE BY BELT->CASSETTE STACKER FOR REWORK.
3. CASSETTE TRANSFERRED TO FRONT METALLIZATION PROCESS.
4. REJECTS ARE REWORKED & RECYCLED.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
SCREEN PRINT & FIRE SYSTEM	1625.00 SH/HR	100.5%	$ 138800.	80.0%	1600.
OPTICAL SCANNER-EXCELLON	1625.00 SH/HR	100.5%	$ 15000.	80.0%	16.
BELT->CASSETTE STACKER	1625.00 SH/HR	100.5%	$ 15000.	80.0%	0.

Figure 48. Process parameters - Ag back metallization.

LABOR

(DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	SCREEN PRINT & FIRE SYSTEM	3.330E-01		
ENGR. SUPPORT	SCREEN PRINT & FIRE SYSTEM	2.500E-02		
MAINTENANCE	SCREEN PRINT & FIRE SYSTEM	2.000E-01		
MAINTENANCE	OPTICAL SCANNER-EXCELLON	1.000E-02		
MAINTENANCE	BELT->CASSETTE STACKER	2.000E-01		
FOREMAN	DL	1.000E-01		

SUPPLIES/EXPENSES

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	UNITS	BASE
ELECTRICITY	0.0	3.200E+01	KWH.	PER AVAILABLE INVESTMENT-HOUR OF SCREEN PRINT & FIRE SYSTEM
ELECTRICITY	0.0	1.000E-01	KWH.	PER AVAILABLE INVESTMENT-HOUR OF OPTICAL SCANNER-EXCELLON
SCREENS	0.0	1.920E+00	$	PER AVAILABLE INVESTMENT-HOUR OF SCREEN PRINT & FIRE SYSTEM
SQUEEGEES	0.0	4.000E-01	$	PER AVAILABLE INVESTMENT-HOUR OF SCREEN PRINT & FIRE SYSTEM
SOLVENT-INK	0.0	1.580E-01	CM**3	PER INPUT UNIT. % UNITS= 101.0%
THERMOCOUPLE,ETC.	0.0	6.060E-04	$	PER INPUT UNIT. % UNITS= 101.0%
INK AG-BACK GRID	0.0	2.220E-02	$	PER INPUT UNIT. % UNITS= 100.0%
INK AG-BACK GRID LOST	0.0	9.320E-03	$	PER INPUT UNIT. % UNITS= 0.5%

Figure 48. Continued.

ESTIMATE DATE:08/01/77 BY:WERNER KERN, X2094, RCA LABS, 83-076 CLASS:AR COATING
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:NEAR FUTURE MATERIAL FORM:3.40" WAFER
INPUT UNIT:SHEETS OUTPUT UNIT:SHEETS TRANSPORT IN:500 SHEET CASSETTE TRANSPORT OUT:500 SHEET CASSETTE
PROCESS YIELD: 99.0% YIELD GROWTH PROFILE: 0
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:FRACTION OF INPUT UNIT VALUE

INPUT UNITS:	0.	0.	0.
FLOOR SPACE,FT**2:	0.	0.	0.

DESCRIPTION:SPRAY-ON ANTIREFLECTION COATING(8)

ASSUMPTIONS:

1. 3.40" DIAMETER WAFER,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. 500 WAFERS/CASSETTE
3. NOTE: IN-HOUSE AR COATING NEEDS TO BE DEVELOPED.
   LIQUID SPRAY-ON SOURCE(TIO2,SIO2) AT $10/LITER. 0.1 CM**3 WILL COVER 1 SIDE WITH 0.07 MICRONS.
   APPLIED AFTER FINAL METALLIZATION.
4. ROOM REQUIREMENTS: DRY,CLEAN FILTERED AIR, 2830 LITERS/HR/SYSTEM.
5. 0.5 FT**3/MIN OF NITROGEN NEEDED(= 8.5CE+05 CM**3/HR.)
6. ZICON MODEL 11000 AUTOCOATER SYSTEM ($185K) INCLUDES:
   1. CASSETTE UNLOADER ($15K)
   2. WAFER COLLATOR ($10K)
   3. SPRAY MACHINE; AIR FLASH PRE-DRY STATION; I.R. PRE-DRY;
      MICROCOMPUTER FEEDBACK CONTROLLER;
      200 DEG. C. CONVECTION OVEN; 400 DEG. C. CONVECTION OVEN.
      TOTAL SUBSYSTEM PRICE: $110K.
   4. CASSETTE LOADER ($15K)
   5. AUTOMATIC SAMPLE EJECT (NEEDS DEVELOPMENT, ABOUT $10K)
   6. THICKNESS MONITOR ($10K)
   7. CASSETTE RELOADER (FOR SAMPLES) ($15K)
      TOTAL SYSTEM PRICE: $185K
7. NEED SPECS FOR AR COATING STRIP FOR REWORK.???????

PROCEDURE

1. WAFERS ARE LOADED FROM CASSETTE TO CONVEYOR BELT IN ROWS OF 5.
2. WAFERS ARE SPRAYED WITH 1000A OF TITANIA-SILICA PRODUCING LIQUID
   SOURCE MATERIAL WITH PRESSURIZED DRY NITROGEN AS CARRIER GAS.
3. WAFERS ARE AIR-FLASHED TO REMOVE BUBBLES AND TO SETTLE COATING MATERIAL.
4. AFTER DEPOSITION, WAFER TRANSPORTED VIA BELT TO INFRARED DRYING ZONE TO PERMIT CASSETTE HANDLING.
5. AFTER PRE-DRY, WAFERS LOADED INTO CASSETTE.
6. EVERY 10TH OR 15TH WAFER IS EJECTED AUTOMATICALLY FOR THICKNESS
   TESTING BY ELLIPSOMETER; DATA IS FED TO MICROCOMPUTERIZED SERVO
   MECHANISM AT SPRAY BOOTH.
7. WAFERS WITHIN SPEC ARE RELOADED IN A SEPARATE CASSETTE; FAILED
   WAFERS WILL BE STRIPPED IN DILUTE AMMONIUM FLUORIDE SOLUTION AND
   COLLECTED FOR REPROCESSING.
8. WAFERS ARE BAKED FOR 15 MIN. AT 200 C. IN AIR.
9. WAFERS ARE BAKED FOR 15 MIN. AT 400 C. IN AIR.
   CASSETTES TRANSFERRED TO NEXT PROCESS STEP.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
ZICON MODEL 11000 AUTOCOATER	3385.00 SH/HR	100.0%	$ 185000.	90.0%	360.

Figure 49. Process parameters - AR spray coat.

LABOR
(CL=CIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	ZICON MODEL 11000 AUTOCOATER	5.0CCE-01		
MAINTENANCE	ZICON MODEL 11000 AUTOCOATER	1.000E-01		
ENGR. SUPPORT	ZICON MODEL 11000 AUTOCOATER	2.5C0E-01		

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	SUPPLIES/EXPENSES UNITS	BASE
ELECTRICITY	0.0	3.00CE+01	KWH.	PER AVAILABLE INVESTMENT-HOUR CF ZICON MODEL 11000 AUTOCOATER
NITROGEN	0.0	8.500E+05	CM**3	PER AVAILABLE INVESTMENT-HOUR OF ZICON MODEL 11000 AUTCCCATER
IN-HOUSE SPRAY-ON AR COATING	C.0	1.23CE-01	C**3	PER INPUT UNIT. % UNITS= 105.0%

Figure 49. Continued.

ESTIMATE DATE:09/20/77 BY:DAVE RICHMAN, X3207, RCA LABS, E-321A CLASS:TEST
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:NEAR FUTURE MATERIAL FORM:3.40" WAFER
INPUT UNIT:SHEETS OUTPUT UNIT:SOLAR CELLS TRANSPORT IN:500 SHEET CASSETTE TRANSPORT OUT:500 SHEET CASSETTE
PROCESS YIELD: 90.0% YIELD GROWTH PROFILE: 0
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:FRACTION OF INPUT UNIT VALUE

INPUT UNITS:	0.	0.	0.
FLOOR SPACE,FT**2:	0.	0.	0.

DESCRIPTION:WAFER ELECTRICAL TEST AND SORT.

ASSUMPTIONS:
1. 3.40" DIAMETER WAFER,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. TEST FOR: OPEN CIRCUIT VOLTAGE;SHORT CIRCUIT CURRENT;REVERSE BIAS LEAKAGE; FILL FACTOR.
3. MINICOMPUTER-CONTROLLED MEASUREMENT OF 12 POINTS ALONG KNEE OF I-V CURVE FOR KNOWN LIGHTING.
4. WAFERS BELOW 10% EFFICIENCY ARE REJECTED. 95% YIELD ESTIMATED.

PROCEDURE
1. OPERATOR LOADS CASSETTE INTO MACHINE.
2. WAFERS AUTOMATICALLY FED TO TEST EQUIPMENT AND MEASUREMENTS MADE.
3. WAFERS SORTED INTO MAGAZINES USING CRITERIA TO BE DEFINED.
4. OPERATOR REMOVES CASSETTES AS THEY ARE FILLED.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
SILTEC WAFER SORTER-W.E.T.	1200.00 SH/HR	100.0%	$ 175000.	80.0%	200.

LABOR
(DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	SILTEC WAFER SORTER-W.E.T.	2.500E-01		
MAINTENANCE	SILTEC WAFER SORTER-W.E.T.	2.000E-01		
FOREMAN	DL	1.000E-01		

SUPPLIES/EXPENSES

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	UNITS	BASE
ELECTRICITY	0.0	5.000E+00	KWH.	PER AVAILABLE INVESTMENT-HOUR OF SILTEC WAFER SORTER-W.E.T.

Figure 50. Process parameters - test.

ESTIMATE DATE:07/28/77 BY:DICK SCOTT, PC4971, CAMDEN, BLDG. 10-8 CLASS:ARRAY FABRICATION
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:NEAR FUTURE MATERIAL FORM:3.40" WAFER
INPUT UNIT:SOLAR CELLS OUTPUT UNIT:SOLAR CELLS TRANSPORT IN:500 SHEET CASSETTE TRANSPORT OUT:PICKUP TABLE
PROCESS YIELD: 98.0% YIELD GROWTH PROFILE: 0
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:VALUE IN$

INPUT UNITS:	0.	0.	0.
FLOOR SPACE,FT**2:	0.	0.	0.

DESCRIPTION:REFLOW SOLDER INTERCONNECTION(S)

ASSUMPTIONS:

1. 3.40" DIAMETER WAFER,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. 1/3 REWORK OPERATOR PER SYSTEM REWORKS STRING TEST REJECTS (=1% OF INPUT).
   ARRAY PANEL REWORK OPERATORS REWORK 1% OF PANELS AT RATE OF 2 PER HR.
3. EACH PANEL CONTAINS 15 STRINGS OF 12 CELLS EACH.

PROCEDURE

1. FIRST INTERCONNECTION STATION:ROTARY INDEX TABLE
A. CASSETTE LOADED WITH BACK OF CELL FACE-UP.
B. CELL FED TO STATION #1, WHERE IT IS ROTATED UNTIL SILVER PAD IS DETECTED BY SENSOR. VACUUM PAD SECURES CELL IN POSITION.
C. AT STATION #2, SILVER PAD IS BURNISHED BOTH SIDES & SLIGHT POSITIVE AIR PRESSURE USED TO REMOVE RESIDUE FROM BURNISHED PAD.
D. AT STATION #3, SOLDER PASTE DOT IS APPLIED TO SILVERED AREA (BOTTOM FACE)
E. AT STATION #4, INSULATED TAB IS BURNISHED, POSITIONED AND SOLDERED ON SOLDER TAB.
   ONCE SOLDERED, TAB IS THEN CUT TO LENGTH.
F. AT STATION #5, CELL IS FLIPPED OVER. VACUUM STILL HOLDS CELL IN POSITION.
   SOLDER PASTE DOT IS APPLIED TO TOP FACE OF CELL.
G. AT STATION #6, BOTTOM VACUUM RELEASES & TOP VACUUM PICK-UP ARM PICKS UP CELL & SWINGS CELL OVER TO STRING TRAY BELT.
2. SECOND INTERCONNECT STATION & COMPLETE STRING ELECTRICAL CHECK.
A. VACUUM LINE IS ATTACHED TO STRING TRAY, HOLDING CELLS IN POSITION.
B. AT SECOND INTERCONNECT STATION, ARM SWINGS TO WIPE TAB OVER SOLDER DOT.
   TAB IS THEN SOLDERED ON TOP FACE OF CELL.
C. AT NEXT STATION, AUTOMATIC TEST PROBE PERFORMS DARK I/V STRING TEST.
   IF STRING IS OK, IT CONTINUES TO STORAGE RACK.
   IF STRING FAILS, STRING TRAY IS REJECTED AND REMOVED FROM BELT.
   FAILED STRINGS ARE MANUALLY REWORKED AND THEN PLACED IN STORAGE RACK.
3. SOLAR PANEL INTERCONNECT TECHNIQUE.
A. PREINSTALLED BUS BAR WITH EXTERNAL TABS PLACED ON BELT.
B. "STRING PICK UP TRAY" INTERFACES INTO HOLDER AND VACUUM PICKS UP
   COMPLETE STRING OF CELLS. STRING PICK UP TRAY THEN WITHDRAWS OUT
   OF HOLDER AND POSITIONS OVER ARRAY TRAY.
   VACUUM IS RELEASED AND CELLS ARE DEPOSITED INTO ARRAY TRAY.
C. ARRAY TRAY INDEXED INTO POSITION FOR EACH STRING OF CELLS.
D. TAB IS WIPED OVER ONTO INTERCONNECT BUS.
E. INTERCONNECT TABS ARE SOLDERED(2 PLACES FOR EACH STRING OF CELLS)
F. DARK I/V ELECTRICAL TEST PERFORMED FOR COMPLETE ARRAY PANEL.
   IF PANEL PASSES TEST, HOLDER WITH PANEL PLACED IN STORAGE RACK.
   IF PANEL FAILS TEST, PANEL IS MANUALLY REWORKED AND THEN PLACED IN STORAGE RACK.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT	UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
ROTARY INDEX TABLE SYSTEM	1200.00	CELLS/HR	100.0%	$ 27500.	90.0%	24.
RS STRING INTERCONNECT EQUIP	2400.00	CELLS/HR	100.0%	$ 119000.	90.0%	36.
PANEL INTERCONNECT STATION	3600.00	CELLS/HR	100.0%	$ 180000.	90.0%	120.

Figure 51. Process parameters - reflow solder interconnect.

LABOR

(DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	ROTARY INDEX TABLE SYSTEM	1.670E-01		
REWORK OPERATOR	ROTARY INDEX TABLE SYSTEM	3.330E-01		
MAINTENANCE	ROTARY INDEX TABLE SYSTEM	1.000E-01		
HOURLY OPERATOR	RS STRING INTERCONNECT EQUIP	1.000E+00		
MAINTENANCE	RS STRING INTERCONNECT EQUIP	1.000E-01		
MAINTENANCE	PANEL INTERCONNECT STATION	1.000E-01		
REWORK OPERATOR	THRUPUT		360.0	1.0
FOREMAN	DL	1.000E-01		

EXPENSE NAME	ANNUAL FIXED PART	VARIABLE PART	SUPPLIES/EXPENSES UNITS	BASE
ELECTRICITY	0.0	0.0	KWH.	PER AVAILABLE INVESTMENT-HOUR OF ROTARY INDEX TABLE SYSTEM
ELECTRICITY	0.0	0.0	KWH.	PER AVAILABLE INVESTMENT-HOUR OF RS STRING INTERCONNECT EQUIP
ELECTRICITY	0.0	0.0	KWH.	PER AVAILABLE INVESTMENT-HOUR OF PANEL INTERCONNECT STATION
AG-PLATED CU WIRE	0.0	1.430E-03	$	PER INPUT UNIT. % UNITS= 100.0%

Figure 51. Continued.

ESTIMATE DATE:07/29/77 BY:DICK SCOTT, PC4971, CAMDEN, BLDG. 1C-8 CLASS:ARRAY FABRICATION
CATEGORY:PROCESS DEFINITION TECHNOLOGY LEVEL:NEAR FUTURE MATERIAL FORM:3.40" WAFER
INPUT UNIT:SOLAR CELLS OUTPUT UNIT:ARRAY MODULES TRANSPORT IN:PICKUP TABLE TRANSPORT OUT:CURING RACK
PROCESS YIELD: 99.5% YIELD GROWTH PROFILE: 0
INPUT UNIT SALVAGE FACTOR: 0.0 FACTOR GP#: 0 SALVAGE OPTION:VALUE IN$

INPUT UNITS:	0.	0.	C.
FLOOR SPACE,FT**2:	0.	0.	0.

DESCRIPTION:GLASS/PVB/CELL ARRAY ASSEMBLY

ASSUMPTIONS:

1. 3.40" DIAMETER WAFER,(100) ORIENTATION,P-TYPE, 1-5 OHM-CM.
2. EACH PANEL CONTAINS 15 STRINGS OF 12 CELLS EACH.
3. MATERIAL REQUIREMENTS:
   1. FRAME: $6.88/180 = $3.82E-02/CELL
   2. GLASS: $7.04/180 = $3.91E-02/CELL
   3. PVB: $6.40/180 = $3.56E-02/CELL
   4. PANEL CONNECTOR: $5.00/180 = $2.78E-02/CELL
   5. GASKET,PVC & AL FOIL TAPES: $1.00/180 = $5.56E-03/CELL

PROCEDURE

1. GLASS WASHED AND DRIED, THEN STORED IN CLEAN STORAGE AREA.
2. GLASS IS PLACED ON AIR TABLE. PVB IS THEN PLACED ON GLASS.
   ROLLER TRANSVERSES, PVB ADHERING TO GLASS.
   GLASS WITH PVB PLACED IN CLEAN STORAGE AREA.
3. GLASS FROM STORAGE RACK PLACED PVB SIDE UP.
   ARRAY TRAY FLIPPED OVER, VACUUM HOLDING CELL STRING ASSEMBLY UNTIL PLACED ON PVB.
   ARRAY TRAY IS ALIGNED WITH BOTTOM GLASS PLATE.
   ARRAY TRAY IS FLIPPED OVER ONTO PVB.
4. SECOND SHEET OF BOTH PVB & GLASS ALIGNED WITH BOTTOM GLASS OVER STRING ASSEMBLY OF CELLS.
   ARRAY ASSEMBLY ENCLOSED IN VACUUM BAG & SENT TO STORAGE OR AUTOCLAVE.
5. FRAME PIECES CUT, ASSEMBLED, AND SPOT WELDED.
   FRAMES SENT TO GLASS ASSEMBLY LINE VIA CONVEYOR.
6. GLASS PANEL ASSEMBLY REMOVED FROM AUTOCLAVE VACUUM BAG & POSITIONED ON ROTATING TABLE.
   ALUMINIZED TAPE IS APPLIED AUTOMATICALLY OVER EDGES AND BOTH SIDES OF GLASS.
   TAPE IS WIPED OVER AND HEAT SEALED TO GLASS.
7. RUBBER GASKET PLACED AROUND GLASS ASSEMBLY & ASSEMBLY PLACED IN FRAME.
   GLASS RETAINING FRAME INSERTED AND MODULE COMPLETED USING PRESS.
8. AFTER FINAL INSPECTION AND TEST, ARRAY MODULE SENT TO PACKAGING AREA.

INVESTMENTS

INVESTMENT NAME	MAX. THRUPUT UNITS	% INPUT UNITS PROCESSED	FIRST COST	AVAIL.	AREA,FT**2
GLASS/PVB/PANEL ASM. STATION	7200.00 CELLS/HR	100.0%	$ 582000.	90.0%	900.
FINAL ASSEMBLY EQUIPMENT(8)	7200.00 CELLS/HR	100.0%	$ 27500.	90.0%	275.
FRAME ASSEMBLY EQUIPMENT	21600.00 CELLS/HR	100.0%	$ 75200.	90.0%	225.

LABOR

(DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
HOURLY OPERATOR	GLASS/PVB/PANEL ASM. STATION	4.000E+00		
HOURLY OPERATOR	FRAME ASSEMBLY EQUIPMENT	1.000E+00		
HOURLY OPERATOR	FINAL ASSEMBLY EQUIPMENT(8)	4.000E+00		
MAINTENANCE	GLASS/PVB/PANEL ASM. STATION	1.000E-01		

Figure 52. Process parameters - glass-PVB panel.

LABOR

(DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME	LABOR REQUIREMENTS BASE	# PERSONS/SHIFT/BASE UNIT	THRUPUT/HR/PERSON	% INPUT UNITS PROCESSED
MAINTENANCE	FRAME ASSEMBLY EQUIPMENT	1.000E-01		
MAINTENANCE	FINAL ASSEMBLY EQUIPMENT(B)	1.000E-01		
FOREMAN	DL	1.000E-01		

	ANNUAL	SUPPLIES/EXPENSES		
EXPENSE NAME	FIXED PART	VARIABLE PART	UNITS	BASE
ELECTRICITY	0.0	0.0	KWH.	PER AVAILABLE INVESTMENT-HOUR OF GLASS/PVB/PANEL ASM. STATION
ELECTRICITY	0.0	0.0	KWH.	PER AVAILABLE INVESTMENT-HOUR OF FRAME ASSEMBLY EQUIPMENT
ELECTRICITY	0.0	0.0	KWH.	PER AVAILABLE INVESTMENT-HOUR OF FINAL ASSEMBLY EQUIPMENT(B)
FRAME	0.0	3.820E-02	$	PER INPUT UNIT. % UNITS= 100.0%
GLASS	0.0	3.910E-02	$	PER INPUT UNIT. % UNITS= 100.0%
PVB	0.0	3.560E-02	$	PER INPUT UNIT. % UNITS= 100.0%
PANEL CONNECTOR	0.0	2.780E-02	$	PER INPUT UNIT. % UNITS= 100.0%
GASKET,PVC & AL FOIL TAPES	0.0	5.560E-03	$	PER INPUT UNIT. % UNITS= 100.0%

Figure 52. Continued.

```
ESTIMATE DATE:07/28/77  BY:DICK SCOTT, PC4971, CAMDEN, BLDG. 10-8                                  CLASS:PACKAGING
CATEGORY:PROCESS DEFINITION       TECHNOLOGY LEVEL:EXISTING     MATERIAL FORM:3.40" WAFER
INPUT UNIT:ARRAY MODULES    OUTPUT UNIT:ARRAY MODULES    TRANSPORT IN:CURING RACK        TRANSPORT OUT:BOX
PROCESS YIELD:100.0%   YIELD GROWTH PROFILE: C
INPUT UNIT SALVAGE FACTOR:  0.0   FACTOR GP#: 0     SALVAGE OPTION:VALUE INS

      INPUT UNITS:        C.        C.        C.
FLOOR SPACE,FT**2:        0.        0.        C.

DESCRIPTION:ARRAY MODULES PLACED IN WOOD CRATE.

                                                    ASSUMPTIONS:

1. 16.0 FT**2 PANEL.
2. 16.0 FT**2 OF WOOD CRATE NEEDED AT $.08 PER FT**2 OF PANEL.
3. 1 OPERATOR CAN PACKAGE 50 MODULES/HR USING PACKAGING EQUIPMENT.
4. N, THE NUMBER OF PANELS PER WOOD CRATE, IS TO BE DETERMINED.

                                                    PROCEDURE

1. OPERATOR PLACES N PANELS FROM STORAGE RACK INTO A BOX.
2. BOX STAPLED.
3. BOX PLACED ON STACK FOR REMOVAL TO WAREHOUSE.

                                                    INVESTMENTS

INVESTMENT NAME              MAX. THRUPUT UNITS    % INPUT UNITS PROCESSED  FIRST COST  AVAIL.  AREA,FT**2
PACKAGING EQUIPMENT               50.00 A.M./HR                    100.0%  $   25000.  100.0%        100.

                                                    LABOR
                                                (DL=DIRECT LABOR PERSONS;TL=TOTAL LABOR PERSONS)

NAME              LABOR REQUIREMENTS BASE      # PERSONS/SHIFT/BASE UNIT    THRUPUT/HR/PERSON  % INPUT UNITS PROCESSED
HOURLY OPERATOR   PACKAGING EQUIPMENT                      1.000E+00
FOREMAN           DL                                      1.000E-01

                                ANNUAL                          SUPPLIES/EXPENSES
EXPENSE NAME                    FIXED PART   VARIABLE PART   UNITS   BASE
BOX FOR MODULE                     C.0          1.28CE+CC    $       PER INPUT UNIT. % UNITS=  100.0%
```

Figure 53. Process parameters - packaging.

assembly. The process step that was changed was junction formation and back diffusion. All cases were analyzed at 1, 3, 10, 30, 50, and 100 MW/year. Case I was ion-implantation on both sides, Case II was spin-on source on the backside and $POCl_3$ in front, Case III was spin-on source on both sides, and Case IV was print-on source on both sides. The processing tree for these sequences is shown in Fig. 54. The matrix was run ignoring wafer costs since all process sequences saturate in cost at a 30 MW/yr production level, a 30-MW factory design is our goal. The spread in cost was about 20% with the lowest cost being print-on source on both sides (Case IV) closely followed by ion implantation on both sides (Case I) while the highest was spin-on back and $POCl_3$ front (Case II). We chose the $POCl_3$ junction formation due to proven cell efficiency and rejected ion implantation for the near term because present machine throughput is inadequate, and increased throughputs to the required level are not anticipated by 1982.

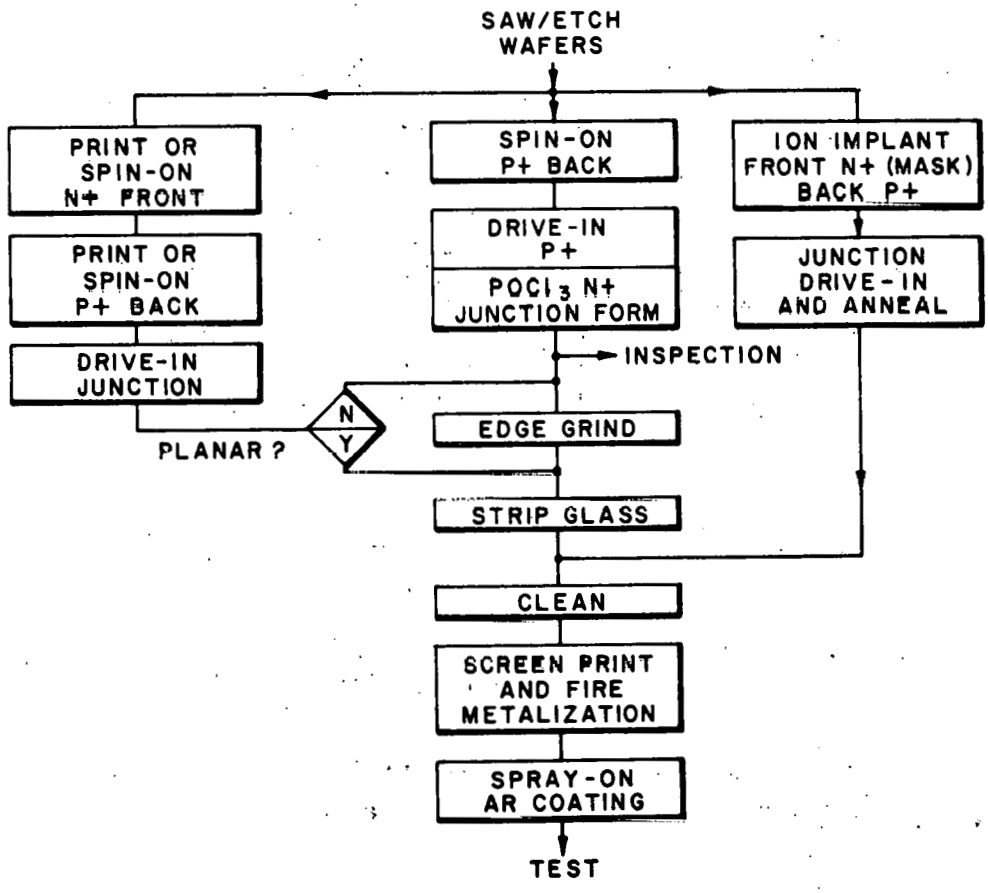

Figure 54. Cell processing sequence.

C. IMPACT OF MANUFACTURING VOLUME AND POLYSILICON COST

It is important to determine the level of production for which volume cost reductions saturate for each of the sheet preparation cases considered. The results of such a calculation are given here assuming that the processes which follow the various sheet preparations are the same as shown in Table 6. We have considered production levels ranging from 3 to 100 MW/yr and have shown the impact of single versus multiple pulling of crystal, i.d. sawing versus wire sawing, and have also considered the limiting case of $0/kg polycrystalline cost. The results of these calculations are shown in Fig. 55. The cost reduction with increased volume reflects more efficient use of capital and labor, while the cost reduction as a function of sheet preparation reflects cost reduction in materials and expense items.

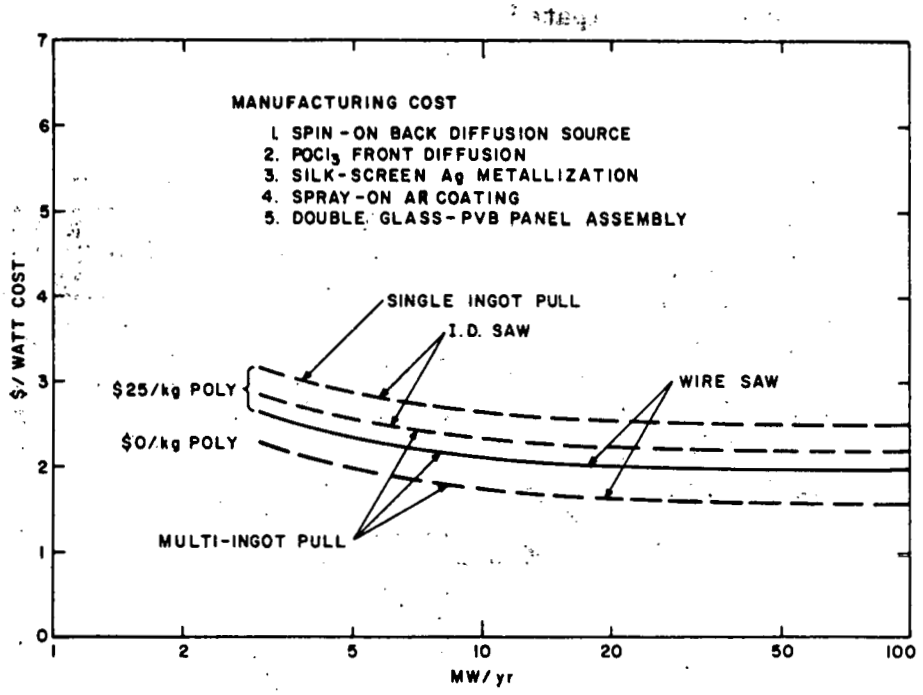

Figure 55. Cost as a function of manufacturing volume with wafer preparation and polysilicon cost as parameters.

Since volume cost reductions are saturated for production levels beyond 30 MW/yr, we have based our preliminary factory design at that production level.

D. FACTORY LAYOUT

The final factory layout is shown in Fig. 56. The factory area is 100,000 ft^2 with provision for office space, cafeteria, storage, receiving, and warehousing. There also is provision for buffering between critical processing steps. The equipment required for this factory is listed in Table 7.

E. SELLING PRICE

We have used the criteria described in Section II in order to arrive at the final selling price. The procedure requires an estimate of factory overhead, such as plant, land, equipment (other than manufacturing equipment), support personnel, materials in storage or in process, and an estimate of the difference between receivables and payables. The itemized list of these components is given in Tables 8 and 9. The manufacturing costs are \$2.011/W so that total cost is \$2.145/W.

We have assumed that the entire factory and capital equipment are financed by debt. In order to remove consideration of debit ratio (% of assets financed by debt) from an estimate of profit, we will assume the following relationship.

$$\frac{\text{Net profit after taxes + after-tax interest}}{\text{First cost of assets}} = 0.15$$

The before-tax interest on the factory is \$0.039/W (factory investment) and the before-tax interest on manufacturing equipment investment is \$0.074/W. Equipment assets are \$0.824/W and factory assets are \$0.430/W. The before-tax profit is \$0.263/W. Thus, the total price is \$2.41/W.

F. CONCLUSIONS - ANALYSIS AND FACTORY DESIGN FOR 1982

From the cost production analyses conducted here, it can be concluded that that the interim 1982 goal of \$2/W array cost can be achieved in a large-scale (~30 MW/yr) factory. The analysis clearly shows that the largest cost centers and therefore the areas needing the greatest attention are the crystal pulling and wafer sawing operations. Conventional Czochralski single-ingot pulling and i.d. wafer sawing are too wasteful of materials and result in a total cost of about \$2.50/W. By considering multiple-ingot pulling and high-yield wire sawing of wafers, we have shown that the cost is reduced to

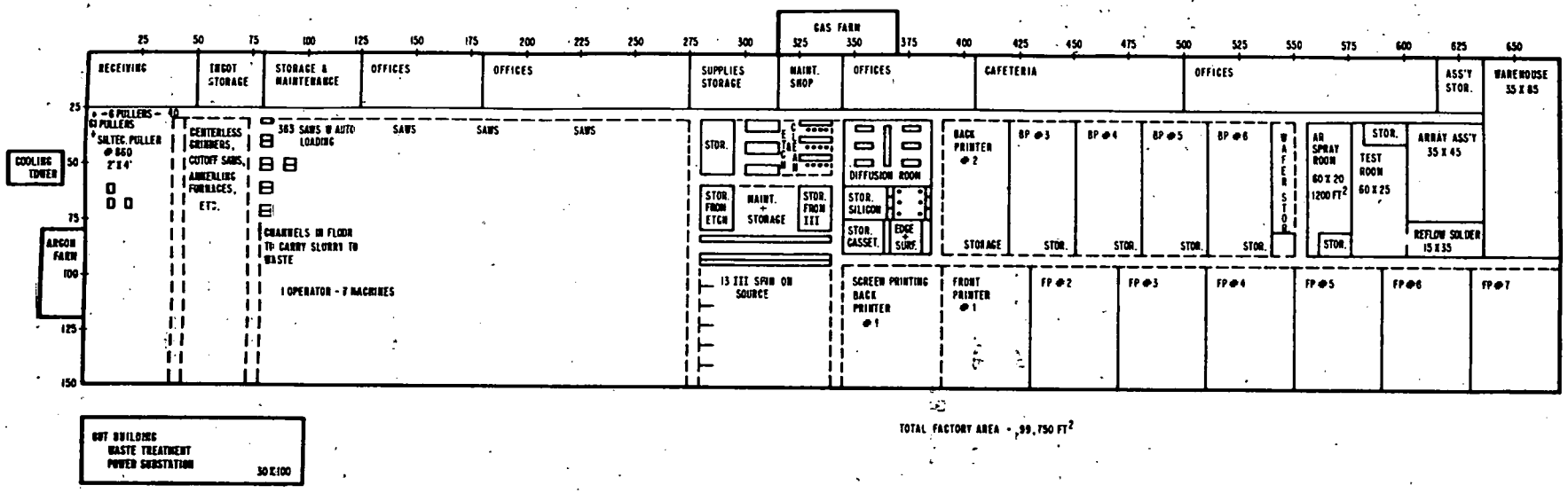

Figure 56. Factory layout.

TABLE 7. FACTORY EQUIPMENT LIST

INVESTMENT SUMMARY

INVESTMENT	UNITS	$TOTAL	$/WATT	$DEPR.	$/WATT	$INTEREST	$/WATT	FT**2
ALUMINUM BLOCK	363.	2904.	0.000	415.	0.000	261.	0.000	0.
ANNEALING FURNACE	16.	72000.	0.002	10286.	0.000	6480.	0.000	0.
ARGON GAS INSTALLATION	13.	195000.	0.006	27857.	0.001	17550.	0.001	0.
BELT->CASSETTE STACKER	16.	240000.	0.008	34286.	0.001	21600.	0.001	0.
CASSETTE STACKER	4.	60000.	0.002	8571.	0.000	5400.	0.000	0.
CENTER GRINDER	7.	126000.	0.004	18000.	0.001	11340.	0.000	0.
CENTERLESS GRINDER	7.	168000.	0.006	24000.	0.001	15120.	0.001	0.
CLAM-SHELL UNLOADER	4.	12000.	0.000	1714.	0.000	1080.	0.000	0.
CRYSTAL MOUNTING BLOCK	363.	30855.	0.001	30855.	0.001	2777.	0.000	0.
CRYSTAL PULLER SPARE PARTS	61.	350750.	0.012	0.	0.0	31567.	0.001	0.
CUTOFF SAW	16.	38400.	0.001	5486.	0.000	3456.	0.000	0.
DISHING GAUGE	52.	7800.	0.000	1114.	0.000	702.	0.000	0.
FINAL ASSEMBLY EQUIPMENT(B)	1.	27500.	0.001	3929.	0.000	2475.	0.000	275.
FRAME ASSEMBLY EQUIPMENT	1.	75200.	0.003	10743.	0.000	6768.	0.000	225.
GRAPHITE PLUG	363.	726.	0.000	104.	0.000	65.	0.000	0.
GRAPHITE STICK CRYSTAL MOUNT	363.	130680.	0.004	18669.	0.001	11761.	0.000	0.
HEADWAY CONTOUR GRINDER	3.	162000.	0.005	23143.	0.001	14580.	0.000	180.
III MODEL 3 SPINNER-3 TRACKS	36.	1440000.	0.048	205714.	0.007	129600.	0.004	2160.
III MODEL 3 OVEN-3 TRACKS IN	36.	720000.	0.024	102857.	0.003	64800.	0.002	2160.
LIFETIME TEST SET	7.	35000.	0.001	5000.	0.000	3150.	0.000	0.
MECHANICAL STACKER	1.	15000.	0.000	2143.	0.000	1350.	0.000	0.
MISCELLANEOUS CP	7.	126000.	0.004	18000.	0.001	11340.	0.000	0.
NIKON COMPARATOR	7.	45500.	0.002	6500.	0.000	4095.	0.000	0.
OPTICAL SCANNER-EXCELLON	16.	240000.	0.008	34286.	0.001	21600.	0.001	256.
OPTICAL SCANNER-EXCELLON R&D	1.	35000.	0.001	5000.	0.000	3150.	0.000	0.
OXIDE STRIP STATION(B)	2.	160000.	0.005	22857.	0.001	14400.	0.000	192.
PACKAGING EQUIPMENT	1.	25000.	0.001	3571.	0.000	2250.	0.000	100.
GLASS/PVB/PANEL ASM. STATION	1.	582000.	0.019	83143.	0.003	52380.	0.002	900.
PANEL INTERCONNECT STATION	2.	360000.	0.012	51429.	0.002	32400.	0.001	240.
POCL3 DIFFUSION FURNACE(B)	4.	266400.	0.009	38057.	0.001	23976.	0.001	1100.
POCL3 FURNACE LINERS(B)	4.	22400.	0.001	5600.	0.000	2016.	0.000	0.
POCL3 FURNACE COILS(B)	4.	32000.	0.001	8000.	0.000	2880.	0.000	0.
POCL3 FURNACE PADDLES(B)	4.	32000.	0.001	4571.	0.000	2880.	0.000	0.
POLYSILICON INVENTORY(B)	61.	1021750.	0.034	0.	0.0	91957.	0.003	0.
POT REFILLER	61.	305000.	0.010	43571.	0.001	27450.	0.001	0.
REICHERT MICROSCOPE	7.	63000.	0.002	9000.	0.000	5670.	0.000	0.
ROTARY INDEX TABLE SYSTEM	5.	137500.	0.005	19643.	0.001	12375.	0.000	120.
RS STRING INTERCONNECT EQUIP	3.	357000.	0.012	51000.	0.002	32130.	0.001	108.
SCREEN PRINT & DRY SYSTEM	6.	532800.	0.018	76114.	0.003	47952.	0.002	4800.
SCREEN PRINT & FIRE SYSTEM	10.	1388000.	0.046	198286.	0.007	124920.	0.004	16000.
SILTEC CRYSTAL PULLER-860	61.	4880000.	0.163	697143.	0.023	439200.	0.015	27450.
SILTEC WAFER SORTER-PROBE	6.	900000.	0.030	128571.	0.004	81000.	0.003	1200.
SILTEC WAFER SORTER-W.E.T.	7.	1225000.	0.041	175000.	0.006	110250.	0.004	1400.
ULTRASONIC WAFER CLEANER	1.	60000.	0.002	8571.	0.000	5400.	0.000	64.
VARIAN MULTIBLADE SAW	363.	7260000.	0.242	1037143.	0.035	653400.	0.022	21780.
WAFER ETCHING STATION(B)	2.	90000.	0.003	12857.	0.000	8100.	0.000	400.
WATER RE-CIRCULATOR	11.	132000.	0.004	18857.	0.001	11880.	0.000	0.

TABLE 8. FACTORY OVERHEAD DETAILS

INVESTMENT	Ft^2	$	$/W
PLANT:			
Process	72,800	7.28M	0.242
Offices	9,400	0.56M	0.018
Cafeteria	2,300	0.14M	0.005
Array Storage	4,000	0.24M	0.008
Wafer Storage	3,300	0.2M	0.007
Ingot Storage	800	0.05M	0.002
Chem. Storage	3,000	0.18M	0.006
Maint Shops	2,000	0.12M	0.004
Receiving	2,300	0.14M	0.005
Total Plant	99,900	8.91M	0.297
LAND	160,000	0.04M	0.001
Parking & Receiving	60,000	0.06M	0.002
Office Equipment		0.02M	0.001
Purchased Material for Inspection and Quality Control		0.5M	0.017
Minicomputers for Payroll and MIS	(2)	0.25M	0.008
Cassettes	(2100)	0.21M	0.007
SUPPORT PERSONNEL	**Number**	**$/Year**	**$/W**
PLANT ADMINISTRATION			
Factory Mgr	1	50K	0.002
Asst Mgr	1	40K	0.001
Secretaries	1	10K	0.000
Receptionist	1	10K	0.000
Industrial Relations	1	18K	0.000
Secretaries	1	10K	0.000
Financial Services	2	60K	0.002
Secretaries	1	10K	0.000
Accounting Services	2	45K	0.002
Secretaries/Clerks	4	40K	0.001
Computer Service	2	40K	0.001
Computer Operators	1/shift	48K	0.002
Purchasing	2	45K	0.002
Secretaries	1	10K	0.000
FACILITIES			
Guards	3/shift	144K	0.005
Maintenance	3/shift	200K	0.007
Janitors	3/shift	100K	0.003
Warehouse	1	25K	0.001
Material Handlers	3/shift	144K	0.005
Dispensary	1/shift	60K	0.002
Industrial Engineering	10	250K	0.008
Quality Control & Purchased Material Inspection	5/shift	360K	0.012
Support People (Total)	107	1719K	0.057

TABLE 9. FACTORY OVERHEAD SUMMARY

Item	Quantity	Cost ($)	Annual Cost ($)	$/W
Support Personnel	107	1719K	1719K	0.057
Cassette (4-yr life)	2100	210K	52.5K	0.002
Heating, Lighting, and AC			188K	0.006
Insurance			115K	0.004
Local Taxes			230K	0.008
Factory Depreciation (20-yr life)		8970K	448K	0.015
Factory Interest (9%)		9010K	811K	0.027
Support Equipment Depreciation (7-yr life)		770K	110K	0.003
Support Equipment Interest (9%)		770K	69K	0.002
Receivables (30 days) (9%)		5000K	450K	0.015
Payables (30 days) (9%)		(1750K)	(158K)	(0.005)
			Total	0.134

$2.01/W, which points out the need for the full development of these techniques by 1982. But even in this case, the cost of wafer preparation comprises 2/3 of the total panel cost, so that additional cost reductions will have great impact on achieving the $2/W goal by 1982.

An optimistic view can be taken for the costs of the remaining process sequences of junction formation, metallization, AR coating, and panel assembly as their costs remain within acceptable limits after repeated analysis and some redesign of the panel.

SECTION IV

EXPERIMENTAL PRODUCTION STUDY OF SILICON SOLAR CELL ARRAY MODULES

A. INTRODUCTION

As reported in Section II, conceptual studies were made of manufacturing process sequences for the large-scale production silicon solar array modules which could be sold for $0.50/peak W in 1986. As a result of that study, the major elements of the most cost-effective manufacturing sequence were identified and described in detail. Those results are summarized in Figs. 57, 58, and 59 for three such sequences which differ only in the junction-formation process. The purpose of the work conducted over a 6-month period and reported here was to evaluate the sensitivity of these processes to changes in the primary variables and to identify the critical variables relating to cost and performance.

The work consisted of three phases: a experimental production study; screen-printed metallization development; and panel design and assembly. The purpose of the experimental production is to produce a statistically significant quantity of solar cells in order to assess the process parameters which affect cell performance. Subsection B of this report describes the results of operating that experimental line for the three junction-formation processes of Figs. 57, 58, and 59. Screen printing of the contact patterns onto the solar cells is an essential element of the low-cost manufacturing; however, it is not now a highly reproducible process. Subsection C describes the development conducted in assessing Ag and Al inks and experimental results obtained in screen printing these inks on test structures and solar cells. Subsection D discusses a double-glass panel designed to meet presently expected electrical and environmental conditions. Preliminary results of a lamination technique used to construct such a panel are also described.

B. EXPERIMENTAL PRODUCTION STUDY

1. Basic Processes and Equipment

The three manufacturing sequences of Figs. 57, 58, and 59 were simulated in an experimental production line located at the RCA Solid State Division,

COST ANALYSIS:CASE II:SPIN-ON +POCL3 DIFFUSION(B) 02/03/77 13:09:18 PAGE 1

PROCESS COST OVERVIEW-$/WATT

ASSUMPTIONS: 0.717 WATTS PER SOLAR CELL AND $ 0.0 FOR 7.6 CM (3") DIAMETER WAFER

STEP	YIELD	PROCESS		MAT'L.	D. L.	EXP.	P. OH.	INT.	DEPR.	SUBTOT	SALVG.	TOTALS	%	INVEST	%
1	99.0%	SYSTEM "Z" WAFER CLEANING	(B)	0.0	0.002	0.002	0.000	0.000	0.000	0.005	0.0	0.005	1.3	0.003	1.0
2	95.0%	SPIN-ON SOURCE:1 SIDE	(B)	0.007	0.010	0.000	0.005	0.002	0.003	0.026	0.0	0.026	6.9	0.018	6.5
3	99.0%	POCL3 DEPOSITION AND DIFFUSION	(A)	0.0	0.017	0.028	0.021	0.003	0.004	0.073	0.0	0.073	19.3	0.031	11.6
4	95.0%	EDGE POLISH	(B)	0.0	0.002	0.004	0.001	0.000	0.001	0.008	0.0	0.008	2.0	0.005	2.0
5	99.0%	GLASS REMOVAL	(B)	0.0	0.002	0.001	0.001	0.000	0.001	0.005	0.0	0.005	1.3	0.005	1.8
6	99.0%	POST DIFFUSION INSPECTION	(B)	0.0	0.003	0.000	0.003	0.003	0.004	0.013	0.0	0.013	3.6	0.030	11.1
7	98.0%	THICK AG METAL-FRONT:AUTO	(B)	0.025	0.009	0.011	0.012	0.006	0.009	0.071	0.0	0.071	18.7	0.062	23.1
8	98.0%	THICK AG METAL-BACK:AUTO	(B)	0.024	0.004	0.005	0.005	0.003	0.004	0.044	0.0	0.044	11.6	0.031	11.5
9	99.0%	AR COATING:SPRAY-ON	(B)	0.002	0.004	0.002	0.001	0.001	0.001	0.011	0.0	0.011	2.8	0.008	3.1
10	80.0%	TEST	(B)	0.0	0.004	0.000	0.003	0.004	0.006	0.018	0.0	0.018	4.7	0.042	15.6
11	98.0%	INTERCONNECT:GAP WELDING	(B)	0.002	0.006	0.002	0.002	0.002	0.003	0.016	0.0	0.016	4.3	0.019	7.2
12	100.0%	DOUBLE GLASS PANEL ASSEMBLY	(B)	0.072	0.002	0.002	0.001	0.001	0.002	0.080	0.0	0.080	21.1	0.014	5.1
13	100.0%	ARRAY MODULE PACKAGING	(A)	0.007	0.001	0.0	0.000	0.000	0.000	0.009	0.0	0.009	2.4	0.000	0.2
	64.6%	TOTALS		0.138	0.066	0.057	0.054	0.024	0.038	0.378	0.0	0.378	100.0	0.269	100.0
			%	36.47	17.46	15.11	14.37	6.41	10.18	100.00					

NOTE: (A)=EXISTING TECHNOLOGY; (B)=NEAR FUTURE; (C)=FUTURE ANNUAL PRODUCTION: 50.0 MEGAWATTS.

Figure 57. Cost summary - spin-on + $POCl_3$ diffusion

COST ANALYSIS:CASE III:SPIN-ON 2 SIDES(B) 02/03/77 13:09:18 PAGE 1

PROCESS COST OVERVIEW-$/WATT

ASSUMPTIONS: 0.717 WATTS PER SOLAR CELL AND $ 0.0 FOR 7.8 CM (3") DIAMETER WAFER

STEP	YIELD	PROCESS		MAT'L.	D. L.	EXP.	P. OH.	INT.	DEPR.	SUBTOT	SALVG.	TOTALS	%	INVEST	%
1	99.0%	SYSTEM "2" WAFER CLEANING	(B)	0.0	0.002	0.002	0.000	0.000	0.000	0.005	0.0	0.005	1.3	0.003	1.0
2	95.0%	SPIN-ON SOURCE:2 SIDES	(B)	0.014	0.030	0.001	0.012	0.004	0.007	0.068	0.0	0.068	18.6	0.046	16.4
3	98.0%	DIFFUSION	(B)	0.0	0.009	0.002	0.002	0.001	0.003	0.016	0.0	0.016	4.5	0.012	4.3
4	95.0%	EDGE POLISH	(B)	0.0	0.002	0.004	0.001	0.000	0.001	0.008	0.0	0.008	2.1	0.005	1.9
5	99.0%	GLASS REMOVAL	(B)	0.0	0.002	0.001	0.001	0.000	0.001	0.005	0.0	0.005	1.3	0.005	1.7
6	99.0%	POST DIFFUSION INSPECTION	(B)	0.0	0.003	0.000	0.003	0.003	0.004	0.013	0.0	0.013	3.7	0.030	10.8
7	98.0%	THICK AG METAL-BACK:AUTO	(B)	0.024	0.004	0.005	0.005	0.003	0.004	0.045	0.0	0.045	12.3	0.031	11.2
8	98.0%	THICK AG METAL-FRONT:AUTO	(B)	0.024	0.009	0.011	0.012	0.006	0.009	0.070	0.0	0.070	19.4	0.062	22.4
9	99.0%	AR COATING:SPRAY-ON	(B)	0.002	0.004	0.002	0.001	0.001	0.001	0.011	0.0	0.011	3.0	0.008	3.0
10	80.0%	TEST	(B)	0.0	0.004	0.000	0.003	0.004	0.006	0.018	0.0	0.018	4.8	0.042	15.1
11	98.0%	INTERCONNECT:GAP WELDING	(B)	0.002	0.006	0.002	0.002	0.002	0.003	0.016	0.0	0.016	4.5	0.019	7.0
12	100.0%	DOUBLE GLASS PANEL ASSEMBLY	(B)	0.072	0.002	0.002	0.001	0.001	0.002	0.080	0.0	0.080	22.0	0.014	4.9
13	100.0%	ARRAY MODULE PACKAGING	(A)	0.007	0.001	0.0	0.000	0.000	0.000	0.009	0.0	0.009	2.5	0.000	0.2
	64.0%	TOTALS		0.145	0.078	0.031	0.043	0.025	0.041	0.363	0.0	0.363	100.0	0.278	100.0
			%	39.87	21.52	8.63	11.87	6.89	11.22	100.00					

NOTE: (A)=EXISTING TECHNOLOGY; (B)=NEAR FUTURE; (C)=FUTURE ANNUAL PRODUCTION: 50.0 MEGAWATTS.

Figure 58. Cost summary - spin-on 2 sides.

COST ANALYSIS:CASE I:ION IMPLANTATION(B) 02/03/77 13:09:18 PAGE 1

PROCESS COST OVERVIEW-$/WATT

ASSUMPTIONS: 0.717 WATTS PER SOLAR CELL AND $ 0.0 FOR 7.6 CM (3") DIAMETER WAFER

STEP	YIELD	PROCESS		MAT'L.	D. L.	EXP.	P. OH.	INT.	DEPR.	SUBTOT	SALVG.	TOTALS	%	INVEST	%
1	99.0%	SYSTEM "Z" WAFER CLEANING	(B)	0.0	0.001	0.001	0.000	0.000	0.000	0.003	0.0	0.003	1.0	0.002	0.5
2	98.0%	ION IMPLANTATION:2 SIDES	(B)	0.0	0.010	0.010	0.009	0.013	0.020	0.061	0.0	0.061	17.9	0.140	38.8
3	98.0%	DIFFUSION	(B)	0.0	0.009	0.002	0.002	0.001	0.003	0.016	0.0	0.016	4.8	0.012	3.3
4	99.0%	POST DIFFUSION INSPECTION	(B)	0.0	0.003	0.000	0.003	0.003	0.004	0.013	0.0	0.013	3.9	0.030	8.3
5	98.0%	THICK AG METAL-BACK:AUTO	(B)	0.024	0.004	0.005	0.005	0.003	0.004	0.045	0.0	0.045	13.0	0.031	8.6
6	98.0%	THICK AG METAL-FRONT:AUTO	(B)	0.024	0.009	0.011	0.012	0.006	0.009	0.070	0.0	0.070	20.5	0.062	17.2
7	99.0%	AR COATING:SPRAY-ON	(B)	0.002	0.004	0.002	0.001	0.001	0.001	0.011	0.0	0.011	3.1	0.008	2.3
8	80.0%	TEST	(B)	0.0	0.004	0.000	0.003	0.004	0.006	0.018	0.0	0.018	5.1	0.042	11.6
9	98.0%	INTERCONNECT:GAP WELDING	(B)	0.002	0.006	0.002	0.002	0.002	0.003	0.016	0.0	0.016	4.7	0.019	5.4
10	100.0%	DOUBLE GLASS PANEL ASSEMBLY	(B)	0.072	0.002	0.002	0.001	0.001	0.002	0.080	0.0	0.080	23.3	0.014	3.8
11	100.0%	ARRAY MODULE PACKAGING	(A)	0.007	0.001	0.0	0.000	0.000	0.000	0.009	0.0	0.009	2.6	0.000	0.1
	70.2%	TOTALS		0.131	0.053	0.035	0.038	0.032	0.053	0.343	0.0	0.343	100.0	0.361	100.0
			%	33.21	15.54	10.31	11.09	9.48	15.36	100.00					

NOTE: (A)=EXISTING TECHNOLOGY; (B)=NEAR FUTURE; (C)=FUTURE ANNUAL PRODUCTION: 50.0 MEGAWATTS.

Figure 59. Cost summary - ion implantation.

Somerville, NJ. A process flow chart showing the sequence of steps used in the fabrication of 3-in.-diameter solar cells is given in Fig. 60. The basic processes and equipment are described below.

a. Silicon Wafers - The solar cell substrates used in this project are obtained from RCA, Mountaintop, PA, and from Siltec Corp., Menlo Park, CA. The solar cell substrates are 3-in., p-type silicon wafers with <100> crystal orientation. Those wafers prepared by RCA Mountaintop from a boule purchased from Monsanto are front-surface polished and have a saw/etched back surface. Wafer thickness is 0.020 in., nominal, and the bulk resistivity ranges from 5 to 10 ohm-cm. The wafers supplied by Siltec Corp. are front-surface polished and back-surface etched. Wafer thickness is 0.015 in., nominal; bulk resistivity ranges from 1 to 2 ohm-cm.

b. Process Descriptions

(1) Junction Formation - Three methods were tested: ion-implantation of phosphorus and arsenic, a spin-on phosphorus source, and gaseous diffusion from phosphorus oxychloride. In all cases the back contact is made through a high-concentration boron diffusion.

Ion Implantation - The Somerville Extrion 200-1000 implant machine uses a gaseous source of phosphine or arsine for the n-type implant and boron trichloride for the p-type implant. The machine is capable of delivering up. to 3-mA beam current in the range of 5 to 200 keV.

The implanter can accommodate 26 3-in.-diameter wafers at a time. Junction implant times are on the order of 10 minutes depending on species and experimental requirements. Holders have been designed which are capable of masking the surface peripherally so that a planar structure results which does not require further etching to define the junction.

Typical doses were 1×10^{15} phosphorus and 1.5×10^{15} arsenic atoms per cm^2. Boron was implanted into the back of the wafers at a dose of $\sim 1 \times 10^{15}$ atoms per cm^2 and simultaneously driven-in in the junction anneal step.

Spin-on Diffusion Source - A Headway* EC 100 spinner is used to apply spin-on diffusion source, dispensed from a hypodermic syringe. A variety of proprietary solutions made by Emulsitone Co., Whippany, NJ, has been used to

*Headway, Corp, Garland, TX.

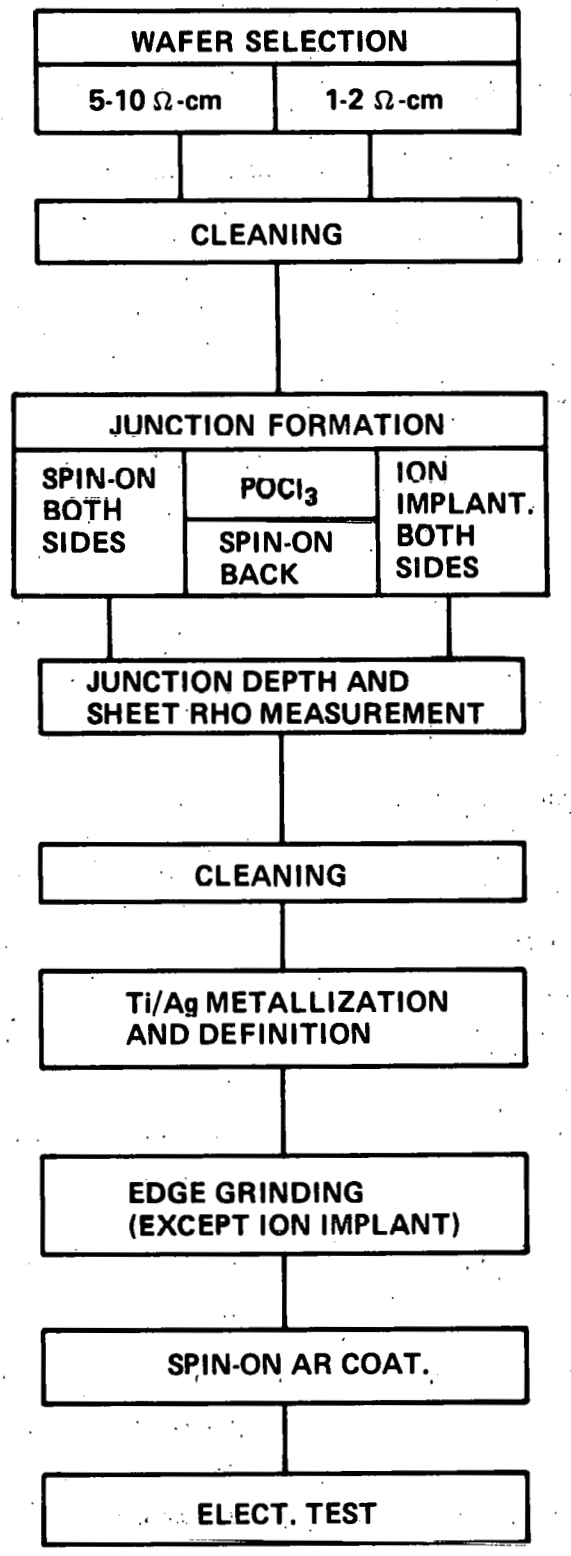

Figure 60. Experimental production process flow chart.

obtain phosphorus and boron films. Care is taken to ensure proper ventilation and safety precautions in handling the toxic solutions.

Phosphorus Oxychloride Deposition and Diffusion - A Thermco* SPARTAN furnace is used, fitted with flowmeters, bubbler, and exhaust. Deposition and diffusion occur simultaneously. A typical cycle is 10 minutes preheat in nitrogen to reach thermal equilibrium, 45 minutes at temperature with oxychloride flowing, 10 minutes in nitrogen-10% oxygen while the wafers are slowly withdrawn at about 50 mm per minute by a programmed puller.

All furnaces are monitored weekly, and the data are recorded together with information on any adjustments. The absolute calibration is maintained by the in-house standards department, which carries out periodic checks on all instruments and refers these to National Bureau of Standards traceable standards.

(2) Cleaning, Etching, and Photolithography - These operations are performed in laminar flow stations using procedures which are standardized for semiconductor device fabrication. All reagents are "Electronic Grade"; the rinse water is deionized, filtered, and monitored to ensure that its resistivity is over 18 Mohm-cm.

Wafers are "Standard Cleaned" first in SC-1, a 1:1:5 mixture of ammonia, hydrogen peroxide, and water, then in hydrofluoric acid, and finally in SC-2 which is hydrochloric acid, hydrogen peroxide, and water again in a 1:1:5 mixture at 85 to 95°C for over 15 minutes. This cleaning technique is specially designed to remove films that inhibit wetting, and to remove the thin native oxide; finally, SC-2 removes virtually all metallic contaminants that may reduce the carrier lifetime in the finished device. For preimplant cleaning, an equally good alternative method has been used, based on a mixture of equal volumes of sulphuric acid and hydrogen peroxide at over 80°C. A standard photolithographic technique is used, based on Shipley A21350J, to produce the fine-line metal patterns used in the experimental stage. Wafers are stored and transported in fluorocarbon carriers with dust-tight lids and transferred to quartz boats wherever required. Oxides and glasses such as the spin-on dopant source are removed by etching in hydrofluoric acid, followed by rinsing in deionized water and drying.

*Thermco Instrument Co., Laporte, IN.

(3) Edge Contouring - When a spin-on source or phosphorus oxychloride is used to produce the junction, and in the case of ion implants when the edge mask wafer holder is not used, it is necessary to either lap, grind, or etch the junction on the wafer periphery to separate the heavily doped n- and p-type regions from each other. This can be done conveniently by either an edge or contour grinder or by lapping the edge with a slurry of garnet* in water and then cleaning.

(4) Metallization - During the initial phase of this work while the details of screen-printing metallization are being investigated, the metal pattern is either evaporated through a metal mask or photolithographically defined.

The pattern is shown in Fig. 61. The back contact metal is not patterned. The metal is evaporated in a Veeco 775 equipped with an Airco-Temescal electron gun and planetary mechanism that permits uniform evaporation of 21 wafers at a

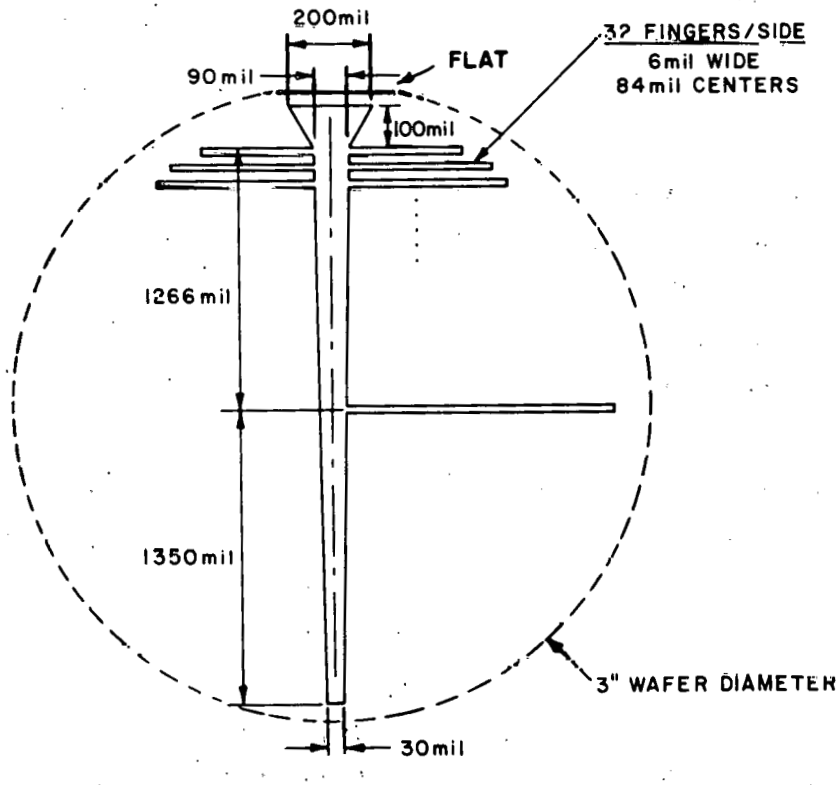

Figure 61. Metallization pattern

*The garnet used was Corundum #1600 (9.5 μm), Bendix Abrasives Div., Westfield, MA.

time. The usual metallization is 0.2 μm of titanium followed by 3 μm of silver, and it is monitored by an Airco-Temescal XMS-3 thickness gage. A fraction of cells will continue to be metallized in this fashion for control purposes.

(5) Antireflection (AR) Coating - Emulsion titaniumsilica film* is applied using a Headway spinner to obtain a layer of about 70 to 80 nm. This is baked at an average temperature of 450°C in a Watkins-Johnson variable-speed belt furnace having six-heat-zone controls, in air. The wafers pass through the hot zone, which peaks at 500°C, in 10 minutes. The metallization is sintered at the same time.

2. Documentation and Measurements

a. Process Measurements and Travelog - Incoming wafers are inspected and measured at the receiving station and the data entered into the record (Fig. 62) together with the ordering details, vendor, lot numbers, and receiving dates. When wafers are drawn from the inventory, they are marked with the solar cell lot number by diamond scribing in small figures near the reference flat, and an entry is made into the solar cell travelog (Fig. 63). A process lot number is assigned and subsequent measurements and observations are entered onto the travelog. A copy of the shipped cell travelog is then filed. Individual measurements on each wafer are recorded at the various checkpoints on log sheets like those shown in Figs. 64 and 65. New experimental runs or changes in scheduling are recorded on the form shown in Fig. 66.

(1) Resistivity and Sheet Resistance - A collinear Fells probe head in conjunction with a Keithley** "Type-All" instrument is used for both measurements. Bulk resistivity is measured with tungsten carbide, 40-μm radius probe tips, loaded with 50 g, while the sheet resistance of the very thin junction layers is measured with "blunt" probe tips having 100-μm radius, loaded with 40 g. The procedures outlined in ASTM F-84-73 and FF 374-74 are followed. Uniformity is checked by reading the sheet resistance in five places on each selected wafer.

*Titaniumsilica film Type-C, purchased from Emulsitone Co., Whippany, N.J.
**Keithley Instruments, Cleveland, OH.

Solar Cells – Incoming Inspection

Vendor | Vendor Lot # | Rec. Rep. #

SC Lot # | SC/Vendor Type | Item

Quan. Recv'd | Sample Size | Inspector | Date

Instructions:

Criteria	Item 1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	Total Defects	Total Items Rej.
Cracks																								
Scratches																								
Chip outs																								
Dimples/Pimples																								

Figure 62. Incoming wafer inspection sheet.

Solar Cell Travelog

SC Lot No. | Quan. | Process Lot No.

Process Description		Material	Operator	Date	Gross	Net	Special Instructions
Incoming Inspection							
Serialization							
SCC # 1 Bulk P Mass							
Clean		Code Z					
Dope							
	Spin-On						
	Gaseous						
Clean							
Drive		T (°C)					Push t (min)
		N_2 (CFH)					Zone t (min)
		O_2 (CFH)					Pull t (min)
SCC #2	Sheet ρ						
	Junc. Depth						
Clean							
Metal	E Gun						
	Screen On						
	Filament						
Clean							
AR Coating							
Electrical Test							
Ship							

Figure 63. Solar cell travelog.

Solar Cells

Bulk Resistivity Measurements

SC Lot = Date Oper. Process Lot =

		Thickness	Factor	V_{FWD}	V_{RCU}	Factor	Bulk P			
	SN	(mil)	0.00254	(mV)	(mV)	4.53	(ohm-cm)			

Figure 64. Solar cell bulk resistivity measurement chart.

Solar Cells

Sheet Resistivity Measurements

Lot No. Oper. Date Sheet of

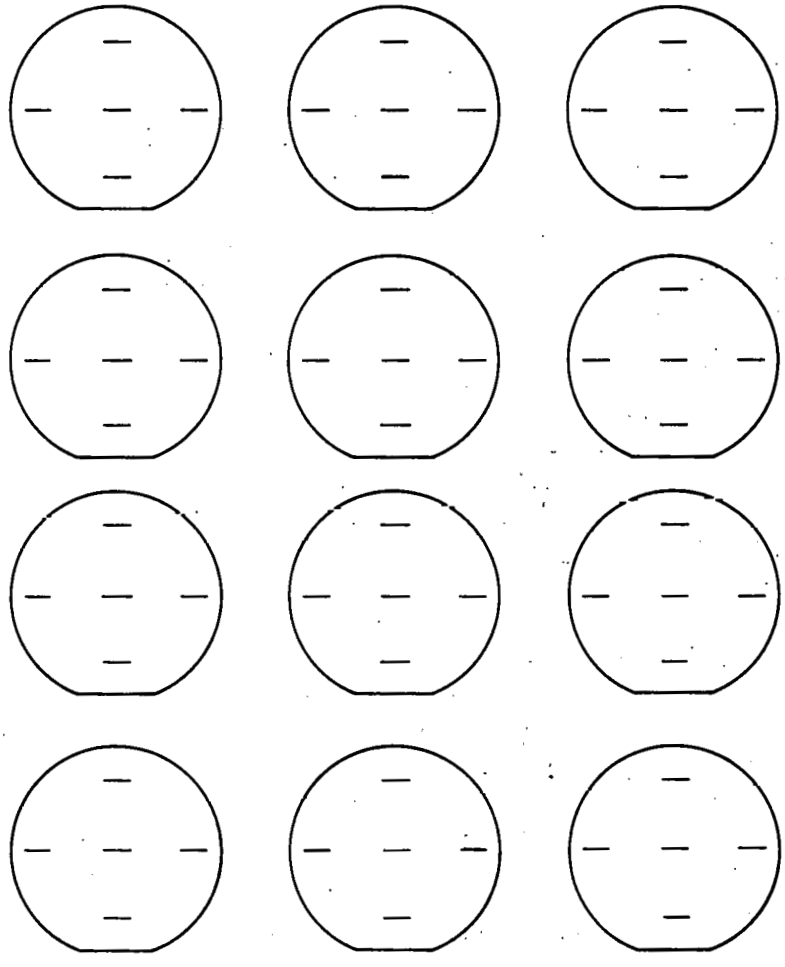

Figure 65. Solar cell sheet resistivity measurement chart.

Date _____

Furnace Number	Temperature Requested	Requested by	Profile Check	Furnace Release	Comments

Figure 66. Chart for recording changes.

(2) Junction Depth - To obtain a junction depth measurement a Philtec Instrument Co.* 2015 D groover is used, followed by staining the p-n junction with the silver stain described in ASTM F 110-72, reagent 6.6. Since this is a destructive measurement, only one wafer per lot of 25 is checked for junction depth routinely. However, some batches are sampled in more detail to obtain statistical data.

(3) Wafer Thickness - Thickness is measured on each incoming wafer in five places with a Bausch and Lomb** Microline DR Optical Gage 25 B. The instrument is calibrated periodically against National Bureau of Standards thickness gages.

(4) Antireflection Coating and Metallization Thickness - After the antireflection coating is baked, a wafer is coated with an etch mask such as wax or etch-resistant tape in a way that permits a straight edge to be defined. This is done by etching in hydrofluoric acid; then the mask is removed. The step height or metal thickness is determined by a surface profilometer such as a Talysurf made by Engis Equipment Corp.*** A set of wafers with a known AR coating thickness has been collected and is used for visual comparison, as routine process control.

*Philtec Instrument Co., Philadelphia, PA.
**Bausch and Lomb, New York, NY.
***Engis Engineering Corp., Mortongrove, IL.

b. Solar Cell Electrical Tests - All completed cells are electrically characterized by a simulated AM-1 illuminated I-V and power output measurement. This measurement is accomplished using an ELH photoflood lamp and dynamic electronic load. The calibration and measurement procedure followed that specified by NASA-Lewis in their publication NASA TM X-71771.

A set of cells from the extremes of the performance distribution were selected for detailed diagnostic measurements. These measurements included spectral response, junction I-V characterization, and lifetime (diffusion length).

3. Summary and Correlation of Solar Cell Results

a. Comparison of Cell Performance

(1) Junction Formation - A summary of the average AM-1 parameters for solar cells fabricated by the three junction-formation processes is given in Table 10. The data are divided into high and low resistivity categories, with nine lots (25 wafers/lot) run with 7 to 8 ohm-cm (20-mil-thick) wafers and eleven lots run with 1 to 2 ohm-cm (15-mil-thick) wafers. The illuminated solar cell parameters listed are average values for each set of lots.

TABLE 10. SUMMARY OF AM-1 CELL PERFORMANCE FOR THREE JUNCTION-FORMATION PROCESSES

	7 to 8 ohm-cm				1 to 2 ohm-cm			
Junction Formation	$\bar{I}_{sc}$ (A)	$\bar{V}_{oc}$ (V)	$\bar{\eta}$ (%)	No. Lots	$\bar{I}_{sc}$ (A)	$\bar{V}_{oc}$ (V)	$\bar{\eta}$ (%)	No. Lots
Gaseous ($POCl_3$)	1.37	0.560	11.9	3	1.20	0.560	10.2	2
Spin-On (P)	1.25	0.530	10.6	4	0.97	0.52	7.8	3
Ion Implantation (P)	1.20	0.520	9.9	2	1.11	0.535	9.5	2
Ion Implantation (As)	-	-	-	0	1.01	0.500	9.1	4

Some conclusions which can be drawn from these data are:

(a) The gaseous ($POCl_3$) diffusion junction-formation process yielded the best cells overall.

(b) Cells made from 1- to 2-ohm-cm wafers had considerably lower short-circuit current than those made from the 7- to 8-ohm-cm wafers. This conclusion should *not* be taken as a general result since the silicon vendor was different for each of the two resistivity ranges, and examination of the wafers by preferential chemical etching (Wright etch) revealed that the lower resistivity wafers had a considerably higher defect density than the 7- to 8-ohm-cm wafers. This does, however, point out the importance of starting wafer quality in obtaining good solar cell performance.

(c) The ion-implantation process yielded lower values of short-circuit and open-circuit voltage than the other two junction-formation processes. The arsenic-implanted junctions were generally slightly poorer than phosphorus-implanted junctions. Spectral response data and pulsed recovery measurements show that the minority carrier lifetimes for cells with ion-implanted junctions are low ($\sim$1 μs), resulting in diminished quantum efficiency at long wavelengths.

(d) The results for the spin-on phosphorus diffusion are encouraging; however, more work is needed to assure stability of the liquid spin-on source and reproducibility of this process.

(2) Variations in Cell Characteristics and Junction Parameters - In most categories an insufficient number of cells were completed to determine the nature of the statistical distribution of cell efficiencies. However, assessments were made of the spread in cell parameters for each junction-formation technology. The mean and standard deviations in measured cell parameters and sheet resistance of the junction layer for typical sets of cells are given in Table 11.

Although these data include the effects of a "learning curve" associated with the start-up of the experimental line, some preliminary conclusions and observations can be made.

(a) The tightest distribution in cell parameters (except fill factor) was obtained from cells fabricated using $POCl_3$ gaseous diffusion for junction formation.

(b) The deviation ($\sim$16%) in sheet resistance for the spin-on phosphorus source is larger than all others, but does not result in abnormally large variations in cell parameters.

TABLE 11. STATISTICAL VARIATIONS IN CELL PARAMETERS

Junction Formation	AM-1 Cell Parameters								Sheet Resistance	
	$\bar{\eta}$	S^*_{η}	$\bar{I}_{sc}$	S_{isc}	$\overline{FF}$	S_{FF}	$\bar{V}_{oc}$	S_{voc}	$\bar{R}_{\square}$	$S_{\square}$
$POCl_3$	11.86	0.68	1.41	0.028	0.640	0.04	0.560	0.012	50.6	4.2
Spin-On (P)	9.46	0.71	1.26	0.042	0.610	0.03	0.530	0.012	97.9	15.6
Ion Implantation (P)	8.04	1.02	1.09	0.056	0.590	0.04	0.540	0.020	218.1	11.1
Ion Implantation (As)	7.81	1.09	0.938	0.098	0.701	0.02	0.510	0.020	89.4	4.1

*S_i = standard deviation for i th variable.

(c) The large deviations in cell parameters (primarily I_{sc}) for the ion-implanted cells do not correlate with the very small variations in sheet resistance obtained with this process. This is consistent with the earlier observation of low minority carrier lifetime in the base of ion-implanted cells. Low lifetime also relates to the low value (0.510 V) of average open-circuit voltage (V_{oc}) in the case of arsenic-implanted cells.

Another observation not shown by the above data is that low values of fill-factor and V_{oc} were traced in some cases to poor ohmic contacts on the back of the cells. This was especially true for processes using diffusion temperatures less than 900°C, because it was found that very little boron diffuses into the back at these temperatures making it more difficult to form a good low-resistance back contact.

Also of importance is the junction quality as reflected in the I-V characteristics and related shunt-leakage resistance. Typical I-V characteristics for each junction process measured under illuminated conditions are shown in Figs. 67, 68, 69, and 70. In these figures, the junction or diode n-factors, saturation current density (J_o), and shunt resistance (R_{SH}) typical of each process are listed.

Examination of the completed cells revealed that the shunt leakage is due mostly to physical damage on the front surface of the cells incurred in handling the wafers. This problem would be reduced considerably in an automated line where wafers are moved in cassettes or by air tracks.

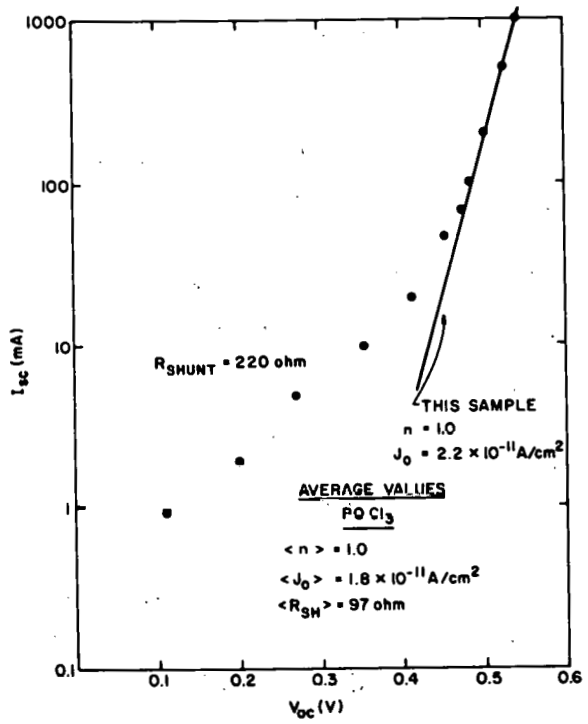

Figure 67. Typical I-V characteristic, $POCl_3$ process.

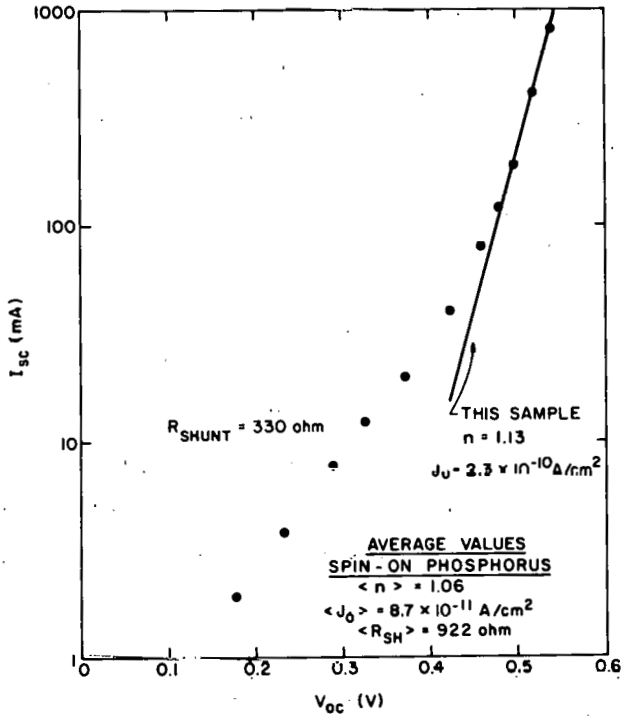

Figure 68. Typical I-V characteristic, spin-on phosphorus.

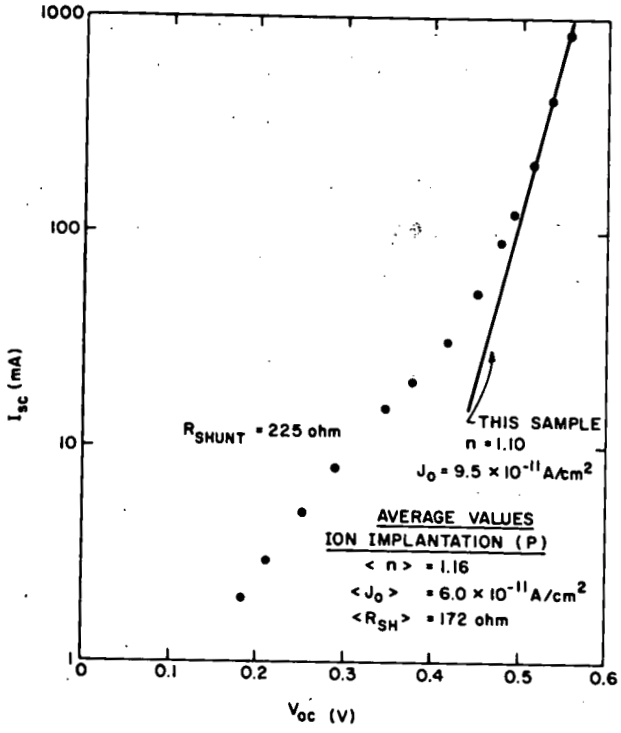

Figure 69. Typical I-V characteristic, ion implantation (P).

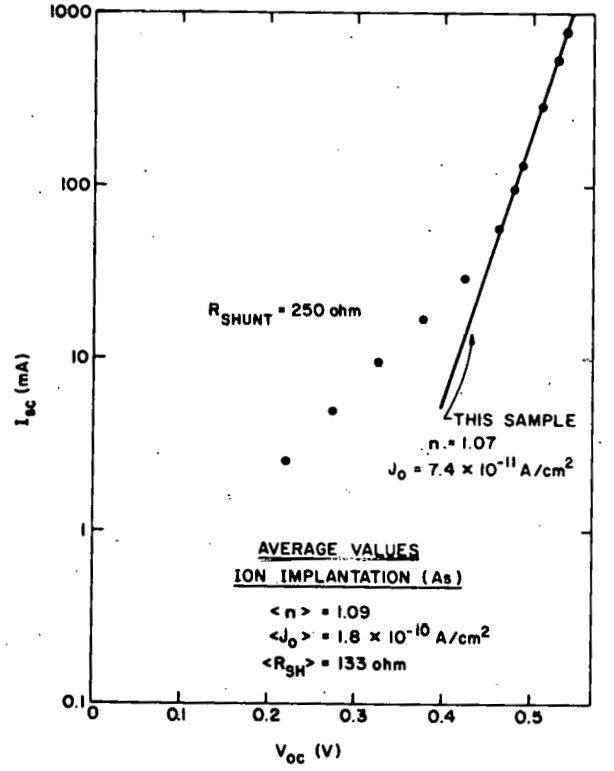

Figure 70. Typical I-V characteristic, ion implantation (As).

(3) Diffusion Temperature - Diffusion temperatures ranging from 800 to 1000°C were used in the junction-formation processes. Examination of the average short-circuit current for lots diffused at different temperatures revealed a general trend toward lower short-circuit current for higher diffusion temperature. Data illustrating this trend are shown in Fig. 71. This result is in agreement with other work in this field indicating that lower diffusion temperatures are preferred for solar cell processing.

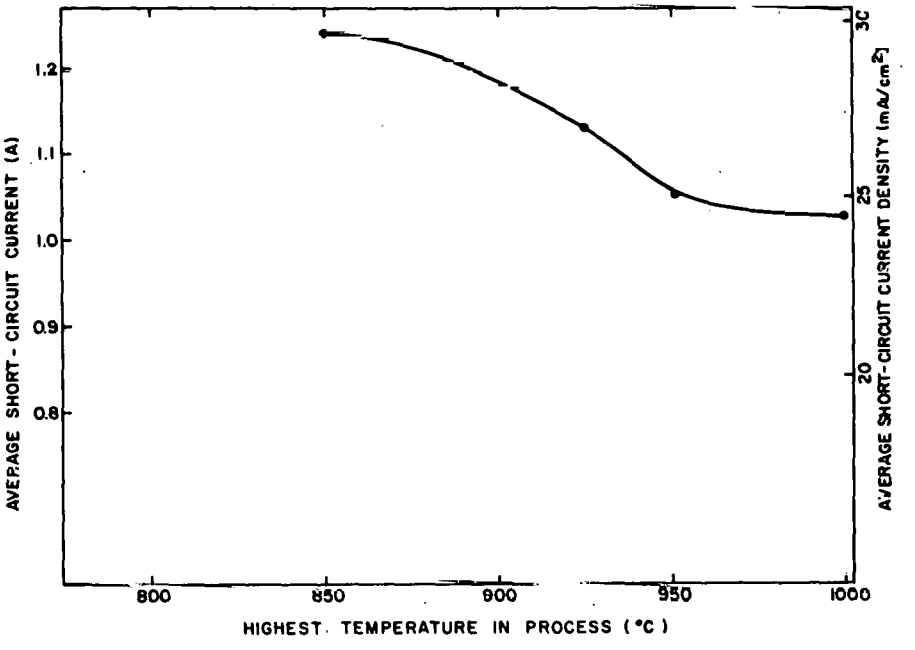

Figure 71. Short-circuit current as a function of temperature.

(4) Performance and Characteristics of Spin-on AR Coatings - The titaniumsilica film, type-C has a reported index of refraction of 1.96. The reflection and absorption properties of this product when applied to a polished silicon wafer in accordance with the procedures outlined in subsection IV.B.1.b above were measured and are shown in Fig. 72. The low reflection and absorption properties combined with the ease of application (non-vacuum process) make this spin-on film technique an attractive candidate for a low-cost antireflection process.

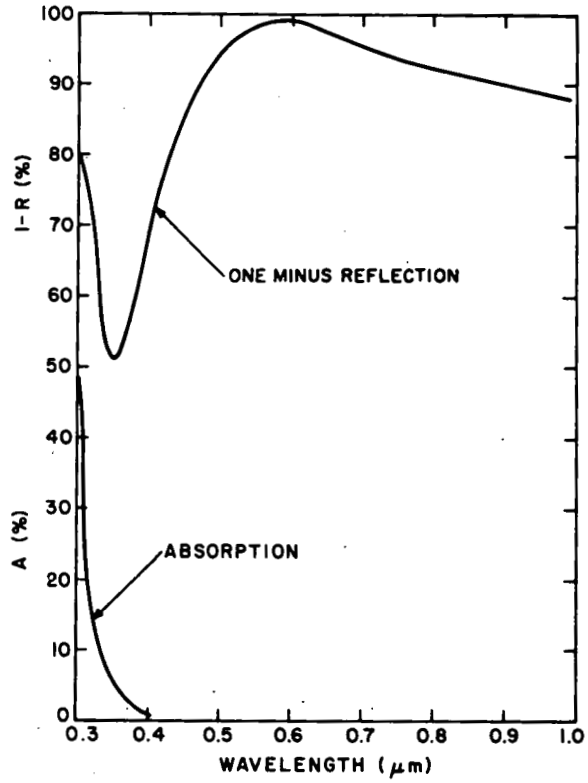

Figure 72. Reflection and absorption properties of spin-on titaniumsilica film as a function of wavelength.

Some of the properties and problems encountered in its use on metallized, 3-in.-diameter solar cells are:

(a) From experience with small (2 by 2 cm) cells, an increase in short-circuit current of 42% is normally achieved when spin-on titanium-silica film is applied to the polished surface. For the 3-in.-diameter cells this factor averaged 36%. This reduction is due mostly to nonuniformities caused by interaction of the spin-on liquid with the metal pattern as discussed below.

(b) Nonuniform film thickness was encountered when this liquid is spun onto cells having metallization thicker than ~4 μm. This becomes extremely severe for thick-film (>10 μm) screen-printed metal.

b. Summary of Yield Analysis - A yield survey was made. The survey included material handling from the incoming inspection station up to final electrical testing. No yield data are included for electrical testing of completed cells

since there were no specificaions on cell performance. Deviations from standard processing requested for engineering purposes are not included. The yield data were collected from 22 lots and spanned approximately 500 solar cells. Every process variation is included in the summary of yield data given in Table 12.

TABLE 12. SUMMARY OF YIELD DATA

Process	Yield %
Wafer Cleaning	98
Spin-On Process	95
$POCl_3$ Diffusion	96
Ion Implantation	95
Junction Depth and Sheet Resistance Test	95 (Junction depth measurement is destructive)
Metallization and Photoresist	90 (Evaporated Ti/Ag only)
Contour Edging	92
Overall Yield (Typical)	67

These process yield figures are for a small (three hourly workers and one foreman) experimental production line. Also, the yield loss in most cases was due to breakage in handling since manual transfers were used throughout. Cassette or air-track automated handling systems should increase these yield figures.

C. SCREEN-PRINTED METALLIZATION

1. Impurity Analysis of Commercial Thick-Film Inks

Four commercial silver-based inks were purchased from two vendors* and analyzed by spark source emission spectrography. The results of that analysis are given in Table 13. The high phosphorus content in the OI-6105 and A-3441

*Engelhard Industries, East Newark, NJ.
Owens-Illinois, Inc., Toledo, OH.

TABLE 13. EMISSION SPECTROGRAPHIC ANALYSIS OF FOUR THICK-FILM SILVER INKS (ppm by wt)

	OWENS ILLINOIS FORMULATIONS		ENGELHARD FORMULATIONS	
Element	OI-6103	OI-6105	A-3233	A-3441
Cu	300-3000	50-500	20-200	10-100
Al	15-150	30-300	100-1000	1000-10,000
Fe	3-30	10-100	10-100	10-100
Mg	1-10	3-30	1-10	50-500
Si	500-5000	60-600	100-1000	600-6000
Pb	2000-20,000	1-10	S*	S
Bg	ND**	ND	1-10	30-300
B	600-6000	ND	S	1000, 10,000
Sb	ND	ND	300-3000	100-1000
Bi	ND	ND	3-30	ND
Ti	ND	ND	3-30	30-300
Zn	ND	ND	300-3000	150-1500
Na	50-500	100-1000	30-3000	30-300
Ni	ND	-	ND	10-100
Mn	ND	0.6-6	ND	1-10
Ga	ND	-	ND	ND
Ag	S	S	S	S
P	ND	1000-10,000	ND	600-6000
Au	10-100	ND	ND	10-100
Pd	3-30	ND	ND	15-150
Ca	ND	ND	ND	3-30
Cr	ND	ND	ND	ND

*S = element concentration is large.
**ND = not detected.

inks arises because of the intentional addition of phosphated grit for a reduction of contact resistance in the case of n-type silicon surfaces, but the high aluminum content in A-3441 is undesirable from this point of view.

2. Specific Contact Resistance

Dot patterns suitable for the determination of contact resistance were screen-printed on 0.01 ohm-cm, bulk n and p silicon, and fired at temperatures ranging from 600 to 700°C. Firing was done in a belt furnace, with furnace profile and belt-feed adjusted so that the wafers are at temperature for 10 minutes.

The specific contact resistivities determined by this method are listed in Table 14. From these data, it appears that (except for A-3233) a firing temperature of greater than 650°C is required to achieve a sufficiently low contact resistance.

Physical (angle polish and stain) examinations were conducted to determine subsurface penetration of silver. No evidence of silver "spiking" was found; however, tests on actual solar cell structures did reveal differences in the amount of junction shunting for the different inks. These results are described below.

3. Screen Printing of Solar Cell Test Patterns

Tests of the four Ag inks described above were conducted by printing the solar cell pattern shown in Fig. 73 on wafers containing a typical junction formed by the $POCl_3$ process.

This test pattern consists of one 2.1- by 2.1-cm cell, two 0.4-cm^2 cells, ten diodes, and structures A and B for measurement of the contact and sheet resistance of the printed metallization.

Solar cell wafers were selected for screen printing from the experimental production line; these wafers had junctions formed by $POCl_3$ gaseous diffusion with sheet resistance of 40 to 50 ohm/square and junction depth of $\sim$0.25 μm. After the wafers were cleaned, the four inks (Owens Illinois OI-6103, OI-6105, Englehard A-3233, and A-3441) were printed onto the junction side of the wafers. The printing was done with an Aremco Accu-Coat Model 3100 screen printer and all inks were printed through a 200-line/in. mesh with the pattern of Fig. 73 defined in the emulsion. The samples were fired in a belt furnace in air at

TABLE 14. SPECIFIC CONTACT RESISTANCE, SCREEN-PRINTED THICK FILMS

Ink	n-type (111)-plane 1.0×10^{19}/cc 0.01 ohm-cm ($ohm\text{-}cm^2$)	p-type (100)-plane 1.1×10^{19}/cc 0.01 ohm-cm ($ohm\text{-}cm^2$)
A-3441		
10m at 700°C	0.08	0.12
650°C	1.64	1.08
600°C	3.54	1.57
A-3233		
10m at 700°C	0.01	0.11
650°C	0.4	0.15
600°C	0.76	0.28
OI-6103		
10m at 700°C	1.21	0.12
650°C	1.0	0.38
600°C	1.95	2.47
OI-6105		
10m at 700°C	0.27	0.44
650°C	2.19	0.39
600°C	5.01	7.20

temperatures ranging from 675 to 725°C for 10 min at peak temperature. Only the front side grid was screen-printed; the back contact was made after firing by evaporated and sintered (500°C) aluminum. The individual devices of Fig. 73 were then defined by mesa etching using wax as a mask. After etching, the area of the large cell is 4.4 cm^2.

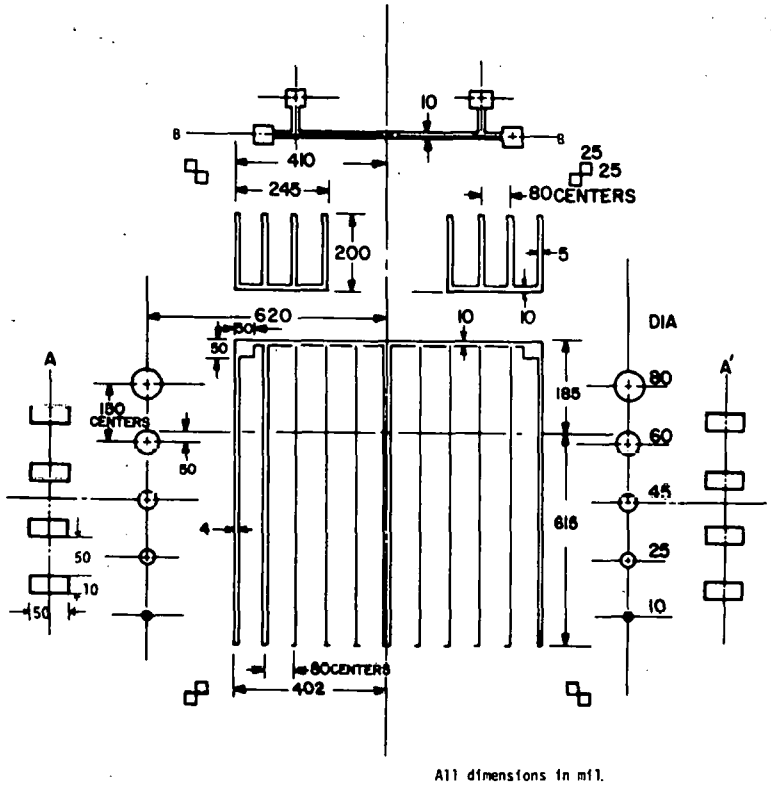

Figure 73. Solar cell mask design including diagnostic cells.

From measurements of solar cell performance and the junction I-V characteristics, the following observations were made concerning the properties of the screen-printed inks:

(1) For all inks, firing temperatures of 700°C or greater caused excessive metal penetration resulting in extensive shorting of the junction.

(2) The best results were obtained at a firing temperature of 675°C, with OI-6105 ink. This ink and firing temperature resulted in low contact resistivity (0.05 to 0.08 ohm-cm^2) and little or no evidence of shunting (see Fig. 74). The major limitation was in printing the 5-mil-wide line over a 2-cm length. The line obtained had a repetitive "hour-glass" shape with some discontinuities in the "necked-down" regions (Fig. 75). Line widths of 10 mil or greater printed well and had a height of ∿20 μm. The measured lateral resistivity of these lines is 4 to 6 μohm-cm. The discontinuities in the 5-mil-wide lines caused excessive series resistance in the 2- by 2-cm cells,

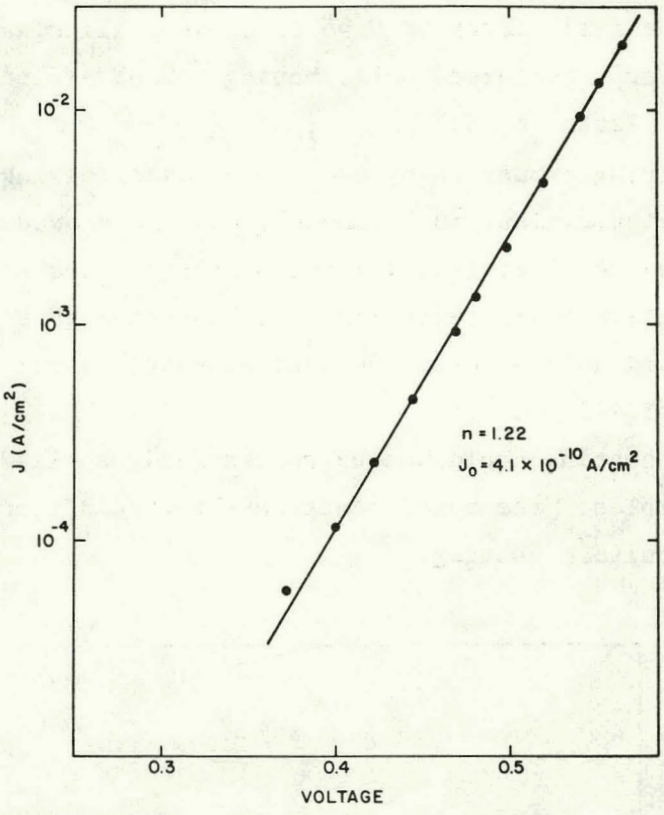

Figure 74. Junction I-V characteristic for solar cell printed with OI-6105 Ag ink and fired at 675°C.

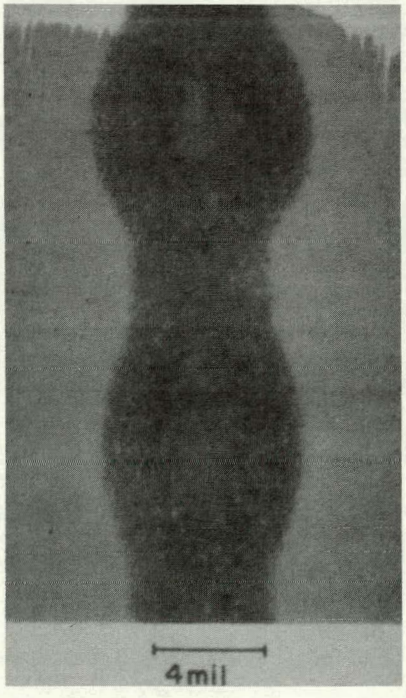

Figure 75. Photomicrograph of 5-mil line printed with OI-6105 ink using 200-line/in. mesh.

limiting the fill factor to 0.45 at one sun illumination. The small cells (0.4 cm^2) performed well, having a 7.8% efficiency (no AR coating) with a fill factor of 0.77.

(3) At 675°C firing temperature, the three remaining ink samples had high contact resistivities, $\gtrsim$0.2 ohm-cm^2, and all showed evidence of junction shunting in the electrical I-V measurements. The effect of shunting on the junction characteristics is illustrated in Fig. 76.

(4) The Englehard inks printed the best geometric 5-mil line width at a thickness of ∿13 μm.

(5) Spin-on AR coating could not be successfully applied to the screen-printed samples. The metal scatters the liquid upon spinning, causing a very nonuniform coating.

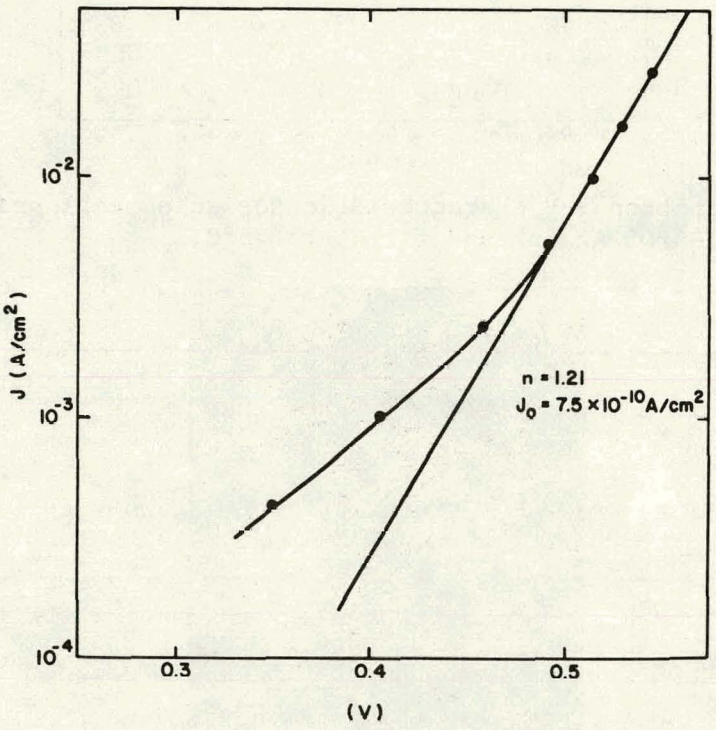

Figure 76. Junction I-V characteristic for solar cell printed with A-3441 Ag ink and fired at 675°C illustrating shunting.

D. PANEL DESIGN AND ASSEMBLY

1. Comparison of Glass Panel Designs Evaluated During Phase II

a. Introduction - RCA is convinced that a glass/cell/glass sandwich construction is required to achieve the JPL life and cost goals. During this period we evaluated, by process analysis and experimental fabrication of panels, several ways to achieve double-glass construction. Basically, there were three classes of designs considered: adhesive bonding between cells, adhesive bonding on cells, and safety glass lamination.

The receipt of the JPL proposed specification 5101-16 "Silicon Solar Cell Module Design, Performance, and Acceptance Test Requirements" had a significant impact on the panel design. The primary effect was due to the provision of a two-edge rather than the previously assumed four-edge support substructure, requiring the incorporation of an aluminum U-channel frame to resist the wind loads. The safety glass lamination technique housed in an alumium frame appears to meet all JPL specifications and is cost effective. A comparison matrix of the various panel techniques evaluated during this phase is shown in Table 15. Photographs of full-size panels containing dummy cells are shown in Figs. 77 and 78.

b. Adhesive Bonding Between Cells - This panel design used 165 3.6-in.-diameter cells in an 11 by 15 array. The space between cells is used to hold a matrix of epoxy dots with spacer discs to form a honeycomb-like structure. To function effectively as a honeycomb structure the two cover sheets should be of equal thickness. Under these conditions the shear stress on the epoxy dots can be determined from the beam equations on the neutral axis. The shear stress at 50-psf loading for two 1/8-in. sheets is 50 psi at the center and 100 psi at the outer edges. Assuming a 5% area coverage for the dots, we have a 2000-psi bond stress. Typical epoxies can provide a bond strength of 3000 psi.

There are several options available on the optical coupling method. The two-surface front glass panel reflection can be reduced from approximately 8 to 3% by an etching process which selectively leaches material out of the glass surface. The porous surface layer created has an effective index less

TABLE 15. PERFORMANCE COMPARISON MATRIX FOR VARIOUS GLASS/CELL/GLASS PANELS EVALUATED DURING PHASE II

Fabrication Technique	Optical Coupling Sequence Prior to Cell Glass Anti-Reflection Etch =AR	Total Optical Coupling Loss (10% Cell) % Power Loss	Change in Thermal Coupling % Power Loss	Effect of Edge Seal Failure on Long-Term Performance	Critical Stress Under 50 psf 10,000 cycles	Substruct Mounting Edges Required	Panel Frame	Panel/Panel Interconnect	Total Encapsulation Materials Cost (Interconnect + Lamination + (Frame) ¢/W	Cell/Circuit Spec	Comment
Adhesive Bonding Between Cells	AR/No AR/Oil AR/AR/Air No AR/No AR /Air	10.0 12.4 17.2	C.5 2.9 2.9	Moisture penetration causes eventual panel failure due to voltage & corrosion	2000 psi Fatigue life poor	4	None	Requires field wiring	8.0	165 3.6-in.-diam cells 11x15 array (33 in series) 15 V @ 20°C cell temp	1. Area for adhesive dots competes with a high packing density. 2. Adhesive dot fatigue life unsatisfactory. 3. Cannot meet LSSA two-edge mounting spec.
Adhesive Bonding on Cells	AR/No AR/Ad No AR/No AR /Air	10.0 14.1	0.5 0.5	Moisture penetration causes eventual panel failure due to voltage & corrosion	500 psi Fatigue life better	4	None	Requires field wiring	8.0	165 3.6-in.-diam cells 11x15 array (33 in series) 15 V @ 20°C cell temp	1. Air bubbles in adhesive cannot be removed. 2. Cannot meet LSSA two-edge mounting spec
Polyvinyl/ Butyral (PVB) Safety Glass Lamination	AR/No AR/PVB No AR/No AR /PVB	10.0 14.1	0.5 0.5	Longer time required but plates will be pried apart by swelling PVB	Glass/glass laminates of this size in wide regular use	2	Aluminum U-Channel	JPL des. connect with pigtail lead	21.1	180 3.6-in.-diam cells 12 x 15 array (36 in series) 15 V @ NOCT (37°C)	1. Autoclave process dissolved air bubbles. 2. Meets all LSSA spec.

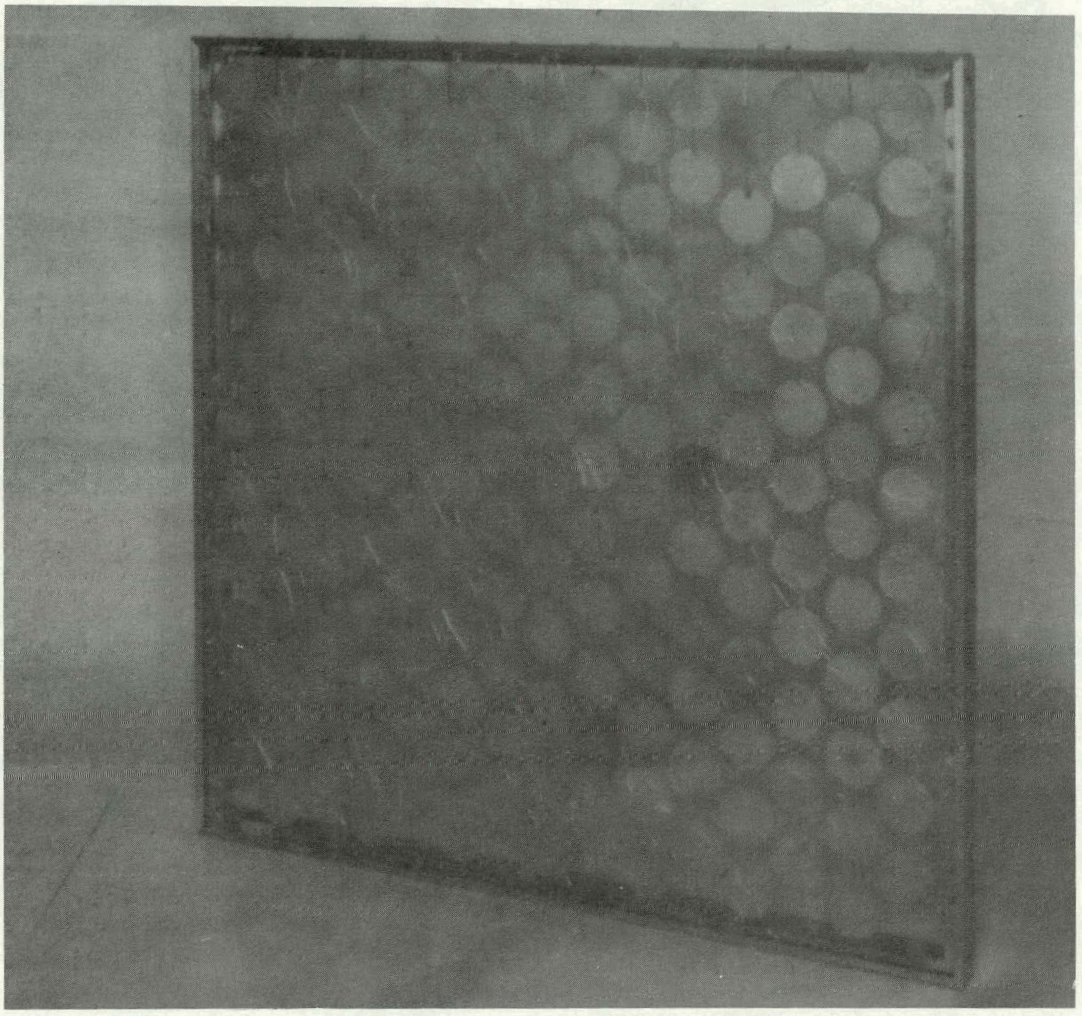

Figure 77. First 4- by 4-ft laminated panel with aluminum frame having extensive breakage and bubbles.

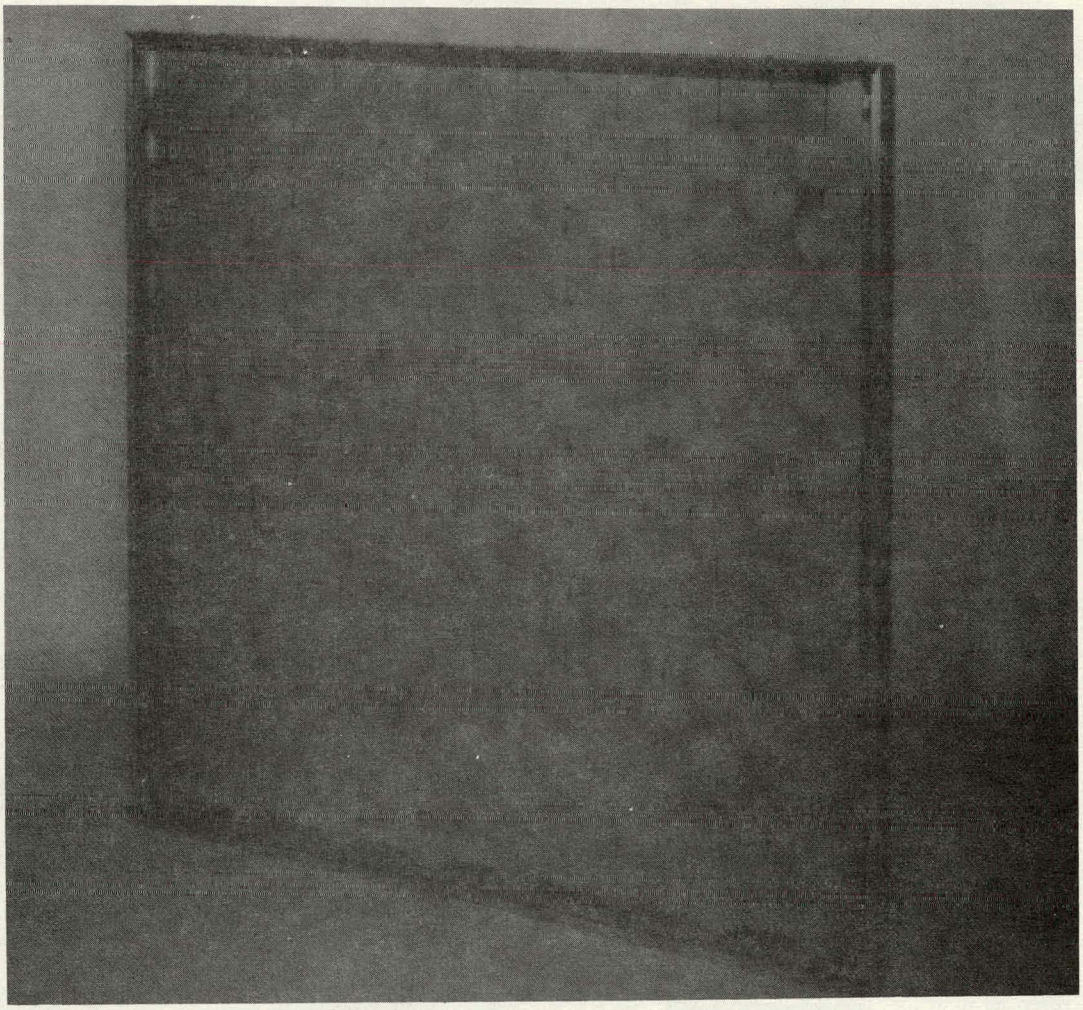

Figure 78. Second 4- by 4-ft laminated panel with aluminum frame having limited breakage and one bubble.

than solid glass. This porous layer, however, is susceptible to body oils and other environmental impurities which tend to destroy the antireflection (AR) character of the surface. With this etch-formed AR coating in mind, the adhesive band between cells approach can be implemented optically through the following options:

(1) AR/No AR/oil
(2) AR/AR/Air
(3) No AR/No AR/Air

The performance of the various choices is summarized on line 1 of Table 15. In addition to the variation of optical coupling, the air film adds a thermal resistance which causes an additional 2.9% power loss due to higher cell temperature.

In light of the JPL specification for 10,000 wind load cycles this panel was judged as very likely to fail at the bond dots. A 2- by 2-ft mechanical panel model was constructed using this technique and is shown in Fig. 79. The area required for epoxy dots decreases panel packing density particularly when sheet-grown rectangular cells become available. Therefore, this technique would not have long-term applicability.

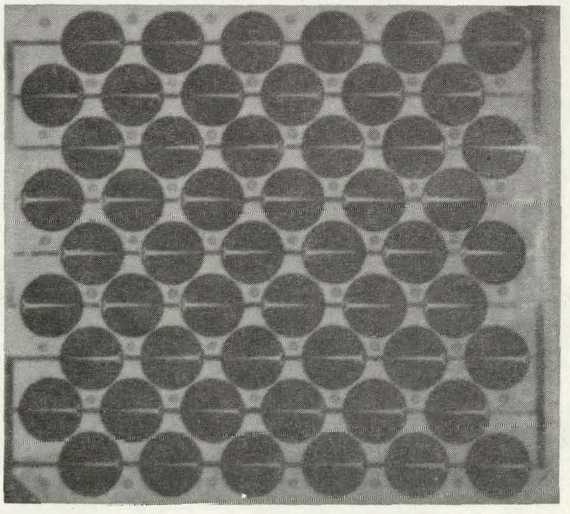

Figure 79. Photograph of mechanical panel model.

c. Adhesive Bonding on Cells - The technique of putting epoxy dots on each cell so that the dots spread over the cell by displacement was considered. This technique would leave air spaces between cells if the epoxy quantity and final gap were closely controlled. The major advantage of this technique is that the bond area could be increased 15 to 20 times, thus largely solving the laminate fatique problem. However, there is nonuniform radial flow caused by finger geometry and wettability variations. These effects always cause air bubble entrapment, and as the bond thickness is decreased to its final value around 0.010 in., the percentage of voids in front of the cells can easily approach 50%.

The fabrication process for this technique would be the implacement of multiple dots of premeasured epoxy on the glass sheet on the cell centers. Then the glass sheet would be lowered on the cell array causing the radial outflow of all dots simultaneously. The subassembly would be turned over, and the same process would be repeated on the other side. A few preliminary tests with this technique using single cells were performed. The resulting bubble patterns and their optical/thermal effects caused this technique to be abandoned.

d. Safety Glass Lamination - This is the preferred panel technique, and all results to date have been quite encouraging. The basic approach is to encapsulate the cells in the same polyvinyl butyral (PVB) resin that is used for safety glass. The technology of laminating two sheets of untempered glass with a 0.015-in. sheet of PVB is widely used for automotive and architectural applications. Current production rates of PVB are equivalent to more than 1000 mW/yr; thus the midterm requirements for PVB would not have an impact on cost and supply.

The refractive index of PVB is 1.48 which is an excellent match to the index of soda lime of 1.50. There are various grades of PVB with UV absorbing compounds added to protect fabrics from yellowing. However, above 0.40 UV transmission tests indicate no detectable interface reflectance between PVB and glass. In the PVB compounds without UV absorbing materials there has never been a report of UV yellowing. Since PVB has been in service for more than 20 years, it appears that this material will definitely achieve the JPL life goals.

The PVB is supplied as sheet stock at 0.015-in. thickness with a carefully controlled moisture content that affects stretchability. To control the moisture content the PVB must be stored at 50°F or below at all times in a protective bag. The blanking and layup room must be controlled at 65°F and 18 to 22% relative humidity. The assembly layup is from top to bottom:

(1) Glass sheet
(2) 0.015-in. PVB sheet
(3) Interconnected cell array
(4) 0.015-in. PVB sheet
(5) Glass sheet

Then the assembly is placed in a rubber bag and the bag is placed in an autoclave (pressure/temperature chamber). Then the bag is evacuated to withdraw most of the air from the interface region. The temperature is then increased to a maximum of 140°C and the autoclave pressurized to 50 to 100 psig to cause the PVB to flow intimately around all the cells and interconnects (Fig. 80). The hydrostatic pressure in the PVB (which is equal to the autoclave pressure) causes all the tiny air bubbles to dissolve in the bulk of the PVB. Thus when the process is properly adjusted, a void-free, optically perfect interface is created.

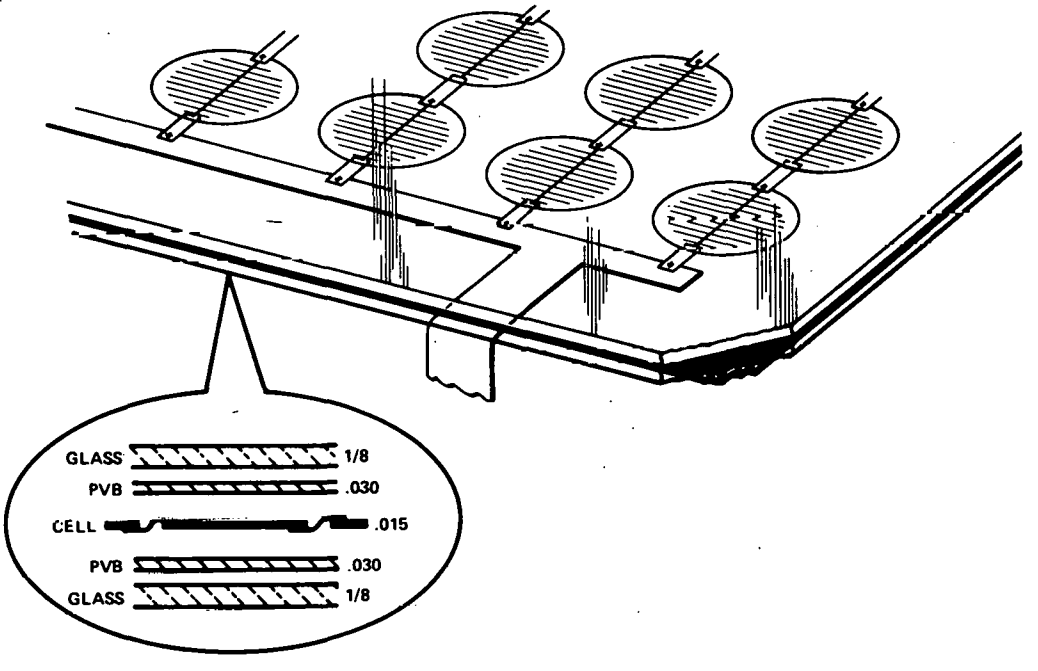

Figure 80. Solar panel configuration.

A 6- by 6-in. laminate with four active series-connected solar cells was fabricated. Over the cell area there were no bubbles, but several small ones were visible between cells. A dark I-V curve was taken before and after laminating with no change. Then the lamination was cycled through 50 cycles from -45 to 95°C with no change in the dark I-V curve. The laminating industry states that any visible bubble will grow through peeling caused by temperature-induced pressure changes within the bubble. This fact was seen to occur with the four-cell laminate where most bubbles approximately doubled in diameter. Thus, it is important that any laminate be entirely bubble-free.

A cross-sectional view of the solar panel frame is shown in Fig. 81. The two frame sections will be a custom-designed aluminum extrusion. Two rubber gaskets are used to cushion the glass against differential thermal expansion and wind-load damping. A foil seal is used on the vertical edge of the laminate to prevent liquid water from contacting the PVB, which swells upon contact with water. Figures 82 and 83 show the details for on-site mounting and panel electrical interconnects.

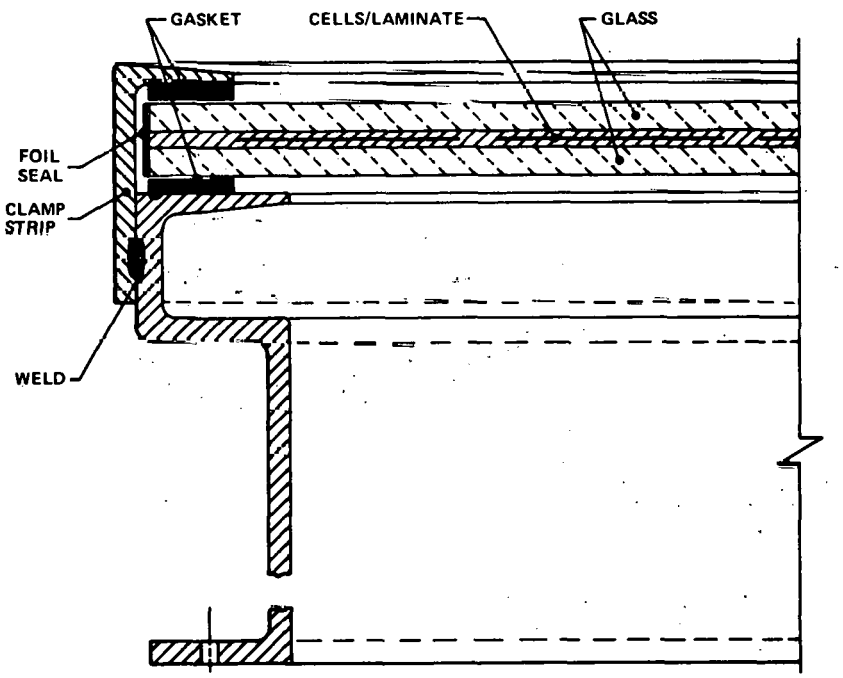

Figure 81. Solar panel framing.

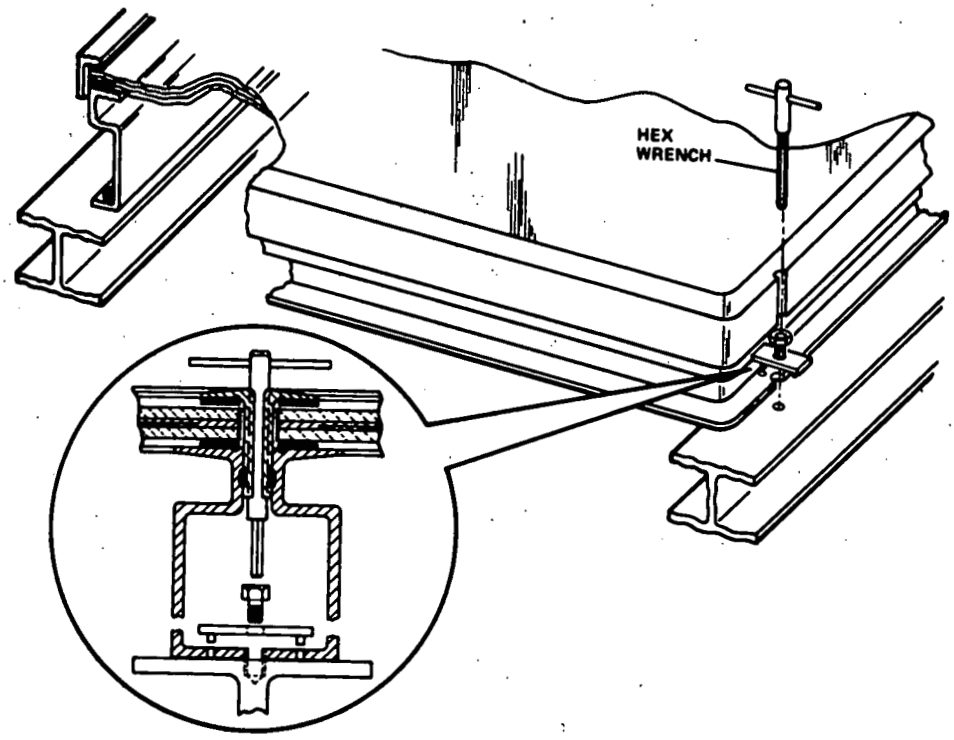

Figure 82. Front/rear mounting.

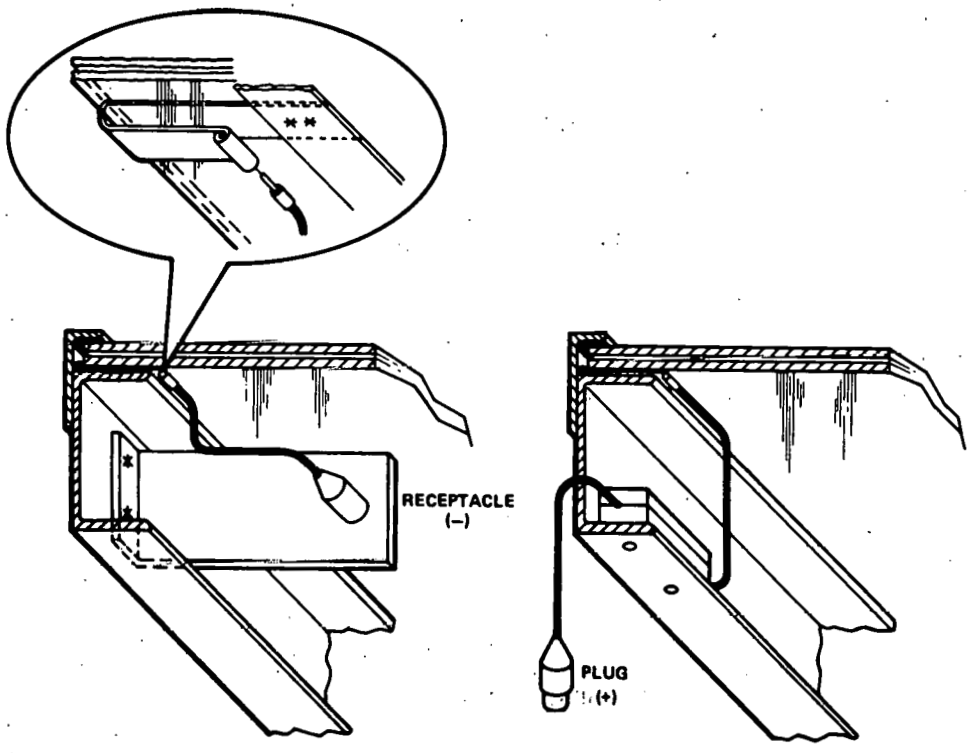

Figure 83. Panel interconnect detail.

At the end of this phase two full-size panels containing interconnected dummy cells were laminated and assembled into frames. The first laminating procedure used too much pressure and broke around every cell and had numerous internal air bubbles (Fig. 77). The second panel laminated has only one air bubble (1 mm) and initially two short cracks. Several additional cracks were caused in handling for assembly into the frame (Fig. 78).

2. Cell Matching Analysis

This analysis is being conducted to determine whether any cell measuring and sorting strategy can increase assembled panel generation capability compared with random cell selection for the panel. It is expected that 100% acceptance testing of cells will be required to avoid the possible use of inactive cells. This effort is directed to the issue of whether there should be sorting of good cells into performance categories.

It is still not possible to characterize the product distribution of a low-cost solar cell production line. This study is based on certain simplifying assumptions concerning cell property variability produced by such a line. Therefore, the results of this study should not be regarded as definitive. The computer models and techniques used in this study can be used for more exacting studies as product variability becomes better defined.

a. Assumptions - It is assumed that the only cell test to be performed will be a measurement of a test current (I_{test}) at AM-1 flux and at a preselected test voltage (V_{test}). The selected test voltage is in the middle of the range of voltages where P_{max} will occur; typically this is 460 mV. Since the AM-1 flux is known, then this test actually measures efficiency (η_{test}) at V_{test}.

In order to compute the panel output power with various cell combinations, a closed form function describing the cell I-V characteristic is required. Basically, there is a choice between two different expressions. The simplest function uses one exponential term to represent junction current leakage while the more complicated function uses two exponential terms. The one-term function requires knowledge of short-circuit current (I_{sc}), open-circuit voltage (V_{oc}), and one point near the P_{max} point, i.e., (I_{test}) at (V_{test}) to solve for the constants (A, I_o) that will pass the characteristic equation through all three

points. In contrast, the two-term I-V characteristic requires one additional point (I, V) to find three constants (A, I_{o1}, I_{o2}) that will pass the characterisic curve through all four points. In order to use the one-term characteristic, the following assumptions have been made.

(1) All usable cells have the same open-circuit voltage, V_{oc}.

(2) The ratio of short-circuit current I_{sc} to test current (I_{test}) is the same for all cells at a value of I_{ratio}.

Some assumptions must also be made about the distribution of cells produced. The most logical assumption is that the measured test efficiencies η_{test} fit a normal (Gaussian) probability distribution; that is, that the probability of a cell having a given efficiency fits the curve in Fig. 84.

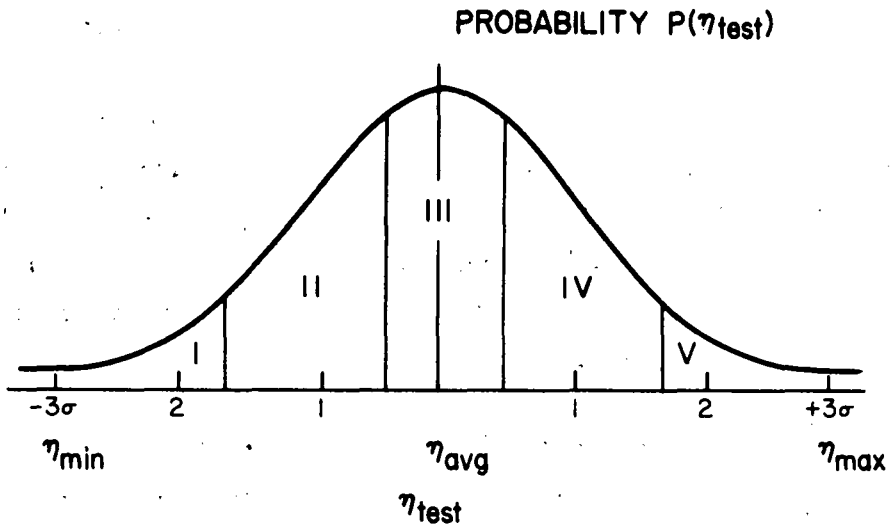

Figure 84. Gaussian probability distribution of test efficiency of cells.

The requirement of this curve is that the integral under a normalized curve over all values of X is equal to 1. This simply states that all cells measured have a measurable test efficiency. It is assumed that all cells between $\pm 3\ \sigma$ (standard deviations) will be accepted for panel fabrication, which would consume 99.8% of all cell production. The final results will show that even if this "window" were narrowed, the conclusions would be unaffected.

It is assumed that all test efficiencies falling in arbitrarily defined ranges of test efficiencies will be separated into different bins. Thus any cell falling within the efficiency range defined by region I in Fig. 84 would be put in box I and so forth. For the purpose of this analysis, it is assumed that all cells in box I can be represented by the efficiency at the middle of the range I and so forth. For the purpose of this analysis, it is assumed deviations defining the various ranges have been picked; the analytical relationship of the Gaussian distribution can be used to find the cell populations of each box.

b. Analytical Model - The basic analytical relationship used in this circuit model is the well-known single exponential relationship between cell voltage and current. The key circuit relationships data processing steps used will be described in the logical sequence used in the model. For the particular case analyzed, the test efficiency points were:

η_{max} = 18% +3 σ
η_{avg} = 15% mean
η_{min} = 12% -3 σ

Five sort regions were chosen with the average efficiency in each bin being:

$\eta[1]$ = 12.62%
$\eta[2]$ = 13.87%
$\eta[3]$ = 15.0%
$\eta[4]$ = 16.12%
$\eta[5]$ = 17.38%

V_{oc} = 0.545 open-circuit voltage
I_{ratio} = 0.75 ratio of short-circuit to test current.

The value of I_{ratio} used is representative of terrestrial cells in use today. Further investigations can accommodate value in the range of 0.55 to 0.85, probably due to variations in series resistance.

AM-1 = 0.097 W/cm^2 (AM-1 flux) (27)

The characteristic I-V expression referred to earlier is

$$I_L = I_{sc} - I_o \left(e^{\lambda/AV_L} - 1\right) = I_L\,(V_L) \qquad (28)$$

where $\lambda = e/kT - 38.647$, a known constant. For reference, the I-V characteristics for the five regions are shown in Fig. 85. By placing the points (I_{test}, V_{test}), $(0, V_{oc})$ along with $I_{sc} = I_{test}/I_{ratio}$ in Eq. (28), two simultaneous equations are generated that define the A and I_o for the particular cell's characteristic curve.

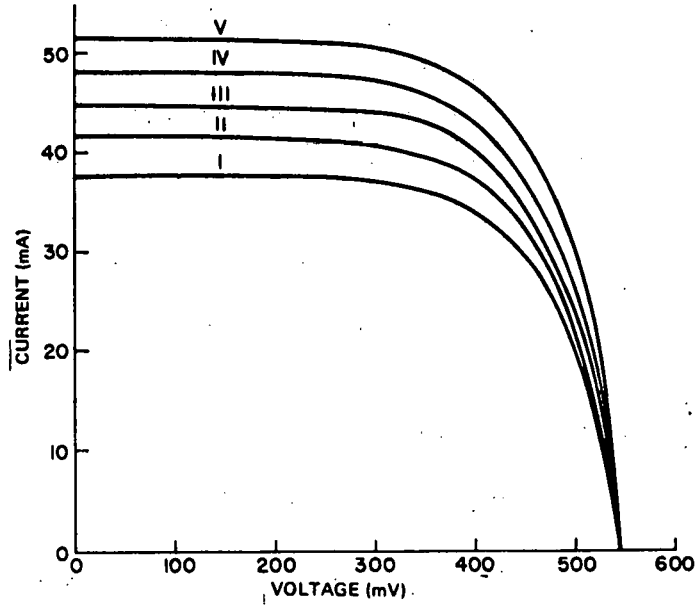

Figure 85. I-V characteristics of five sort regions.

A and I_o are found by a Newton-Rapheson technique. In this manner, the constants for all cell bins are found A[J], I_o[J] for J = 1 to 5.

The fraction of production (Frac) that falls in equal regions found by numerical fit to the Gaussian distribution is

Frac[1] = 0.047
Frac[2] = 0.264
Frac[3] = 0.378
Frac[4] = 0.264
Frac[5] = 0.047

The calculation which must be made is to compare the maximum performance of a circuit with the distribution of cells shown above, all operating at maximum efficiency with the same circuit operating at the design terminal voltage and each cell at the same current.

(1) Operation at Maximum Circuit Efficiency - The power produced by a P_L is given by

$$P_L = V_L \; I_L \; (V_L) \tag{29}$$

where $I_L \; (V_L)$ is given by Eq. (28). To find the maximum power, the derivative $\frac{d(P_L)}{d(V_L)}$ of Eq. (29) can be found readily in closed form. Then by using the Newton-Rapheson method, the value of voltage $V_{pmax}[J]$ in Eq. (29), the values of $P_{max}[J]$ per cm^2 of cell for all regions can be found. Each of the values of power must be multiplied by the appropriate area Frac[J] to get the actual power. Therefore, the maximum total produced is given by

$$P_{mi} = \sum_{J=1}^{J=5} \text{Frac}[J] \; P_{max}[J] \tag{30}$$

In other words, P_{mi} is the maximum power that could be produced if the cells were sorted and assembled into five different panel types.

(2) String Operation - When power is produced by a string of cells, they must all have the same current density. However, the power to the panel is contributed in proportion to the areas Frac[J]. Thus, the expression for the string power as a function of current I_L is given by

$$P_{string} \; (I_L) = \sum \text{Frac}[J] \; P_L \; (I_L) \tag{31}$$

Here the power as a function of current I_L is needed which can be found by solving Eq. (28) for $V_L(I_L)$, and, therefore, $P_L(I_L) = I_L * V_L \; (I_L)$. Here again the derivative of string power with respect to current $d(P_{string})/d(I_L)$

can be found in closed form. Then the value of I_L for maximum string power is found, I_{pms}. In this manner, the maximum string power found is

$$P_{ms} = V_{string} (I_{pms}) \tag{32}$$

Thus, the value of P_{ms} corresponds to the panel power produced if the panel were composed of the appropriate fractions of production Frac[J] for the normal distribution. That is, P_{ms} represents the typical panel with no sorting.

(3) Results - The result of all these calculations is that

$P_{mi} = 16.4$ mW/cm^2 - independent optimized operation
$P_{ms} = 15.9$ mW/cm^2 - string optimized operation

Thus there is only a 2.95% gain in the power produced due to the sorting and selective assembly postulated in this analysis. For 100% test of wafers in an automated facility, we have shown that the test cost is \$0.012/W. If the installed power supply costs \$1/W, this ∿3% increase in output power saves 1.8¢/W, and, therefore, the implementation of this procedure is cost-effective. It is recognized that many assumptions had to be made to conduct this analysis. It is possible that other distributions of cells or a distribution of different cell characteristics could change the conclusions somewhat. It will probably not be worthwhile to pursue this issue further until the low-cost parameters are more completely characterized.

E. CONCLUSIONS - EXPERIMENTAL PRODUCTION STUDY

The work reported here represents a 6-month experimental production study of the elements of low-cost manufacturing sequences previously identified. In starting any production line, a "learning-curve" process is inevitably experienced, so that the conclusions drawn are to be considered preliminary, and should be weighted accordingly.

1. Solar Cell Experimental Production Study

The major process variable studied, that of junction formation, included $POCl_3$ gaseous diffusion, spin-on source (P) diffusion, and ion implantation (P and As). The major conclusions concerning these are:

- $POCl_3$ gaseous diffusion resulted in the best cell performance.
- Spin-on phosphorus sources resulted in reasonably good junctions and cell performance. Reproducibility, stability of the source, and uniformity all need further verification.
- The ion-implanted junction-formation process for both arsenic and phosphorus generally resulted in poor cell performance. The short-circuit currents obtained from cells made by ion implantation were lowest of the three junctions processes and exhibited the largest in-lot and lot-to-lot variations. Generally poorer junction quality and low values of lifetime characterized this process.
- Individual process step yields exceeded 90% even though manual handling was used. Wafer breakage was the major factor in yield loss.
- High temperature processing (>900°C) resulted in lower short-circuit current.
- Little correlation was noted between measured junction sheet resistance and cell performance in that wide variations of sheet resistance did not result in similar variations in electrical cell parameters.

2. Screen-Printed Thick-Film Metallization

- Of the four commercial inks studied, the Owens-Illinois 6105 phosphated ink exhibited the best electrical characteristics.
- Inks which do not contain phosphates were found to yield unacceptably high values of contact resistance and generally resulted in shunted junctions.
- A firing temperature of 675°C was found adequate to obtain a contact resistivity of ~0.05 to 0.08 ohm-cm to n^+ junction layers having 30- to 50-ohm/square sheet resistance and junction depth of 0.25 μm.
- Screen meshes of 200 lines/in. and emulsion thickness of 1 mil were found to result in poor dimensional control in the printing of 5-mil-wide lines.

- The thickness of the fired lines ranged from 15 to 20 μm and had sheet resistivity of 4 to 6 μohm-cm. These values were found adequate for the front grid of solar cells.

3. Panel Assembly

A preferred panel design and assembly technique has been determined. This design incorporates features directed towards satisfying JPL specifications on electrical performance and acceptance test requirements. The panel is a double-glass laminate structure, 4 by 4 ft in size, containing 11 x 15 array of 3.6-in.-diameter cells. The construction makes use of a well-established safety glass lamination technique by laminating two 1/8-in.-thick sheets of untempered glass with two 0.015-in.-thick sheets of polyvinyl butyral (PVB) which encapulate the cells and bond the glass. Some preliminary conclusions derived from initial tests of this laminating procedure are:

- It is important that the laminate be entirely bubble-free since even small bubbles will eventually cause delamination during thermal cycling.
- Small, 6- by 6-in. panels were successfully constructed containing active cells. No change in cell characteristics was noted after 50 cycles of -45 to +95°C thermal testing.
- The lamination procedures required for full-size (4 by 4 ft) panels have not been determined. In initial tests, lamination of 4- by 4-ft panels resulted in cracking of the glass.

F. RECOMMENDATIONS

In order to more fully verify those process steps which are currently acceptable and to develop and bring to a state of readiness the processes needed for a complete cost-effective manufacturing sequence, the following recommendations are made:

(1) Economic analysis and experimental production data are required on silicon wafers having saw/etched surfaces.

(2) The details of the limits on input/output requirements of the $POCl_3$ gaseous diffusion junction-formation technique in conjunction with the requirements for screen-printed contacts should be determined by experimental production of a sufficient quantity of cells.

(3) While spin-on source dopants seem econonically viable, further work is required on the relationship of the liquid source composition to its stability and the resultant junction properties. Specifically, water-based dopant sources should be evaluated.

(4) The ion implantation and thermal activation and anneal process require a thorough evaluation to determine the processing steps necessary to achieve higher efficiencies in cells fabricated by this method.

(5) A complete procedure for front-grid and back surface screen-printed metallization requires development. Specific attention should be directed toward compatibility of the metallization with interconnect technology (solderability), back surface ohmic contacting, wafer breakage, and development of performance and cost-effective inks.

APPENDIX A

A. COST ANALYSIS PROCEDURE

For purposes of cost analysis, the manufacture of solar array modules has been represented by a series of technological process. (See Appendix B for definition of terms.) Each technological process must be described in terms of the following:

(1) Incoming material requirements.

(2) Value added - material, labor, overhead.

(3) Equipment requirements as a function of production levels.

(4) Process yield - ratio of output units to input units. (Note that this is a measure of *physical flow*, not product quality.)

After these parameters have been provided, alternative manufacturing processes can be defined in terms of a subset of these technological processes. For a specified level of output (measured in megawatts), cost data will be provided for each technological process and the total manufacturing process.

The following problems arise even in this simple cost model:

(1) The electrical characteristics of the output of two alternative technological processes may differ.

(2) The quality of two alternative processes may differ.

(3) Synergistic effects of combining various processes may need consideration.

In the initial model implementation, the material input to any technological process i will be M_i units. If y_i is the process yield and r_i is the number of input units constituting one output unit (e.g., 7.35 g per wafer), then the output M_i of this process will be $(M_i/r_i)y_i$. The number of input units scrapped in the process will be $M_i - M_i' r_i = M_i(1-y_i)$.

Figure A-1 depicts a technological process used in the manufacture of solar array modules. M_i incoming units valued at $\$X_i$ per unit are processed. Direct material, direct labor, and overhead increase the value of each unit to $\$X_i'$. M_i' units leave the process and enter the next step; the remaining input units are scrapped, with the salvage value being used to reduce process overhead. The average output unit cost X_i' is determined from process cost information.

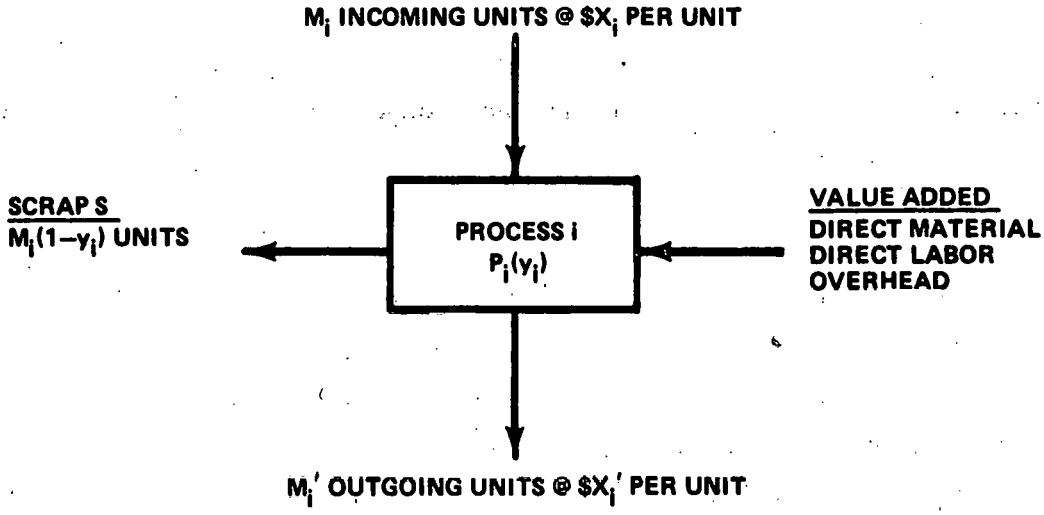

Figure A-1. Technological process representation.

It is important to note that the number of units entering a process normally will be greater than the number leaving the process. Hence, the capacity requirements of various processes may differ. This simple model assumes that flow is from one process to the next; no feedback of units to an earlier stage is currently permitted. Therefore, for a given megawatt requirement, the processing requirements of each technological process can be determined and then the cost of processing a unit computed.

Once a description of each technological process has been made, the user of the model must specify the output requirements (megawatts), the technological processes to be used, and the electrical characteristics of the final solar cells (electrical characteristics will be dependent upon the processes used). The model will then compute the cost of output requirements and provide detailed cost estimates on a process basis. Alternative strategies can be explored. Also sensitivity of cost to various parameters can be studied by varying the individual parameters.

Once a small number of feasible alternatives have been selected, a detailed financial analysis could be made of each alternative. This analysis could use a simulation approach in order to incorporate uncertainty rather than the deterministic approach utilized in the initial screening process in order to estimate the risk involved in each alternative scheme.

This model facilitates the analysis of alternative manufacturing approaches. It is only a first approximation, however, whose primary purpose is to systematize

the financial analysis and permit comparisons with current state-of-the-art cost estimates. This initial model will need enhancements to incorporate some os all of the following items:

(1) Multi-year analysis capability utilizing discounted cash flow techniques.

(2) Distribution of electrical characteristics to represent the "quality" of individual processes. This would be based upon the performance approach described in Quarterly Report No. 1 [A-1].

(3) Synergistic effects of combining certain processes.

The selection of those features to be implemented will depend upon the number of different process combinations to be analyzed and the accuracy to which process parameters can be estimated.

The cost estimates provided by the model include:

(1) Processing cost, expressed in $/W

(2) Floor area requirements for manufacturing area

(3) Direct and indirect labor personnel required

(4) Material and direct expense summary

In order to estimate selling price, wafer cost, factory investment, interest and depreciation on this investment, and salaries of support personnel must be determined. (Support personnel includes administration, warehouse personnel, finance, quality control, etc.)

That is,

Wafer cost, $/W
+ Processing cost, $/W
+ Heating, cooling, lighting, $/W
+ Insurance, $/W
+ Factory interest & depreciation, $/W
+ Administrative & support salaries, $/W
+ Profit, $/W

= Selling price, $/W

A-1. B. F. Williams, *Automated Array Assembly*, Quarterly Report No. 1, ERDA/JPL-954352/1, prepared under Contract No. 954352 for Jet Propulsions Laboratory, March 1976.

APPENDIX B - GLOSSARY OF TERMS

A. GENERAL INPUT PARAMETERS

1. Growth profile - not used currently
2. Shift premium - 2nd or 3rd shift bonus rate
3. Depreciation method: SL = straightline; SYD = sum-of-the-year-digits
4. Interest rate on debt - interest rate on borrowed funds
5. Debt ratio - % of fixed assets financed by debt
6. Sheet - 7.8-cm (3.07)-diameter wafer
7. Solar cell - a "sheet" after electrical test
8. Array module - a 14.6 ft^2 panel containing 224 solar cells
9. Purchased silicon cost, $/W - not used currently

B. GENERAL INPUTS: INVESTMENT TYPE DEFINITIONS

1. Name - investment name
2. Type - process or factory
3. Availability - % of time investment is available for use. Remainder of time consists of preventive maintenance, unscheduled maintenance, or idle time due to lack of availability of related investments
4. Cost - first cost + delivery charges + taxes + installation costs
5. Book life - estimated life for depreciation purposes
6. Area - area, in ft^2, occupied by investment and associated operators

C. GENERAL INPUTS: LABOR TYPE DEFINITIONS

1. Labor name - labor category
2. Labor type - direct: labor which varies directly with the level of production; indirect: labor which is constant over a range of production
3. Wage rate = $/hr base pay
4. GP# - not used
5. Fringe benefits - cost of employee fringe benefits expressed as a % of wage rate
6. Efficiency - ratio of labor required to actual labor (allows for rest periods, lunch periods, absences, etc.)

D. GENERAL INPUTS: EXPENSE TYPE DEFINITIONS

1. Expense name - material or direct expense name
2. Type - material: items which become an integral part of solar cell or array module; direct expense: items consumed in cell or array manufacture which do not become an integral part of assembly
3. Cost - (a) cost of item, in $/cm^3, $/gram, $/kwh (process expenses will be expressed in units specified); (b) "specified in $" if process expense will be expressed in $
4. Salvage value - not used currently

E. PROCESS PARAMETERS

1. Process - group of operations associated with a specific technology step
2. Subprocess - a group of operations shared by one or more processes
3. Input unit, output unit - "sheet," "solar cell," or "array module"
4. Transport In, Transport Out - method of transferring units into and out of the process area
5. Process yield ("YIELD") - ratio of output units to input units. This is a measure of physical flow, not process quality
6. Input unit salvage value ("SALVAGE VALUE") - estimated recovery value of a scrapped input unit. At this moment, all values are zero
7. Production area floor space requirements - estimate of floor area needed, excluding area occupied by investments. "Floor space" is calculated using the "AREA (SQ.FT.)" value associated with the largest "INPUT UNITS" volume less than or equal to current production volume. The area associated with investments is added to this base area amount to determine the "estimated floor area" of the process
8. Description - brief process description
9. Assumptions - list of assumptions made in preparing cost estimate
10. Procedure - description of process major steps
11. Investments - (a) name: investment name, defined in B above; (b) maximum throughput units: throughput of investment (sheets/h, solar cell/h, or array module/h. Effective rate = maximum throughput x availability. (If both sides of an input wafer are to be processed separately, either adjust the throughput rate *or* adjust the "fraction of input units processed" parameter.) (c) % input units processed: used to adjust input volume for rework and for processing both sides of a wafer separately. It may also be used for "rework only" investments to specify fraction of input units requiring rework. NOTE: If two or more different investments are part of a set, the *effective* throughput rates must be the same.

12. Labor - (a) name: defined in C above; (b) labor requirements base: (1) investment name or (2) "fixed" - # persons/shift fixed (3) "DL" - base is # of direct labor persons; (4) "TL" - base is # fo labor persons associated with process (c) # of persons/shift/base unit - ratio of persons of specified labor type to # units of specified base *or* (d) throughput/h/person - # of input units per hour handled by specified labor type

    % input units processed - % of input units for which this type of labor is required. If an input unit is processed more than once (both sides and/or rework), this factor may be greater than 100%. If only reworked units or units passing some internal test are processed, this factor may be less than 100%.

$$\#\ \text{operators/shift} = \frac{\#\ \text{input units/yr} \times \%\ \text{input units processed}/100}{\text{throughput/h} \times \#\ \text{hours/year} \times \text{efficiency}}$$

13. Supplies/expenses - (a) name - see D above; (b) annual fixed part - fixed part of expense (multiplied by # labor persons or investment units for labor or investment bases). Must be specified in same units as espense name. (c) variable part - units - variable part of expense; (d) base - (1) per input unit, % input units processed (2) per available investment/hr of specified investment

$$\$\ \text{Cost} = (\text{Annual fixed part} + \text{variable part} \times \text{base units}) \times (\$/\text{unit})$$

F. COST ANALYSIS: PROCESS AND OTHER COST ESTIMATES

1. Material - material cost, $/W
2. D.L. - direct labor cost, including fringe benefits, $/W
3. EXP. - direct expense cost, $/W
4. P.OH. - process overhead cost, $/W (indirect labor cost)
5. INT. - interest cost, $/W
6. DEPR. - depreciation cost, $/W
7. TOTALS - total of items 1-6, above
8. INVEST - investment required, $/W

G. COST ANALYSIS: MANUFACTURING SEQUENCE NAME

1. Material, etc. - as in F above
2. SALVG. - estimated recovery value of scrap, $/W

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